

PCN

AO-PCN-2023-030-A

Introduction of next chip generation for OSOLON Signal devices

03.04.2023

Dear Customer,

please review this **PCN** and provide your feedback in the **Customer approval form** (at the end of this PCN document) to your ams OSRAM sales partner before **10.05.2023** *).

Your prompt reply will help ams OSRAM to assure a smooth and well executed transition. If ams OSRAM does not hear from your side by the due date, we will assume your (if you are a Distributor: and your customer's) full acceptance to this proposed change and its implementation.

ams OSRAM understands the time requirements your organization needs to approve this PCN. However, if you can provide ams OSRAM an estimated date your organization will have finalized this PCN review, ams OSRAM can use this date to plan continued production to secure your order needs during the transition time.

Your attention and response to this matter is highly appreciated.

Please direct your inquiries to your local Sales office.

- *) ams OSRAM aligns with the widely recognized JEDEC/ECIA/IPC Joint Standard No. 46, which stipulates:
- Customers should acknowledge receipt of the PCN within 30 days of delivery of the PCN.
 - Lack of acknowledgement of the PCN within 30 days constitutes acceptance of the change.
 - After acknowledgement, lack of additional response within the 90 day period constitutes acceptance of the change. If the customer requires additional time to perform sample testing, beyond the 90 day review period, an extension must be negotiated with the supplier.

Subject of change: Introduction of next chip generation for OSOLON Signal devices

Affected products: Refer to document 2_cip_AO-PCN-2023-030-A

Reason for change:

- Secure continuous supply
- Chip performance improvement

	<u>Current status</u>	<u>New status</u>
Description of change:	<ul style="list-style-type: none"> • Current Chip • 38µm wire diameter 	<ul style="list-style-type: none"> • Next Generation Chip • 30µm wire diameter for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01

For details refer to document 2_cip_AO-PCN-2023-030-A

Time schedule for PCN material:
(after implementation of change):

Final qualification report: 03.04.2023

Samples available: On Request

Intended Start of delivery: 01.07.2023^{*)}
^{*)} or earlier if released by customer and upon mutual agreement

Time schedule for Pre-PCN material:
(prior to implementation of change):

Last time order date (LTO): 01.07.2023^{**)}
^{**)} Lead time and LTO quantity shall be mutually agreed between ams OSRAM and customer.

Last time delivery date (LTD): 02.10.2023^{***)}
^{***)} planned last date for delivery of products of current status

Assessment: No change in form and reliability

Documentation:

2_cip_AO-PCN-2023-030-A
 3_Qual_AO-PCN-2023-030-A
 4_Qual_AO-PCN-2023-030-A

Note:

Pre-PCN material: Products of current status, means before implementation of the changes as described in the PCN.

PCN material: Products with implementation of the changes as described in the PCN.

Customer approval form AO-PCN-2023-030-A

Introduction of next chip generation for OSOLON Signal devices

Please list product(s) affected in your application(s):

Please check the appropriate box below:

- | | |
|--|---|
| <input type="radio"/> Approval:
We agree with the proposed change and accept start of the shipment upon availability of PCN material | <input type="radio"/> Not relevant:
Change is not relevant for products in use. |
|--|---|

☐ **Change cannot be accepted:**

- ☐ **We have objections:**
- ☐ **We request following Information:**
- ☐ **We request following Samples:**
- ☐ **Expected approval date:**
- ☐ **Volume requirements for Pre-PCN material:**

☐ **Remarks:**

Sender:

Company:

Address / Location:

Signature:

Date:

Please return this approval form to your Sales partner.

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PCN

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Introduction of next chip generation for OSLON Signal devices

Customer information package

OS Q CQM ICI
2023-04-03

Agenda

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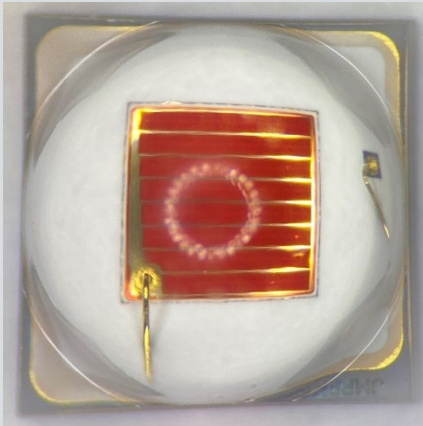
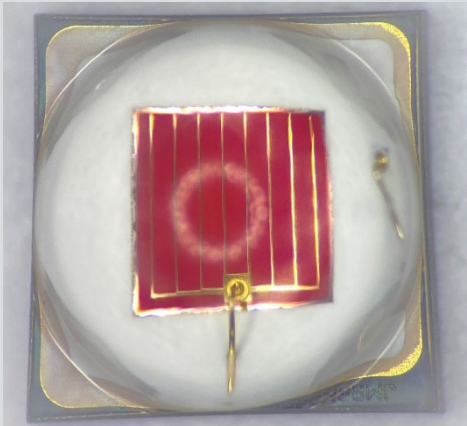
Reason for change

Item	Description
1.	Secure continuous supply
2.	Chip performance improvement

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Introduction of next chip generation for OSOLON Signal devices

Description of change

Item	Current status	New status
1.	Current Chip	Next Generation Chip
2.	Wire diameter of 38µm	Change of wire diameter to 30µm for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 only
3.	Current appearance LJ CRBP.01 	New appearance LJ CRBP.01 

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Description of change

Item	Current status	New status
4.	<div>Current appearance LB CRBP.01</div> <div></div>	<div>New appearance LB CRBP.01</div> <div></div>

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Introduction of next chip generation for OSOLON Signal devices

Changes in the datasheet for LJ CRBP.01

Item	Current status	New status																																																																																																																																								
Characteristics	<div><p>Characteristics</p><p>$I_F = 350 \text{ mA}$; $T_g = 25 \text{ }^{\circ}\text{C}$</p><table><tr><th>Parameter</th><th>Symbol</th><th></th><th>Values</th></tr><tr><td>Peak Wavelength</td><td>λ_{peak}</td><td>typ.</td><td>635 nm</td></tr><tr><td>Dominant Wavelength ²⁾</td><td>λ_{dom}</td><td>min.</td><td>612 nm</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>625 nm</td></tr><tr><td></td><td></td><td>max.</td><td>636 nm</td></tr><tr><td>Spectral Bandwidth at 50% $I_{\text{rel,max}}$</td><td>$\Delta\lambda$</td><td>typ.</td><td>14 nm</td></tr><tr><td>Viewing angle at 50% I_V</td><td>2ϕ</td><td>typ.</td><td>120 °</td></tr><tr><td>Forward Voltage ³⁾</td><td>V_F</td><td>min.</td><td>1.90 V</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>2.15 V</td></tr><tr><td></td><td></td><td>max.</td><td>2.35 V</td></tr><tr><td>Reverse voltage (ESD device)</td><td>V_{RESD}</td><td>min.</td><td>5 V</td></tr><tr><td>Reverse voltage ⁴⁾</td><td>V_R</td><td>max.</td><td>7 V</td></tr><tr><td>$I_R = 5 \text{ mA}$</td><td></td><td></td><td></td></tr><tr><td>Real thermal resistance junction/solderpoint ⁵⁾</td><td>$R_{\text{thJS real}}$</td><td>typ.</td><td>7.0 K / W</td></tr><tr><td></td><td></td><td>max.</td><td>8.4 K / W</td></tr><tr><td>Electrical thermal resistance junction/solderpoint ⁵⁾</td><td>$R_{\text{thJS elec.}}$</td><td>typ.</td><td>3.0 K / W</td></tr><tr><td>with efficiency $\eta_e = 57 \text{ } \%$</td><td></td><td>max.</td><td>3.6 K / W</td></tr></table></div>	Parameter	Symbol		Values	Peak Wavelength	λ_{peak}	typ.	635 nm	Dominant Wavelength ²⁾	λ_{dom}	min.	612 nm	$I_F = 350 \text{ mA}$		typ.	625 nm			max.	636 nm	Spectral Bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	14 nm	Viewing angle at 50% I_V	2ϕ	typ.	120 °	Forward Voltage ³⁾	V_F	min.	1.90 V	$I_F = 350 \text{ mA}$		typ.	2.15 V			max.	2.35 V	Reverse voltage (ESD device)	V_{RESD}	min.	5 V	Reverse voltage ⁴⁾	V_R	max.	7 V	$I_R = 5 \text{ mA}$				Real thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS real}}$	typ.	7.0 K / W			max.	8.4 K / W	Electrical thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS elec.}}$	typ.	3.0 K / W	with efficiency $\eta_e = 57 \text{ } \%$		max.	3.6 K / W	<div><p>Characteristics</p><p>$I_F = 350 \text{ mA}$; $T_g = 25 \text{ }^{\circ}\text{C}$</p><table><tr><th>Parameter</th><th>Symbol</th><th></th><th>Values</th></tr><tr><td>Peak Wavelength</td><td>λ_{peak}</td><td>typ.</td><td>636 nm</td></tr><tr><td>Dominant Wavelength ²⁾</td><td>λ_{dom}</td><td>min.</td><td>612 nm</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>625 nm</td></tr><tr><td></td><td></td><td>max.</td><td>636 nm</td></tr><tr><td>Spectral Bandwidth at 50% $I_{\text{rel,max}}$</td><td>$\Delta\lambda$</td><td>typ.</td><td>15 nm</td></tr><tr><td>Viewing angle at 50% I_V</td><td>2ϕ</td><td>typ.</td><td>120 °</td></tr><tr><td>Forward Voltage ³⁾</td><td>V_F</td><td>min.</td><td>1.90 V</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>2.10 V</td></tr><tr><td></td><td></td><td>max.</td><td>2.35 V</td></tr><tr><td>Reverse voltage (ESD device)</td><td>V_{RESD}</td><td>min.</td><td>5 V</td></tr><tr><td>Reverse voltage ⁴⁾</td><td>V_R</td><td>max.</td><td>7 V</td></tr><tr><td>$I_R = 5 \text{ mA}$</td><td></td><td></td><td></td></tr><tr><td>Real thermal resistance junction/solderpoint ⁵⁾</td><td>$R_{\text{thJS real}}$</td><td>typ.</td><td>6.5 K / W</td></tr><tr><td></td><td></td><td>max.</td><td>7.4 K / W</td></tr><tr><td>Electrical thermal resistance junction/solderpoint ⁵⁾</td><td>$R_{\text{thJS elec.}}$</td><td>typ.</td><td>2.5 K / W</td></tr><tr><td>with efficiency $\eta_e = 62 \text{ } \%$</td><td></td><td>max.</td><td>2.8 K / W</td></tr></table></div>	Parameter	Symbol		Values	Peak Wavelength	λ_{peak}	typ.	636 nm	Dominant Wavelength ²⁾	λ_{dom}	min.	612 nm	$I_F = 350 \text{ mA}$		typ.	625 nm			max.	636 nm	Spectral Bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	15 nm	Viewing angle at 50% I_V	2ϕ	typ.	120 °	Forward Voltage ³⁾	V_F	min.	1.90 V	$I_F = 350 \text{ mA}$		typ.	2.10 V			max.	2.35 V	Reverse voltage (ESD device)	V_{RESD}	min.	5 V	Reverse voltage ⁴⁾	V_R	max.	7 V	$I_R = 5 \text{ mA}$				Real thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS real}}$	typ.	6.5 K / W			max.	7.4 K / W	Electrical thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS elec.}}$	typ.	2.5 K / W	with efficiency $\eta_e = 62 \text{ } \%$		max.	2.8 K / W
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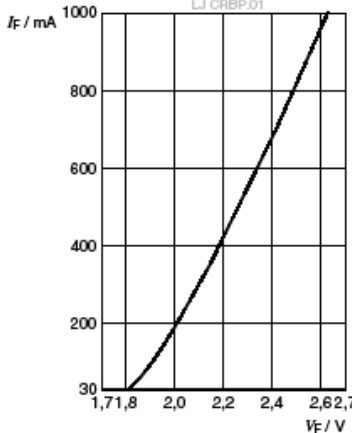
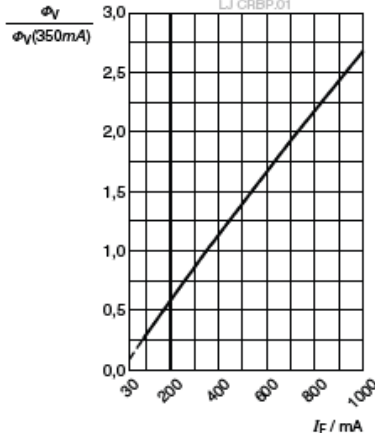
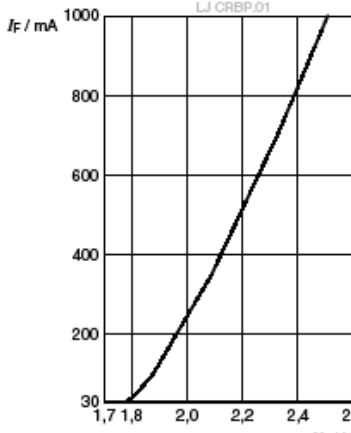
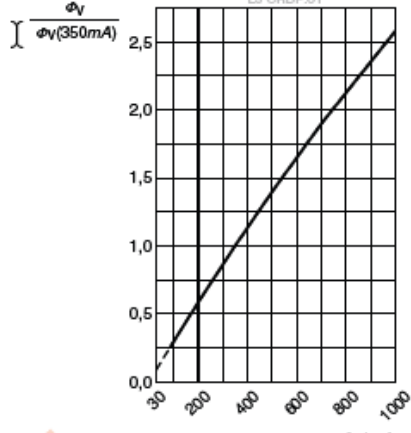
Changes in the datasheet for LJ CRBP.01

Item	Current status	New status
Relative Spectral Emission	<div> <div> Relative Spectral Emission⁶⁾ $\Phi_{rel} = f(\lambda); I_F = 350\text{ mA}; T_g = 25\text{ °C}$ </div> <div> </div> </div>	<div> <div> Relative Spectral Emission⁶⁾ $\Phi_{rel} = f(\lambda); I_F = 350\text{ mA}; T_g = 25\text{ °C}$ </div> <div> </div> </div>

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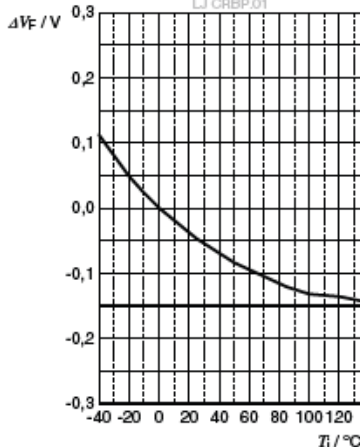
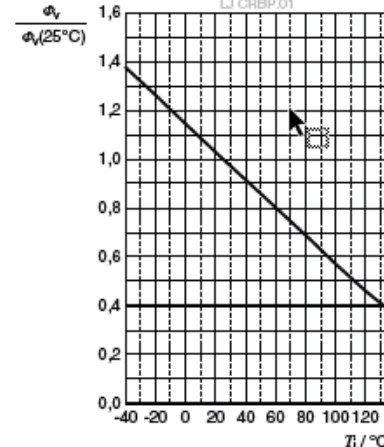
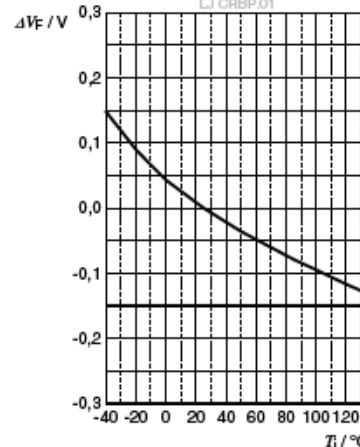
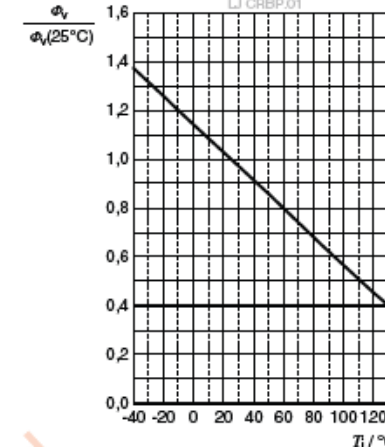
Changes in the datasheet for LJ CRBP.01

Item	Current status	New status
Forward current & Relative Luminous Flux	<div><p>Forward current ⁶⁾</p><p>$I_F = f(V_F); T_s = 25\text{ °C}$</p></div> <div><p>Relative Luminous Flux ^{6), 7)}</p><p>$\Phi_V / \Phi_V(350\text{ mA}) = f(I_F); T_s = 25\text{ °C}$</p></div>	<div><p>Forward current ⁶⁾</p><p>$I_F = f(V_F); T_s = 25\text{ °C}$</p></div> <div><p>Relative Luminous Flux ^{6), 7)}</p><p>$\Phi_V / \Phi_V(350\text{ mA}) = f(I_F); T_s = 25\text{ °C}$</p></div>

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Introduction of next chip generation for OSOLON Signal devices

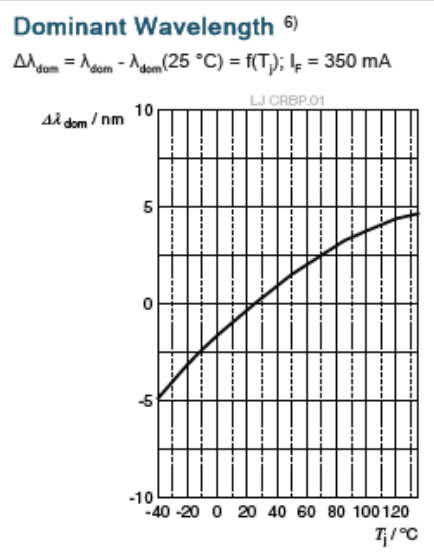
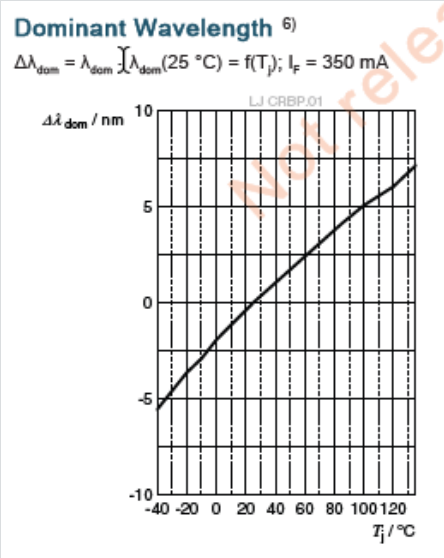
Changes in the datasheet for LJ CRBP.01

Item	Current status	New status
Forward Voltage & Relative Luminous Flux	<div><div><p>Forward Voltage ⁶⁾</p><p>$\Delta V_F = V_F - V_F(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p></div><div><p>Relative Luminous Flux ⁶⁾</p><p>$\Phi_v / \Phi_v(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p></div></div>	<div><div><p>Forward Voltage ⁶⁾</p><p>$\Delta V_F = V_F - V_F(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p></div><div><p>Relative Luminous Flux ⁶⁾</p><p>$\Phi_v / \Phi_v(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p></div></div>

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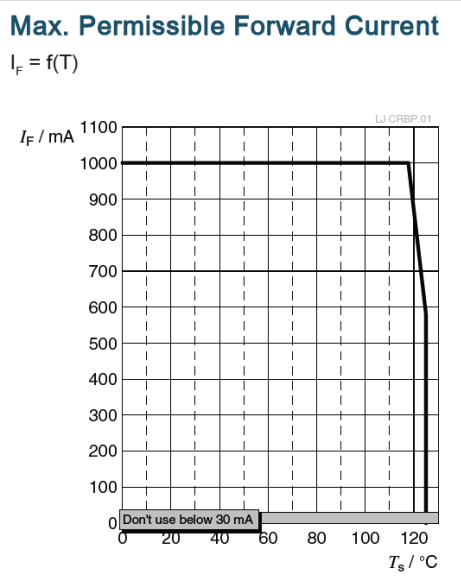
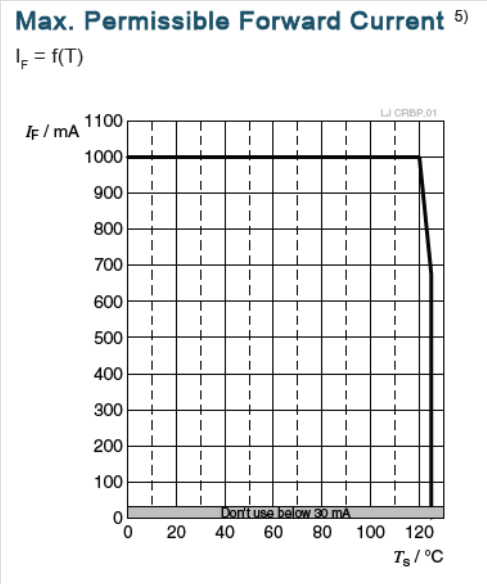
Changes in the datasheet for LJ CRBP.01

Item	Current status	New status
Dominant Wavelength	<div><p>Dominant Wavelength ⁶⁾</p><p>$\Delta\lambda_{\text{dom}} = \lambda_{\text{dom}} - \lambda_{\text{dom}}(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p><p>LJ CRBP.01</p></div>	<div><p>Dominant Wavelength ⁶⁾</p><p>$\Delta\lambda_{\text{dom}} = \lambda_{\text{dom}} - \lambda_{\text{dom}}(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p><p>LJ CRBP.01</p></div>

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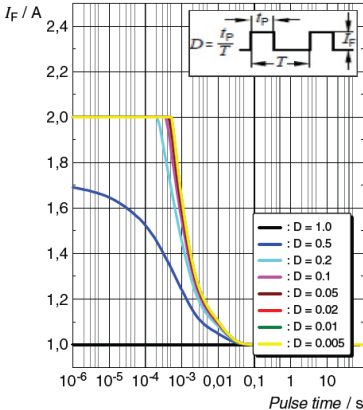
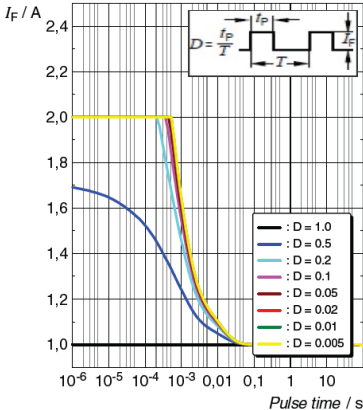
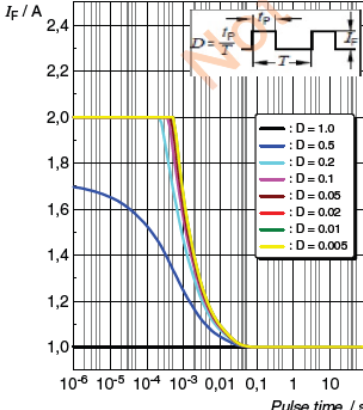
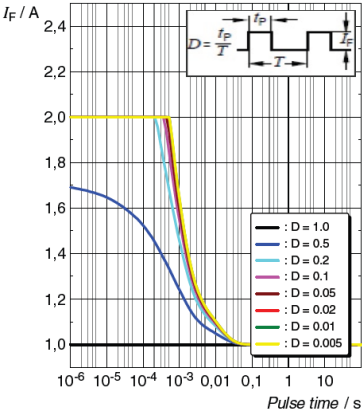
Changes in the datasheet for LJ CRBP.01

Item	Current status	New status
Max. Permissible Forward Current	<div><p>Max. Permissible Forward Current $I_F = f(T)$</p></div>	<div><p>Max. Permissible Forward Current ⁵⁾ $I_F = f(T)$</p></div>

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Introduction of next chip generation for OSLO® Signal devices

Changes in the datasheet for LJ CRBP.01

Item	Current status	New status
Permissible Pulse Handling Capability	<div><div><p>Permissible Pulse Handling Capability</p><p>$I_F = f(t_p)$; D: Duty cycle; $T_s = 25\text{ °C}$</p><p>LJ CRBP.01</p></div><div><p>Permissible Pulse Handling Capability</p><p>$I_F = f(t_p)$; D: Duty cycle; $T_s = 85\text{ °C}$</p><p>LJ CRBP.01</p></div></div>	<div><div><p>Permissible Pulse Handling Capability</p><p>$I_F = f(t_p)$; D: Duty cycle; $T_s = 25\text{ °C}$</p><p>LJ CRBP.01</p></div><div><p>Permissible Pulse Handling Capability</p><p>$I_F = f(t_p)$; D: Duty cycle; $T_s = 85\text{ °C}$</p><p>LJ CRBP.01</p></div></div>

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Introduction of next chip generation for OSOLON Signal devices

Changes in the datasheets for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 (The examples below are for LB CRBP.01. Regarding details for LCY CRBP.01 and LUW CRBP.01 please refer to the updated datasheets)

Item	Current status	New status																																																																																																																																								
Characteristics	<div><p>Characteristics $I_F = 350 \text{ mA}$; $T_8 = 25 \text{ }^{\circ}\text{C}$</p><table><tr><th>Parameter</th><th>Symbol</th><th>Unit</th><th>Values</th></tr><tr><td>Peak Wavelength</td><td>λ_{peak}</td><td>typ.</td><td>472 nm</td></tr><tr><td>Dominant Wavelength ²⁾</td><td>λ_{dom}</td><td>min.</td><td>440 nm</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>475 nm</td></tr><tr><td></td><td></td><td>max.</td><td>480 nm</td></tr><tr><td>Spectral Bandwidth at 50% $I_{\text{rel,max}}$</td><td>$\Delta\lambda$</td><td>typ.</td><td>20 nm</td></tr><tr><td>Viewing angle at 50% I_V</td><td>2ϕ</td><td>typ.</td><td>110 °</td></tr><tr><td>Forward Voltage ³⁾</td><td>V_F</td><td>min.</td><td>2.65 V</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>2.90 V</td></tr><tr><td></td><td></td><td>max.</td><td>3.25 V</td></tr><tr><td>Reverse voltage (ESD device)</td><td>V_{RESD}</td><td>min.</td><td>5 V</td></tr><tr><td>Reverse voltage ⁴⁾</td><td>V_R</td><td>max.</td><td>7 V</td></tr><tr><td>$I_R = 5 \text{ mA}$</td><td></td><td></td><td></td></tr><tr><td>Real thermal resistance junction/solderpoint ⁵⁾</td><td>$R_{\text{thJS real}}$</td><td>typ.</td><td>7.8 K / W</td></tr><tr><td></td><td></td><td>max.</td><td>9.4 K / W</td></tr><tr><td>Electrical thermal resistance junction/solderpoint ⁵⁾ with efficiency $\eta_a = 56 \%$</td><td>$R_{\text{thJS elec.}}$</td><td>typ.</td><td>3.4 K / W</td></tr><tr><td></td><td></td><td>max.</td><td>4.1 K / W</td></tr></table></div>	Parameter	Symbol	Unit	Values	Peak Wavelength	λ_{peak}	typ.	472 nm	Dominant Wavelength ²⁾	λ_{dom}	min.	440 nm	$I_F = 350 \text{ mA}$		typ.	475 nm			max.	480 nm	Spectral Bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	20 nm	Viewing angle at 50% I_V	2ϕ	typ.	110 °	Forward Voltage ³⁾	V_F	min.	2.65 V	$I_F = 350 \text{ mA}$		typ.	2.90 V			max.	3.25 V	Reverse voltage (ESD device)	V_{RESD}	min.	5 V	Reverse voltage ⁴⁾	V_R	max.	7 V	$I_R = 5 \text{ mA}$				Real thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS real}}$	typ.	7.8 K / W			max.	9.4 K / W	Electrical thermal resistance junction/solderpoint ⁵⁾ with efficiency $\eta_a = 56 \%$	$R_{\text{thJS elec.}}$	typ.	3.4 K / W			max.	4.1 K / W	<div><p>Characteristics $I_F = 350 \text{ mA}$; $T_8 = 25 \text{ }^{\circ}\text{C}$</p><table><tr><th>Parameter</th><th>Symbol</th><th>Unit</th><th>Values</th></tr><tr><td>Peak Wavelength</td><td>λ_{peak}</td><td>typ.</td><td>472 nm</td></tr><tr><td>Dominant Wavelength ²⁾</td><td>λ_{dom}</td><td>min.</td><td>440 nm</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>475 nm</td></tr><tr><td></td><td></td><td>max.</td><td>480 nm</td></tr><tr><td>Spectral Bandwidth at 50% $I_{\text{rel,max}}$</td><td>$\Delta\lambda$</td><td>typ.</td><td>20 nm</td></tr><tr><td>Viewing angle at 50% I_V</td><td>2ϕ</td><td>typ.</td><td>120 °</td></tr><tr><td>Forward Voltage ³⁾</td><td>V_F</td><td>min.</td><td>2.65 V</td></tr><tr><td>$I_F = 350 \text{ mA}$</td><td></td><td>typ.</td><td>2.90 V</td></tr><tr><td></td><td></td><td>max.</td><td>3.25 V</td></tr><tr><td>Reverse voltage (ESD device)</td><td>V_{RESD}</td><td>min.</td><td>5 V</td></tr><tr><td>Reverse voltage ⁴⁾</td><td>V_R</td><td>max.</td><td>7 V</td></tr><tr><td>$I_R = 5 \text{ mA}$</td><td></td><td></td><td></td></tr><tr><td>Real thermal resistance junction/solderpoint ⁵⁾</td><td>$R_{\text{thJS real}}$</td><td>typ.</td><td>7.8 K / W</td></tr><tr><td></td><td></td><td>max.</td><td>9.4 K / W</td></tr><tr><td>Electrical thermal resistance junction/solderpoint ⁵⁾ with efficiency $\eta_a = 56 \%$</td><td>$R_{\text{thJS elec.}}$</td><td>typ.</td><td>3.4 K / W</td></tr><tr><td></td><td></td><td>max.</td><td>4.1 K / W</td></tr></table></div>	Parameter	Symbol	Unit	Values	Peak Wavelength	λ_{peak}	typ.	472 nm	Dominant Wavelength ²⁾	λ_{dom}	min.	440 nm	$I_F = 350 \text{ mA}$		typ.	475 nm			max.	480 nm	Spectral Bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	20 nm	Viewing angle at 50% I_V	2ϕ	typ.	120 °	Forward Voltage ³⁾	V_F	min.	2.65 V	$I_F = 350 \text{ mA}$		typ.	2.90 V			max.	3.25 V	Reverse voltage (ESD device)	V_{RESD}	min.	5 V	Reverse voltage ⁴⁾	V_R	max.	7 V	$I_R = 5 \text{ mA}$				Real thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS real}}$	typ.	7.8 K / W			max.	9.4 K / W	Electrical thermal resistance junction/solderpoint ⁵⁾ with efficiency $\eta_a = 56 \%$	$R_{\text{thJS elec.}}$	typ.	3.4 K / W			max.	4.1 K / W
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Introduction of next chip generation for OSOLON Signal devices

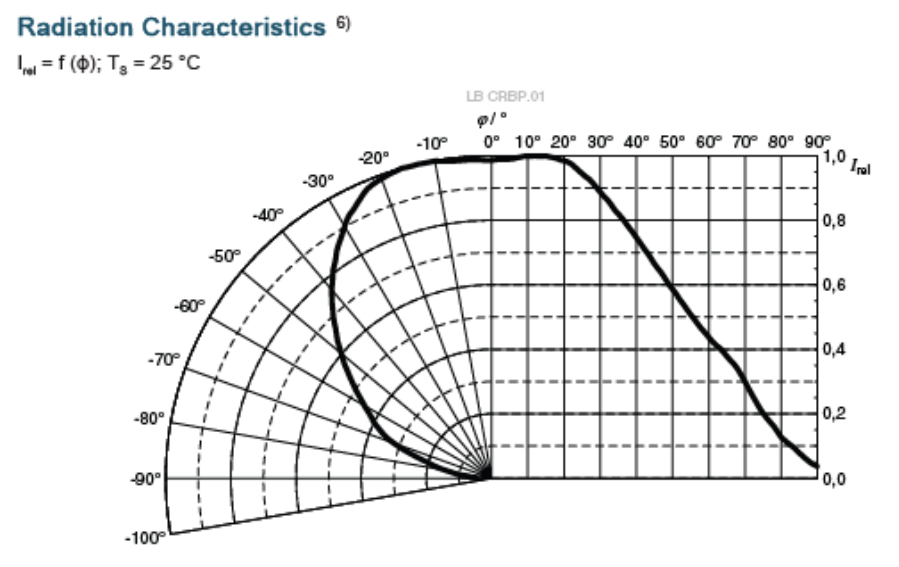
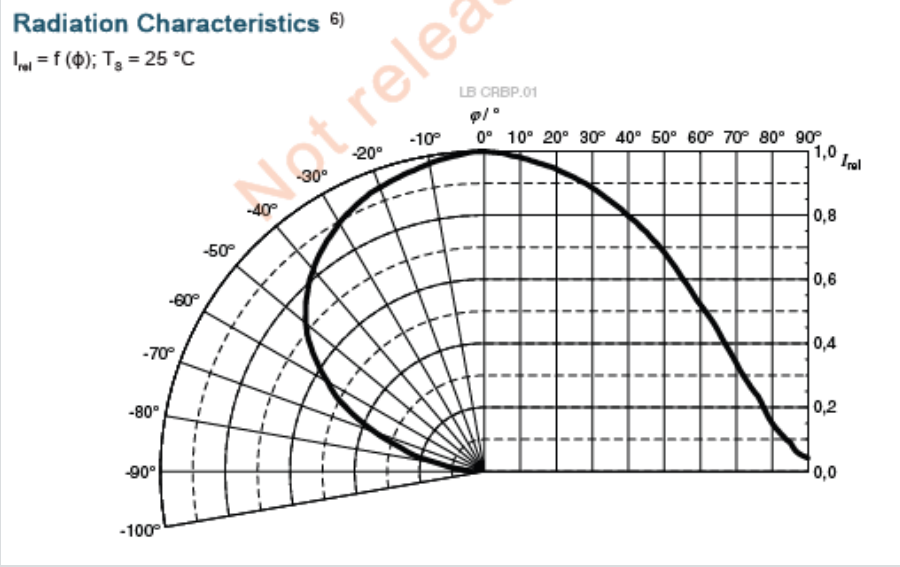
Changes in the datasheets for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 (The examples below are for LB CRBP.01. Regarding details for LCY CRBP.01 and LUW CRBP.01 please refer to the updated datasheets)

Item	Current status	New status
Relative Spectral Emission	<div> <div> Relative Spectral Emission⁶⁾ $\Phi_{rel} = f(\lambda); I_F = 350\text{ mA}; T_s = 25\text{ °C}$ </div> <div> </div> </div>	<div> <div> Relative Spectral Emission⁶⁾ $\Phi_{rel} = f(\lambda); I_F = 350\text{ mA}; T_s = 25\text{ °C}$ </div> <div> </div> </div>

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Introduction of next chip generation for OSOLON Signal devices

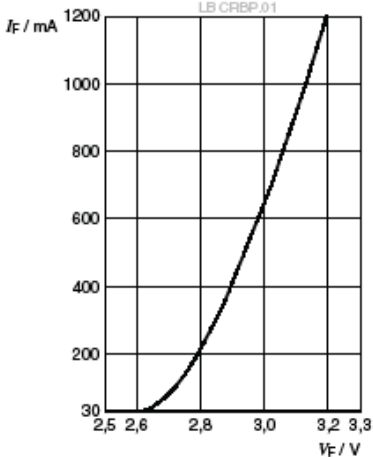
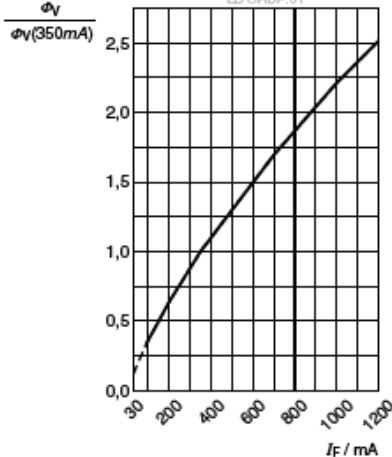
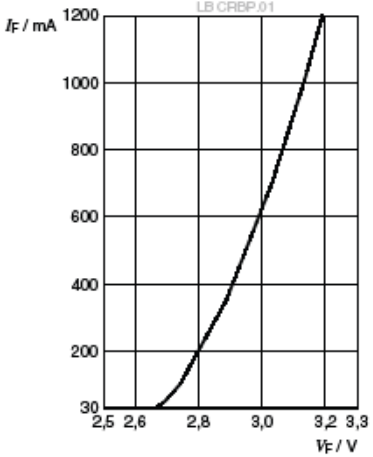
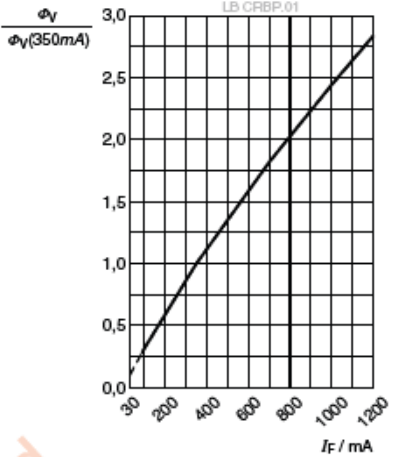
Changes in the datasheets for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 (The examples below are for LB CRBP.01. Regarding details for LCY CRBP.01 and LUW CRBP.01 please refer to the updated datasheets)

Item	Current status	New status
Radiation Characteristics	<div><p>Radiation Characteristics ⁶⁾</p><p>$I_{rel} = f(\phi); T_s = 25\text{ °C}$</p><p>LB CRBP.01</p></div>	<div><p>Radiation Characteristics ⁶⁾</p><p>$I_{rel} = f(\phi); T_s = 25\text{ °C}$</p><p>LB CRBP.01</p></div>

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Introduction of next chip generation for OSOLON Signal devices

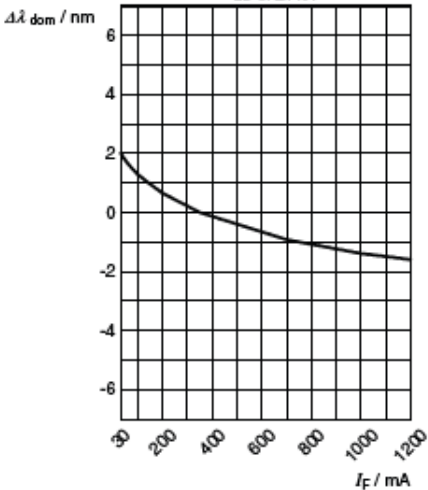
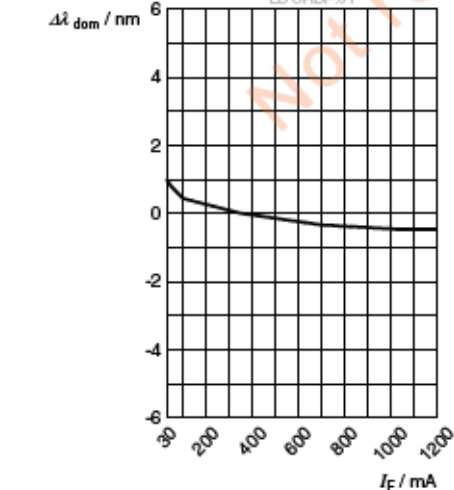
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Item	Current status	New status
Forward current & Relative Luminous Flux	<div> <div> Forward current ⁶⁾ $I_F = f(V_F); T_s = 25\text{ °C}$  </div> <div> Relative Luminous Flux ^{6), 7)} $\Phi_V / \Phi_V(350\text{ mA}) = f(I_F); T_s = 25\text{ °C}$  </div> </div>	<div> <div> Forward current ⁶⁾ $I_F = f(V_F); T_s = 25\text{ °C}$  </div> <div> Relative Luminous Flux ^{6), 7)} $\Phi_V / \Phi_V(350\text{ mA}) = f(I_F); T_s = 25\text{ °C}$  </div> </div>

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Changes in the datasheets for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 (The examples below are for LB CRBP.01. Regarding details for LCY CRBP.01 and LUW CRBP.01 please refer to the updated datasheets)

Item	Current status	New status
Dominant Wavelength	<div><p>Dominant Wavelength ⁶⁾</p><p>$\Delta\lambda_{\text{dom}} = f(I_F); T_s = 25\text{ °C}$</p><p>LB CRBP.01</p></div>	<div><p>Dominant Wavelength ⁶⁾</p><p>$\Delta\lambda_{\text{dom}} = f(I_F); T_s = 25\text{ °C}$</p><p>LB CRBP.01</p></div>

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Introduction of next chip generation for OSOLON Signal devices

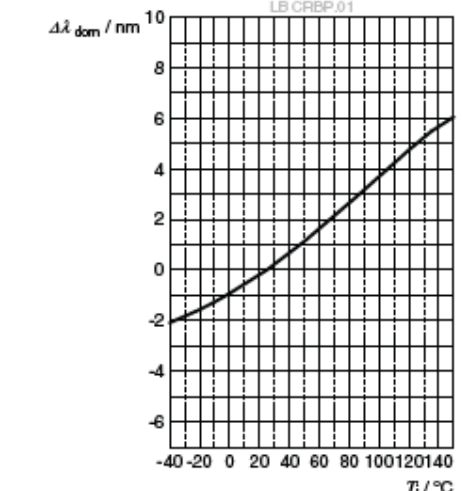
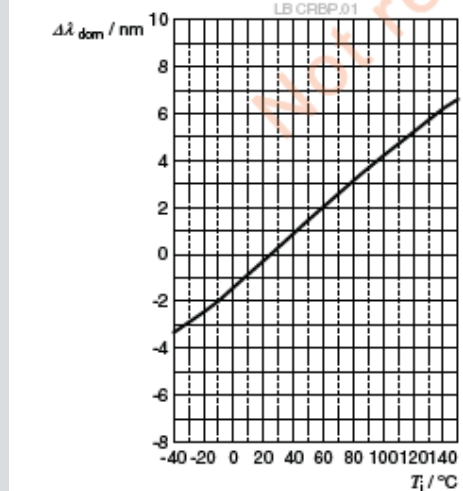
Changes in the datasheets for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 (The examples below are for LB CRBP.01. Regarding details for LCY CRBP.01 and LUW CRBP.01 please refer to the updated datasheets)

Item	Current status	New status
Forward Voltage & Relative Luminous Flux	<div> <div> Forward Voltage ⁶⁾ $\Delta V_F = V_F - V_F(25\text{ }^{\circ}\text{C}) = f(T_j); I_F = 350\text{ mA}$ </div> <div> Relative Luminous Flux ⁶⁾ $\Phi_v / \Phi_v(25\text{ }^{\circ}\text{C}) = f(T_j); I_F = 350\text{ mA}$ </div> </div>	<div> <div> Forward Voltage ⁶⁾ $\Delta V_F = V_F - V_F(25\text{ }^{\circ}\text{C}) = f(T_j); I_F = 350\text{ mA}$ </div> <div> Relative Luminous Flux ⁶⁾ $\Phi_v / \Phi_v(25\text{ }^{\circ}\text{C}) = f(T_j); I_F = 350\text{ mA}$ </div> </div>

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Introduction of next chip generation for OSOLON Signal devices

Changes in the datasheets for LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 (The examples below are for LB CRBP.01. Regarding details for LCY CRBP.01 and LUW CRBP.01 please refer to the updated datasheets)

Item	Current status	New status
Dominant Wavelength	<div><p>Dominant Wavelength ⁶⁾</p><p>$\Delta\lambda_{dom} = \lambda_{dom} - \lambda_{dom}(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p><p>LB CRBP.01</p></div>	<div><p>Dominant Wavelength ⁶⁾</p><p>$\Delta\lambda_{dom} = \lambda_{dom} - \lambda_{dom}(25\text{ °C}) = f(T_j); I_F = 350\text{ mA}$</p><p>LB CRBP.01</p></div>

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Introduction of next chip generation for OSOLON Signal devices

Changes in the datasheets: Updated Datasheet Version

Product type	Data sheet version <u>before PCN</u>	Data sheet version <u>after PCN</u>
LB CRBP.01	1.2	1.3
LCY CRBP.01	1.5	1.6
LUW CRBP.01	1.3	1.4
LJ CRBP.01	1.3	1.4

Note: After PCN approval and shipment of new material, the new data sheet versions will be valid.
Latest version of data sheet is accessible on the ams OSRAM homepage.

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Introduction of next chip generation for OSOLON Signal devices

List of affected products



OSOLON Signal
LB CRBP.01
LCY CRBP.01
LUW CRBP.01
LJ CRBP.01

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Introduction of next chip generation for OSOLON Signal devices

PCN Samples

OSOLON Signal
LB CRBP.01
LCY CRBP.01
LUW CRBP.01
LJ CRBP.01

Color code:  available  on request

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Introduction of next chip generation for OSOLON Signal devices

Time schedule

for PCN material (<u>after</u> implementation of change):		
Final qualification report	03.04.2023	
Samples available	On request	
Intended Start of delivery	01.07.2023 *)	*) or earlier if released by customer and upon mutual agreement

for Pre-PCN material (<u>prior to</u> implementation of change):		
Last time order date (LTO)	01.07.2023 **)	**) Lead time and LTO quantity shall be mutually agreed between ams OSRAM and customer.
Last time delivery date (LTD)	02.10.2023 ***)	***) planned last date for delivery of products of current status

Note:

Pre-PCN material: Products of current status, means before implementation of the changes as described in the PCN.

PCN material: Products with implementation of the changes as described in the PCN.

Sensing is life



Qualification Report 230025C1

Subject	Qualification report for OSOLON Signal LJ CRBP.01 according to OS-PCN-2023-030-A
Date	15.03.2023
Tested device	LJ CRBP.01
Brand (including sub brands)	OSOLON Signal
Applies to	LJ CRBP.01

Pre-conditioning according to Jedec Level 2

Test Performed		Condition	Duration	Sample Size	Failures		
					El.	Opt.	Vis
Wet High Temperature Operating Life	<i>JESD22-A101</i>	$T_A = 60^{\circ}\text{C}$; r.H.= 93% $I_F = 30\text{mA}$	1000h	4x30	0	0	0
WHTOL							
Wet High Temperature Operating Life	<i>JESD22-A101</i>	$T_A = 60^{\circ}\text{C}$; r.H.= 93% $I_F = 1000\text{mA}$ 30min on / 30min off	1000h	4x30	0	0	0
WHTOL							
Temperature Cycling	<i>JESD22-A104</i>	$T_A = -40^{\circ}\text{C}/+125^{\circ}\text{C}$ 15min each extreme	1000c	4x30	0	0	0
TC							
Damp heat cyclic	<i>IEC 60068-2-30</i>	$T_{A,\text{min}} = 25^{\circ}\text{C}$ $T_{A,\text{max}} = 65^{\circ}\text{C}$ r.H.= 90%; $I_F = 30\text{mA}$	10c	4x30	0	0	0
High Temperature Operating Life	<i>JESD22-A108</i>	$T_A = 110^{\circ}\text{C}$ $I_F = 1000\text{mA}$	1000h	4x30	0	0	0
HTOL							
High Temperature Operating Life	<i>JESD22-A108</i>	$T_A = 125^{\circ}\text{C}$ $I_F = 600\text{mA}$	1000h	4x30	0	0	0
HTOL							
Low Temperature Operating Life	<i>JESD22-A108</i>	$T_A = -40^{\circ}\text{C}$ $I_F = 1000\text{mA}$	1000h	4x30	0	0	0
LTOL							
Pulsed Operating Life	<i>JESD22-A108</i>	$T_A = 25^{\circ}\text{C}$ $I_F = 1500\text{mA}$; $t_p = 0.1\text{ms}$ $D = 3\%$	1000h	4x30	0	0	0
PLT							
Electrostatic Discharge							
HBM	<i>ANSI/ESDA/ JEDEC JS-001</i>	Human Body Model	2000V	4x30	0	0	0

Note: Lot A-C evaluation lot, Lot D control lot

Failure criteria:

Electrical failures: V_f ($I_f = 350\text{mA}$) $> 2.35\text{V}$; $\pm 10\%$ from initial value

Optical failures: I_v ($I_f = 350\text{mA}$) $> \pm 30\%$ from initial value

Visual failures: acc JEDEC JESD22-B101

Conclusion: The tested device fulfills the reliability requirements.

Disclaimer

PLEASE CAREFULLY READ THE BELOW TERMS AND CONDITIONS BEFORE USING THE INFORMATION.
IF YOU DO NOT AGREE WITH ANY OF THESE TERMS AND CONDITIONS, DO NOT USE THE INFORMATION.

The Information contained in this Document does not constitute an independent warranty. The committed behavior is described in the Product data sheet and/or further, mutually agreed specifications.

Distribution of part or all of the contents of this Document to any 3rd party in any form without the prior permission of ams-OSRAM International GmbH is prohibited except in accordance with applicable mandatory law.

Further explanations:

Data: The Data used in this Document consider the reliability test results under the mentioned driving conditions only. For Product information on the maximum operating conditions and the OSRAM standard qualification profile please refer to the Product data sheet or contact your local sales partner.

Conditions: The conditions for the generation of the Data are as follows:

1. The Data and curves shown in this Document are based on experiments carried out under laboratory conditions on a random sample size of LED/IRED/Laser/Detector with readouts at discrete readout times (where applicable). Thus, the Data above represent a limited number of production lots only and may differ between different assembly lots over time (including chip or package changes). Thus, the behavior of the LED/IRED/Laser/Detector in the final application may differ from the Data. The behavior of the LED/IRED/Laser/Detector at conditions or readout times deviating from those stated above may not be deduced from the Data.

2. If applicable:

a) Extended driving conditions:

The tested driving conditions exceed the maximum limits stated in the Product data sheet. Therefore, a reduced lifetime or an accelerated degradation is expected. Failure limits noted in the Document refer to the testing condition according to the OSRAM standard Product qualification profile and not to the actual testing condition.

b) Extended testing duration:

The testing duration exceed the OSRAM standard qualification profile of the mentioned Product. Failure limits noted in the Document refer to the testing duration according to the OSRAM standard Product qualification profile and not to the actual testing duration.

c) Exceeding standard qualification conditions – (Product data sheet limits not affected):

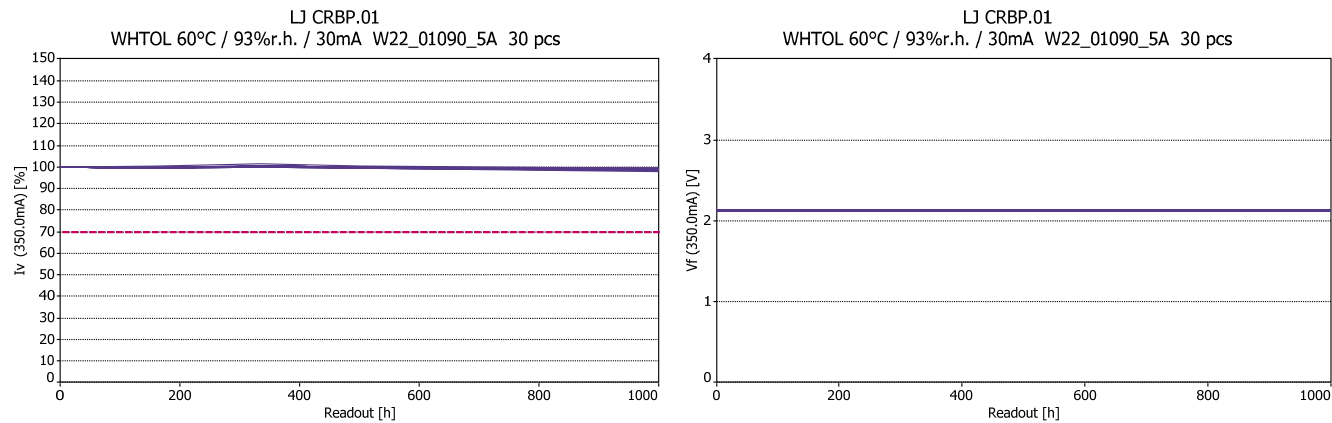
The tested driving conditions exceed the OSRAM standard qualification profile of the mentioned Product. Therefore a reduced lifetime or an accelerated degradation is expected. Failure limits noted in the Document refer to the testing condition according to the OSRAM standard Product qualification profile and not to the actual testing condition.

3. For long term operation additional failure modes of the chip or package can occur which are not shown in this Document.

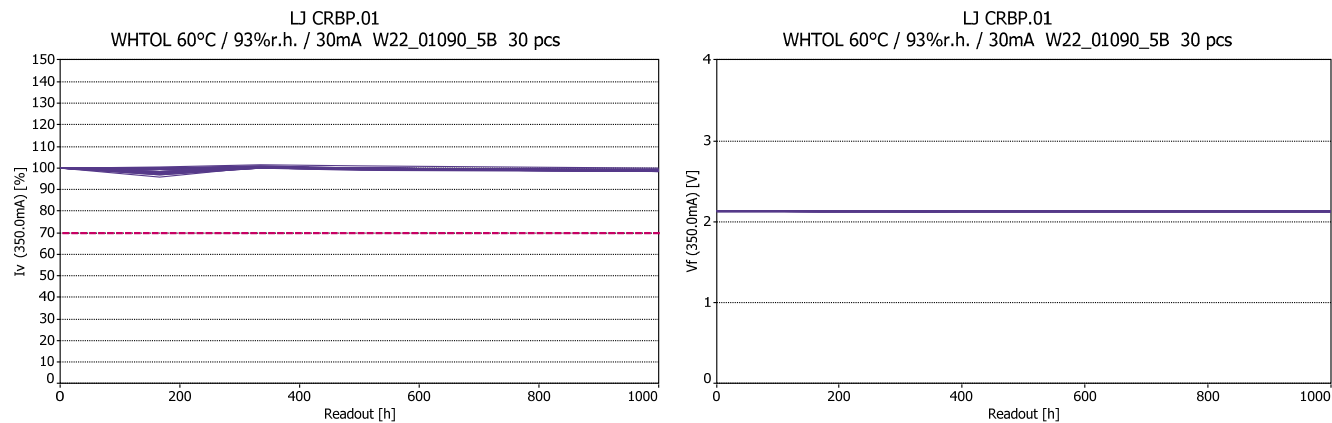
4. Possible differences in the thermal management of OSRAM and customer's setup may lead to a different aging behavior.

WHTOL 60°C / 93% r.H./ 30mA

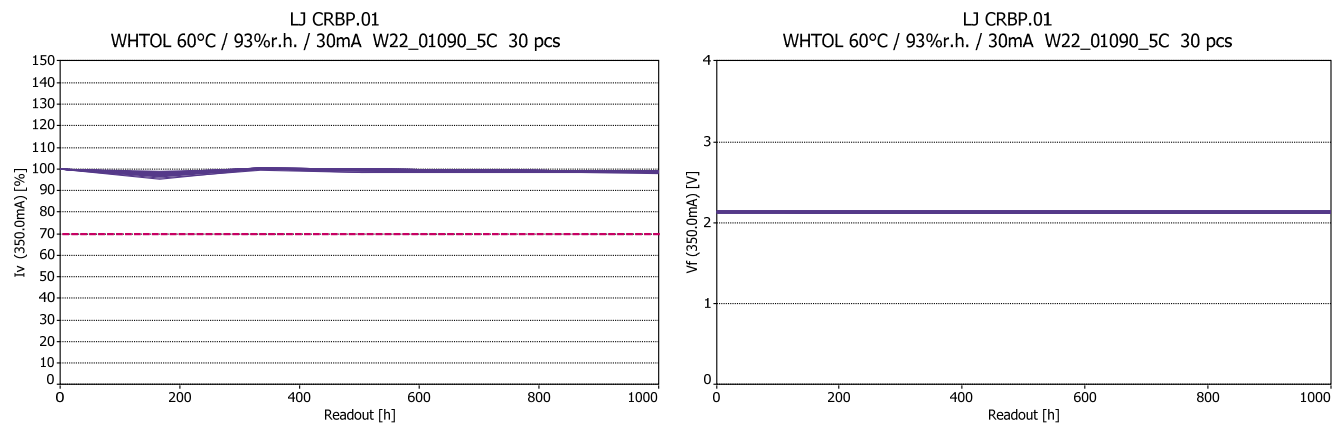
Lot A



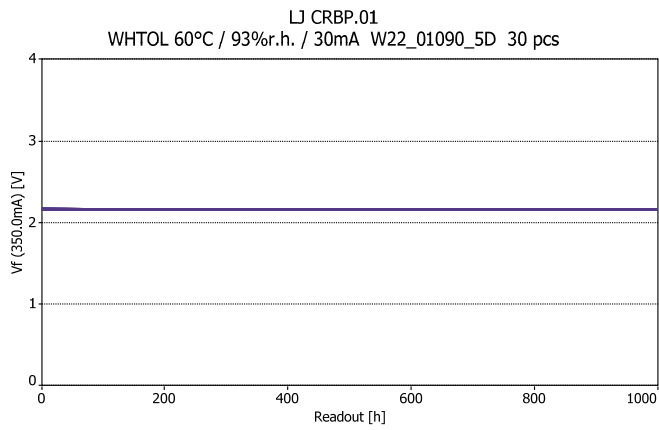
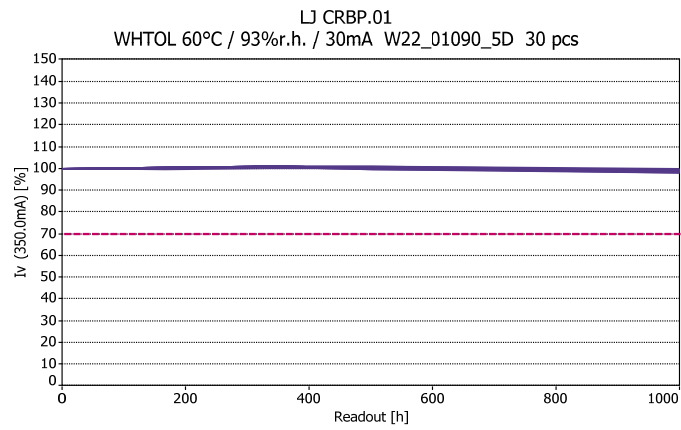
Lot B



Lot C

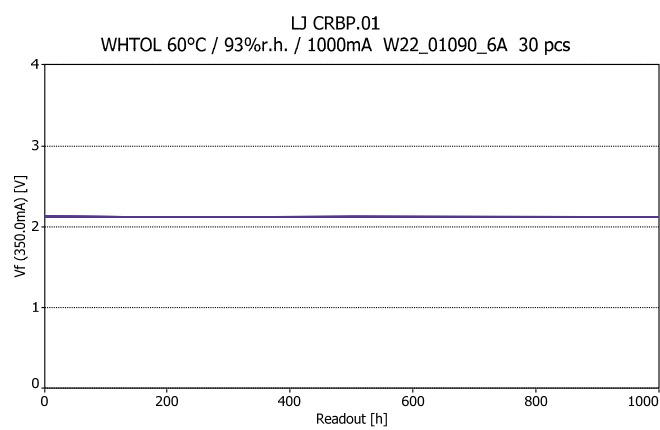
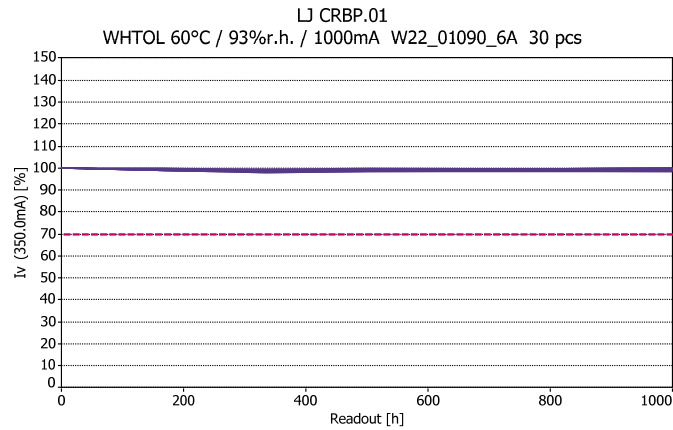


Lot D

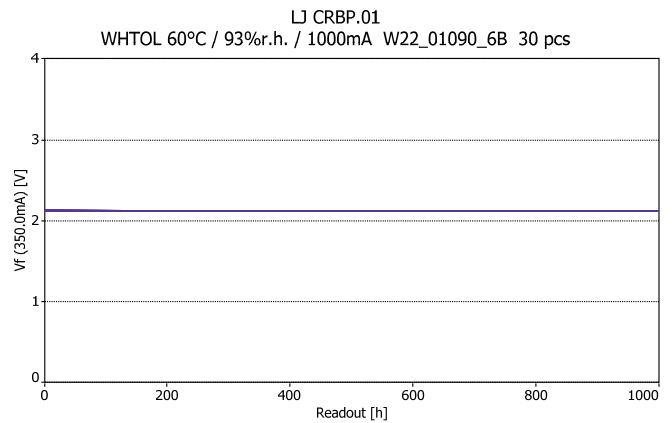
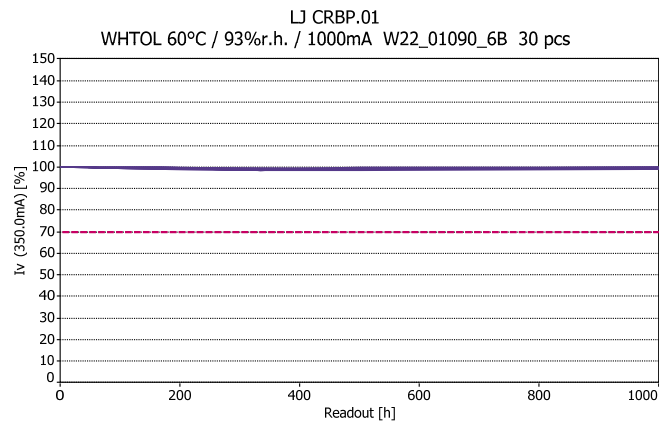


WHTOL 60°C / 93% r.H./ 1000mA

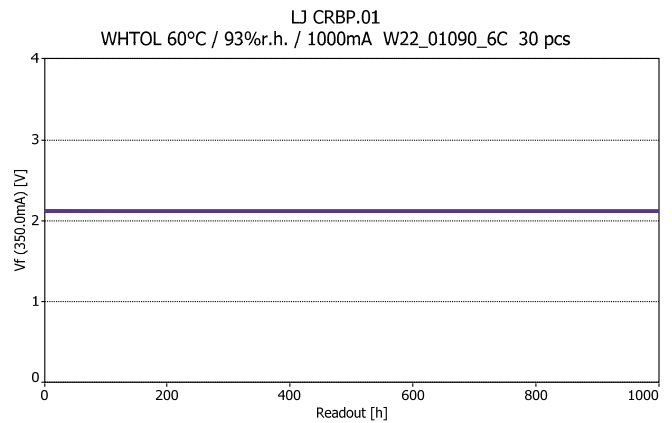
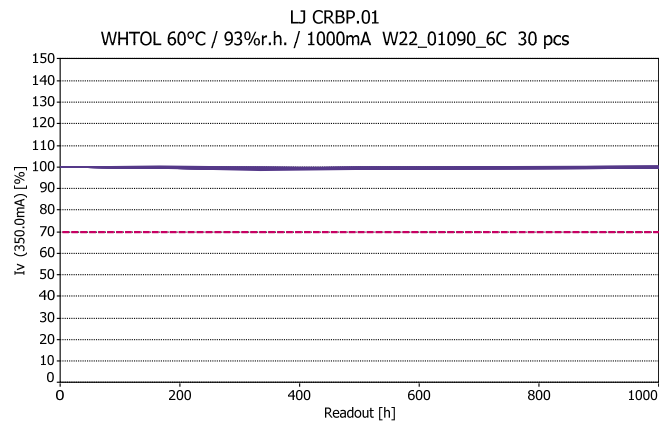
Lot A



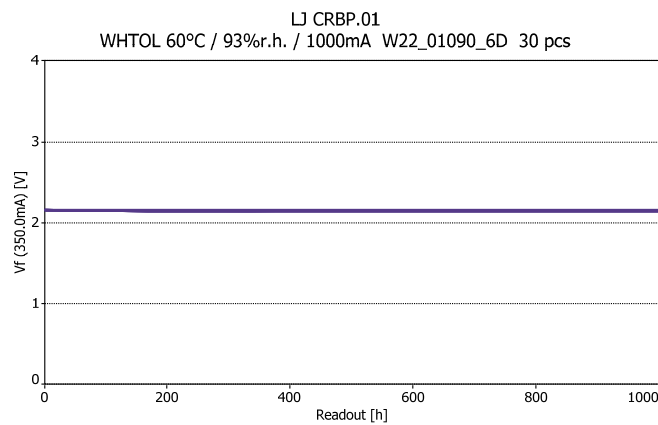
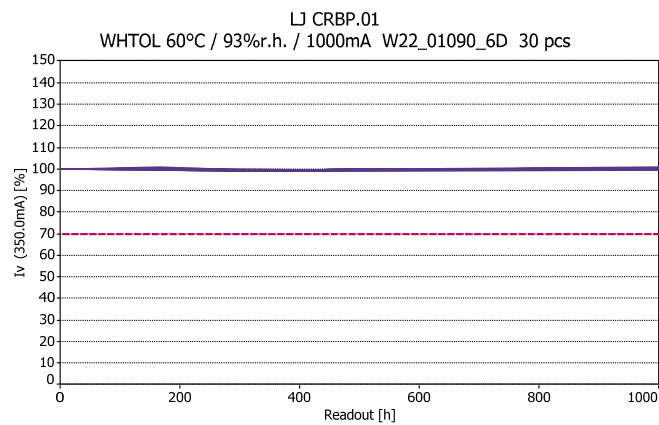
Lot B



Lot C

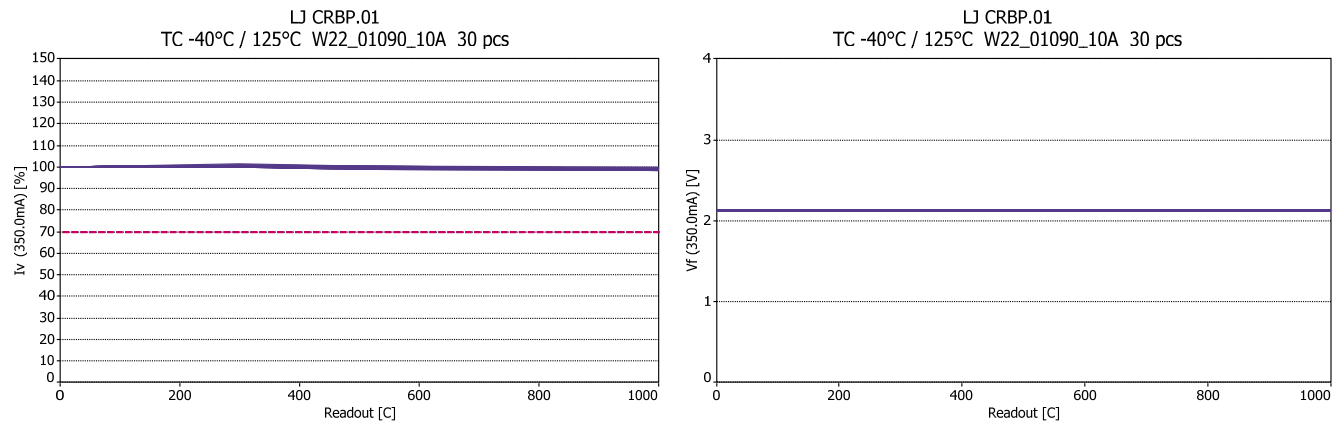


Lot D

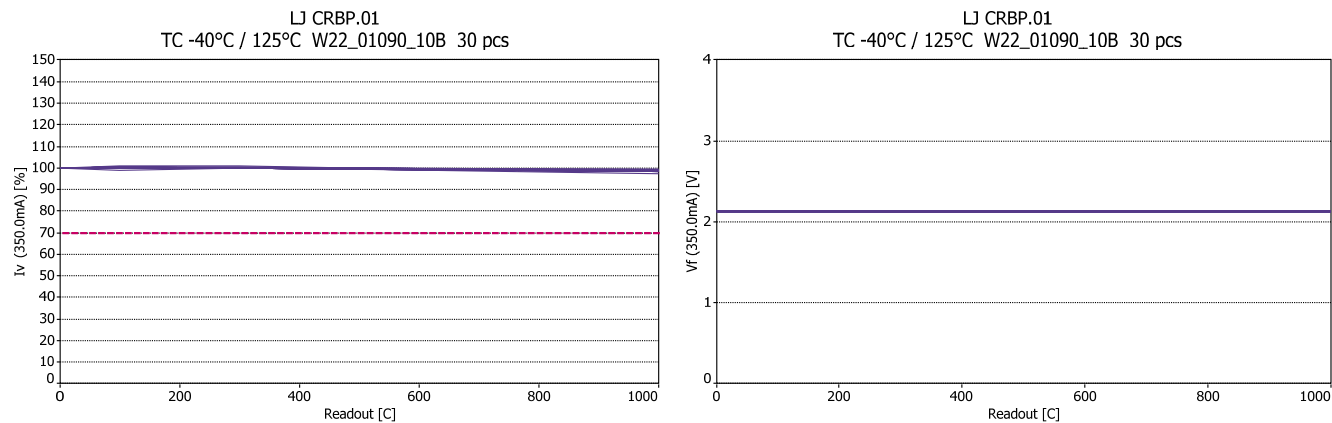


TC -40°C/125°C

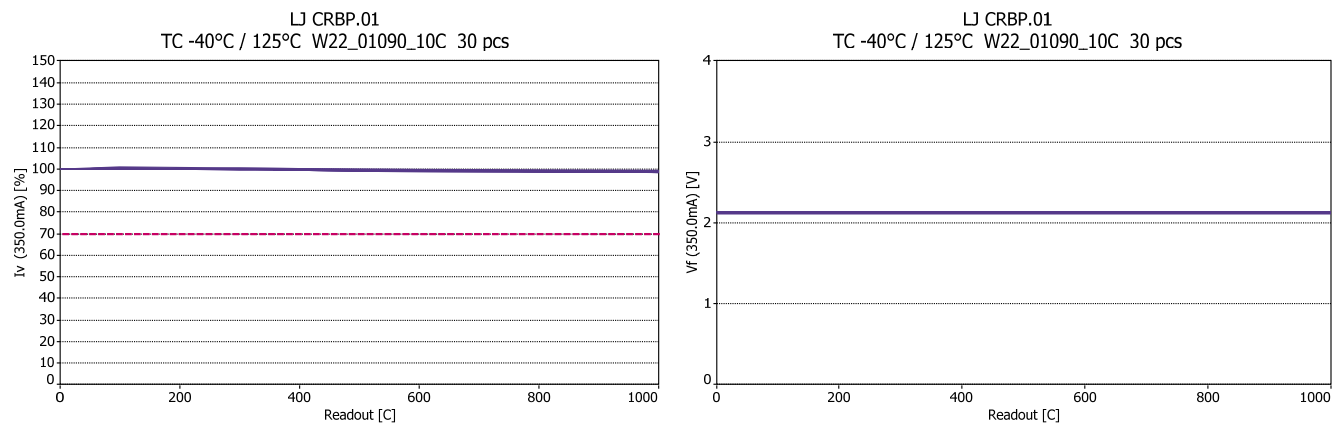
Lot A



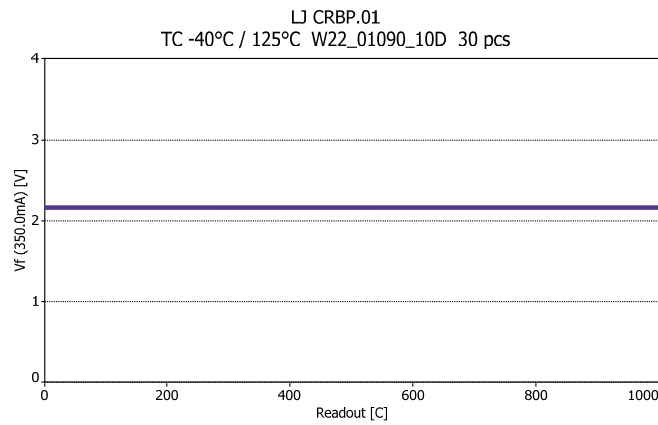
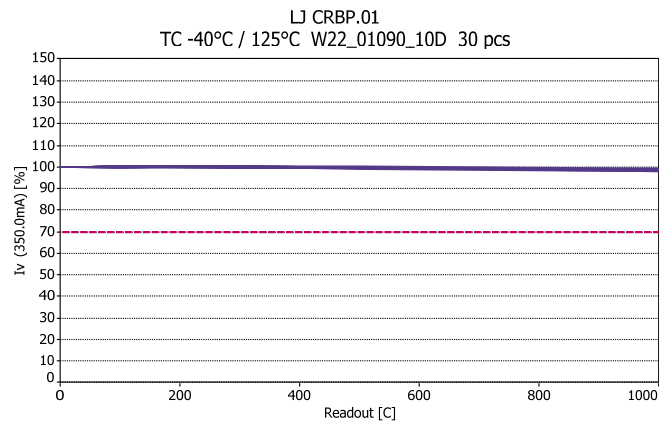
Lot B



Lot C

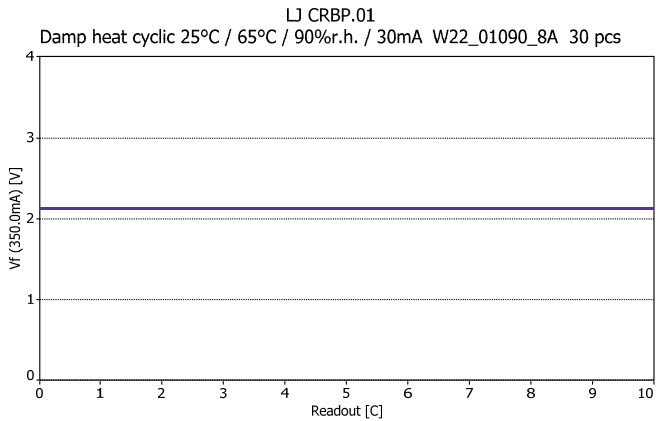
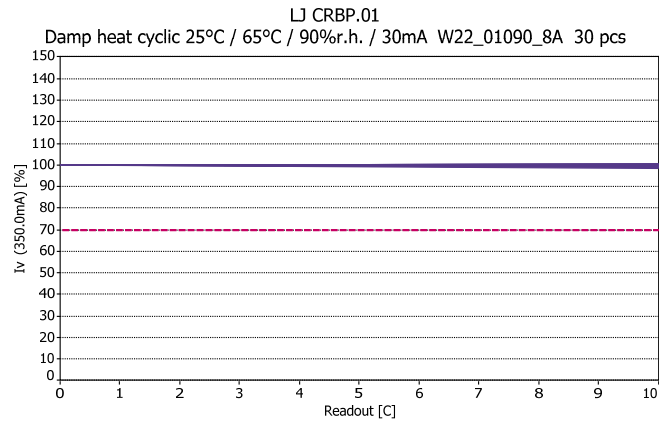


Lot D

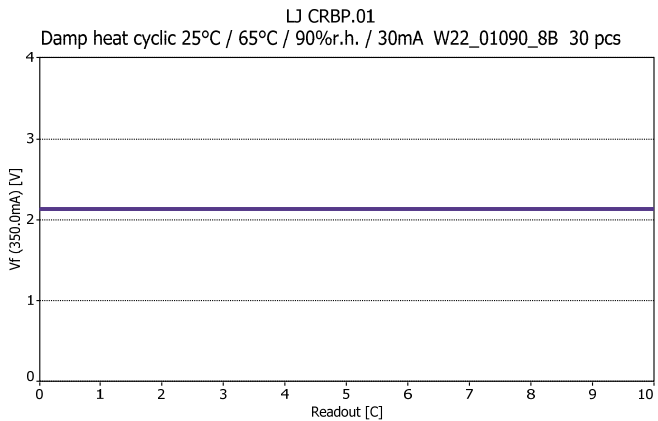
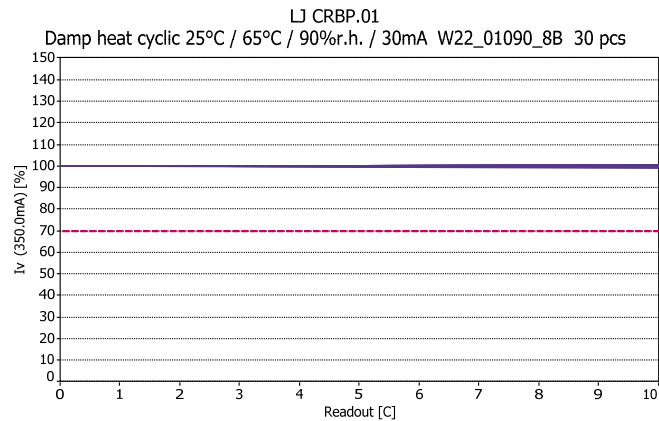


Damp heat cyclic 25°C / 65°C / 90% r.h. / 30mA

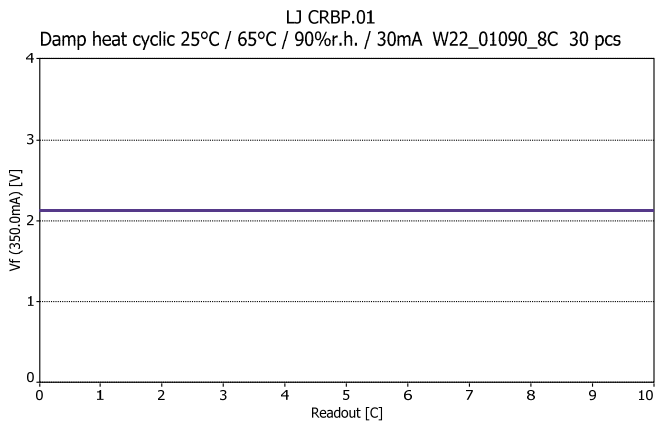
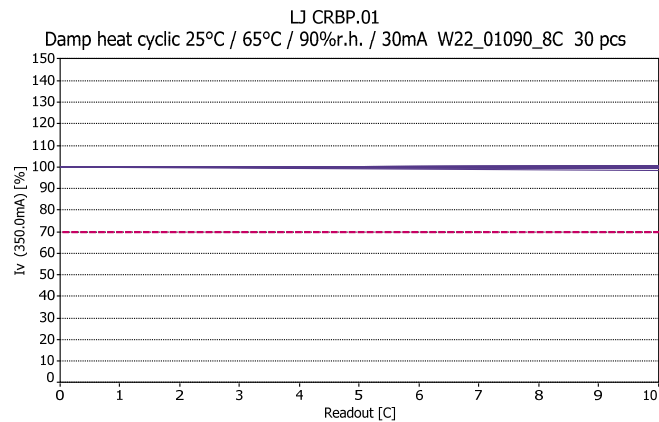
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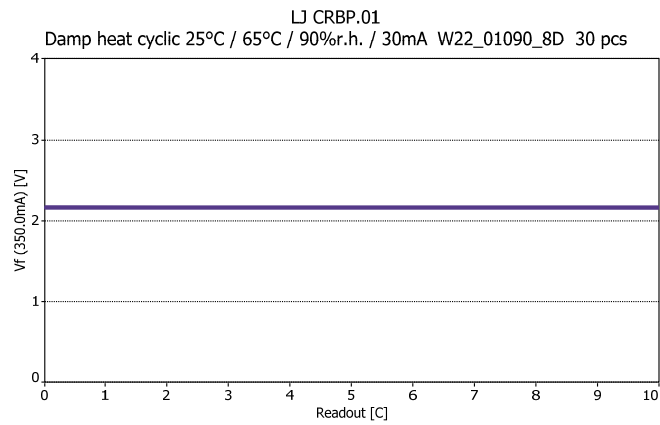
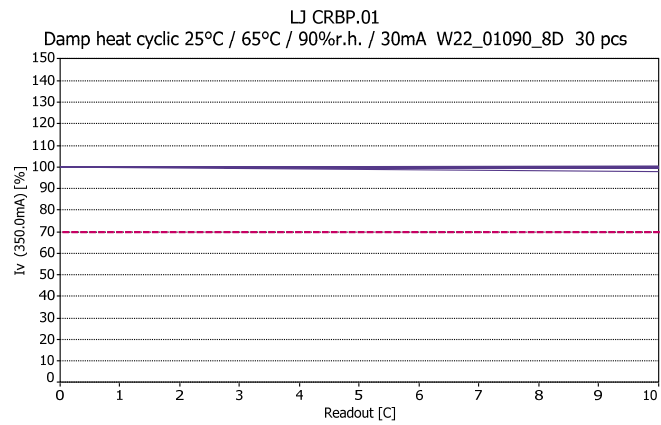
Lot B



Lot C

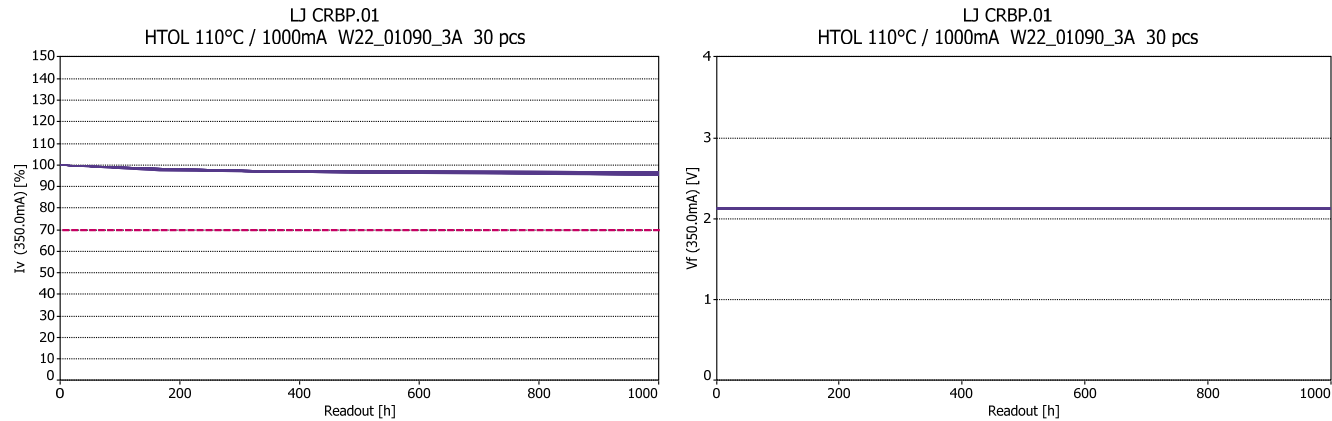


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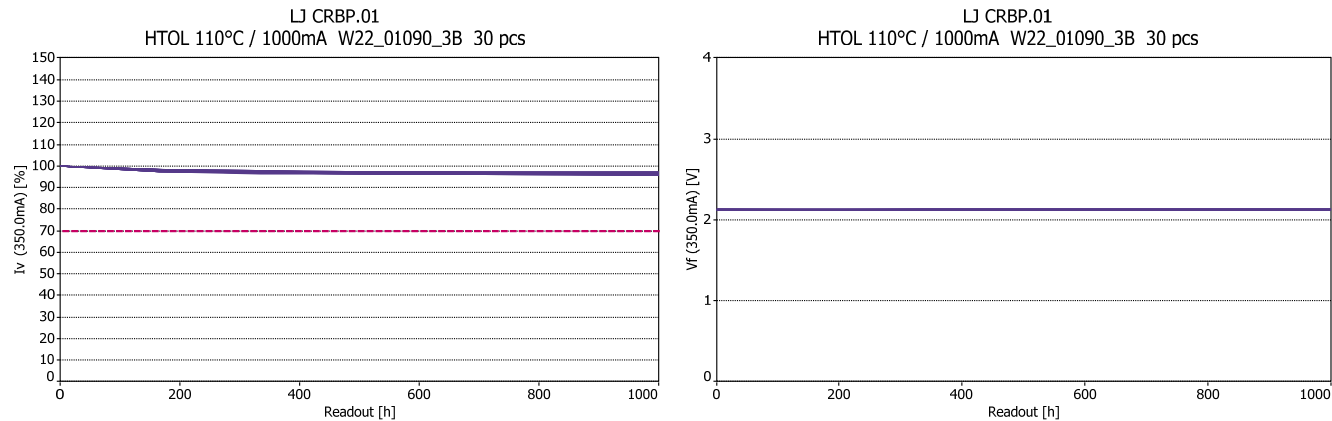


HTOL 110°C / 1000mA

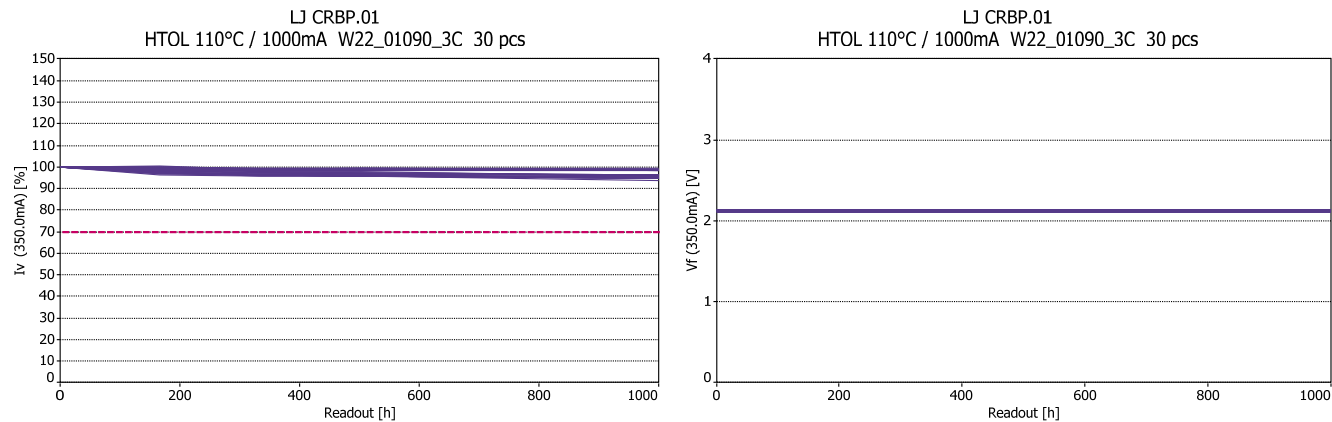
Lot A



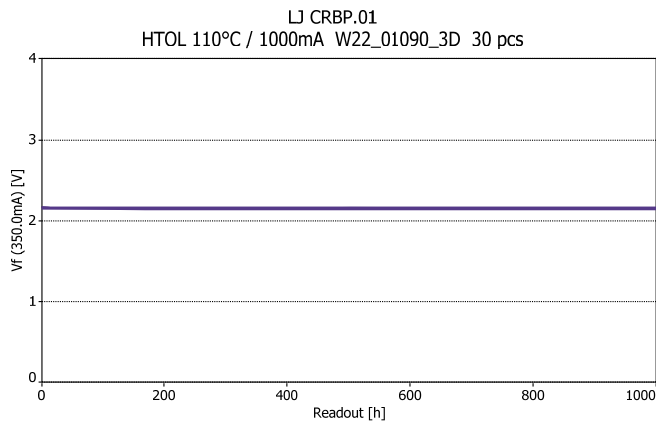
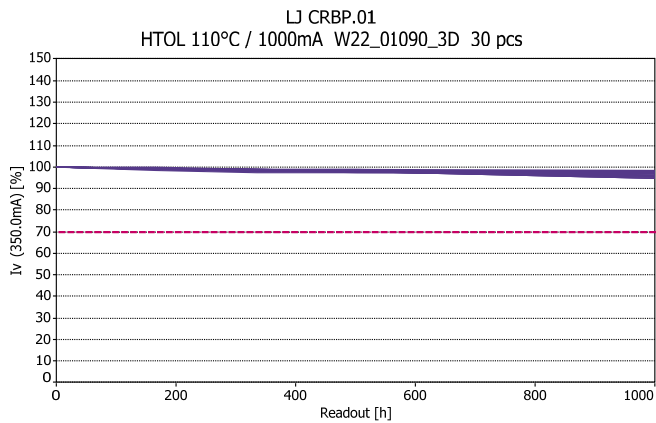
Lot B



Lot C

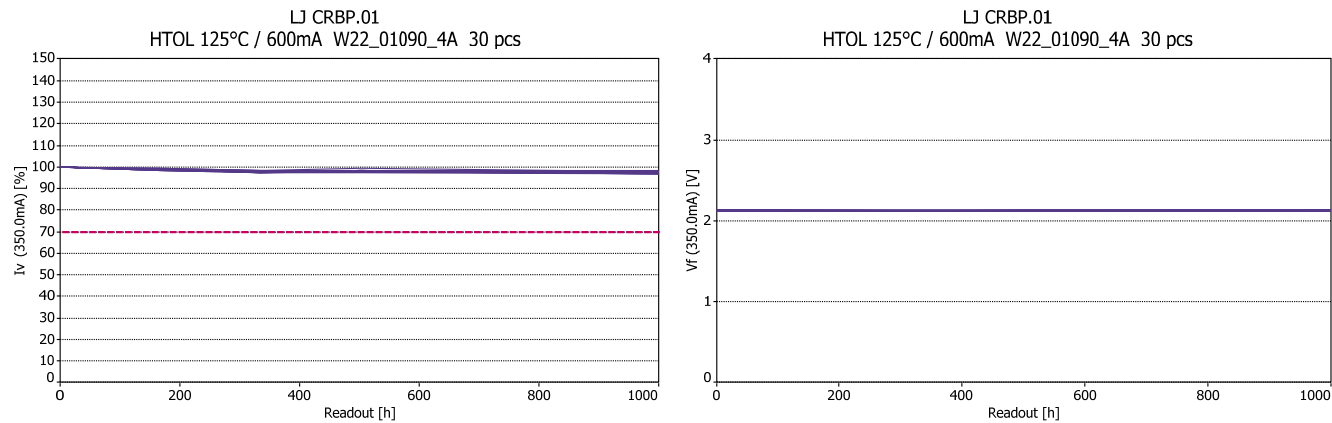


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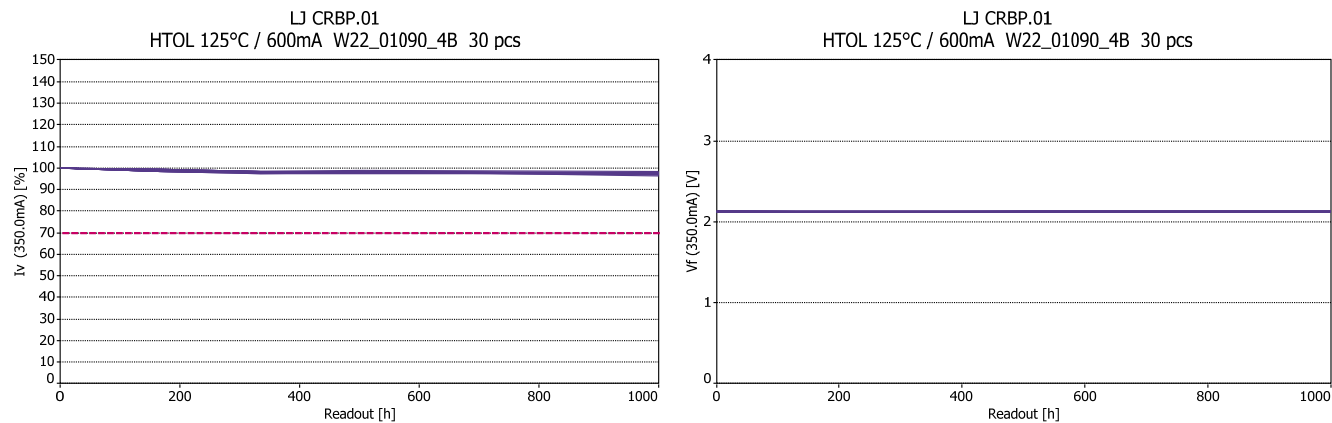


HTOL 125°C / 600mA

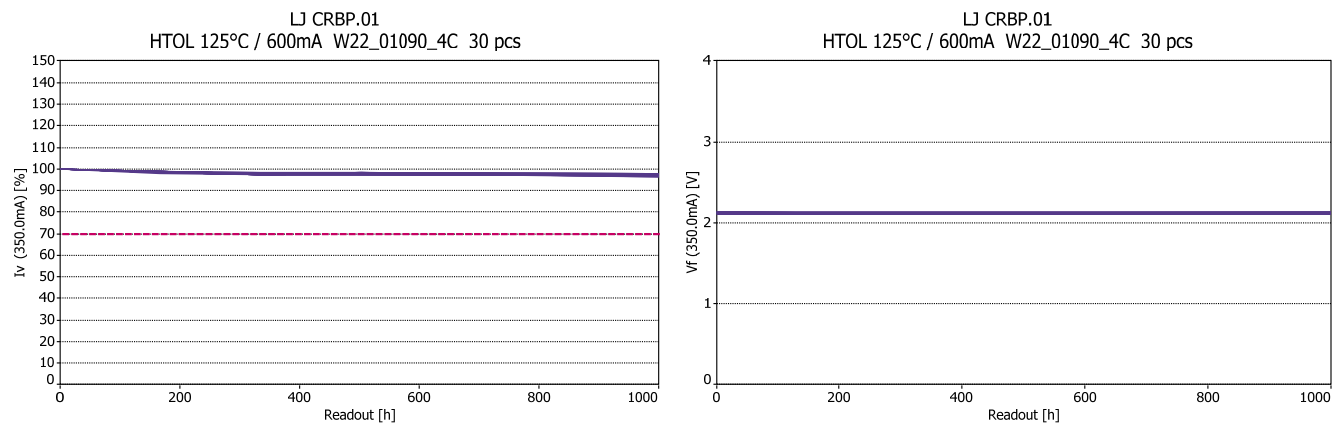
Lot A



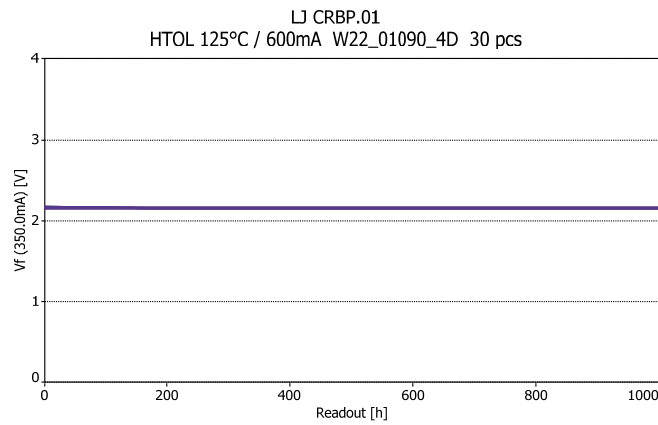
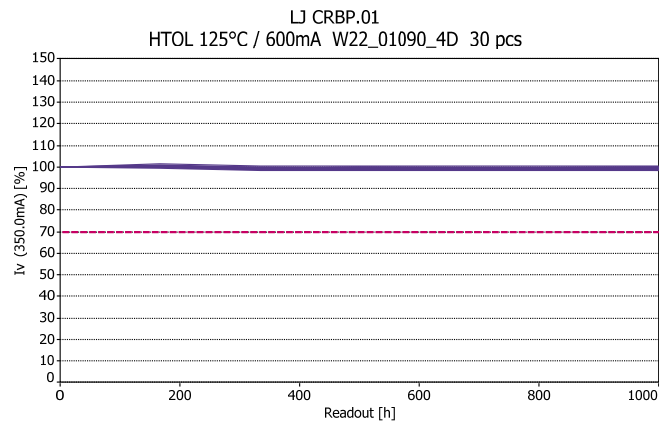
Lot B



Lot C

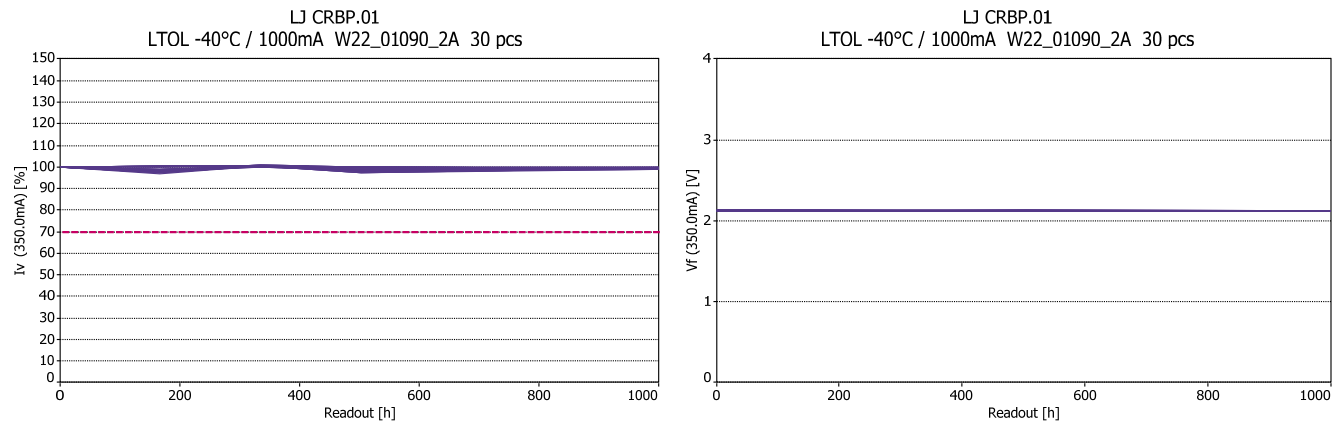


Lot D

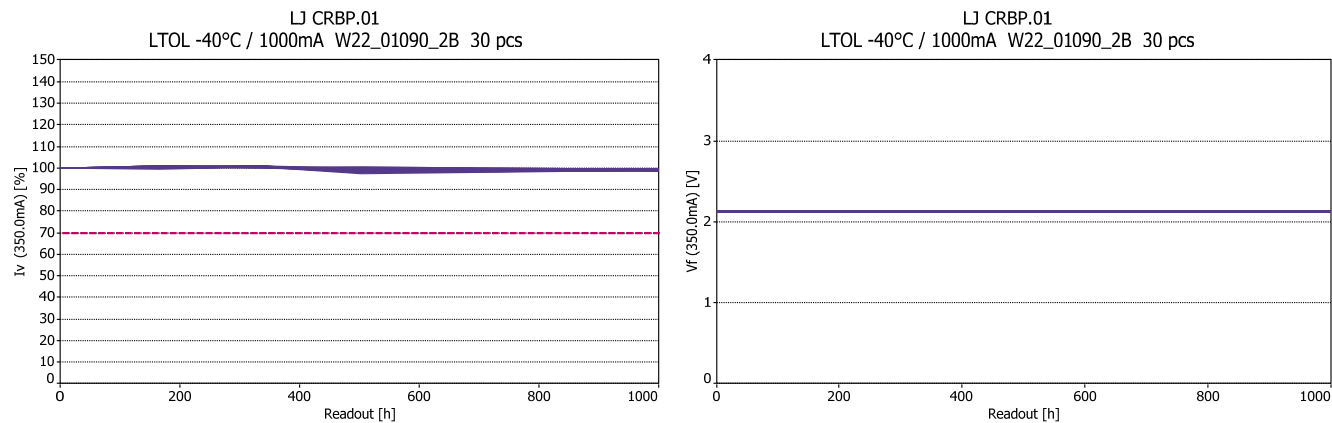


LTOL -40°C / 1000mA

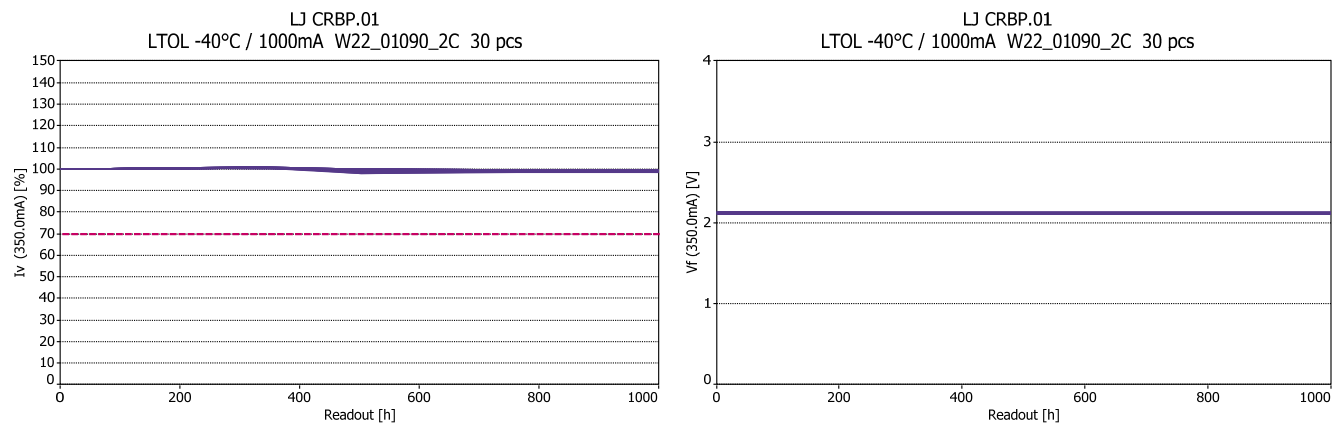
Lot A



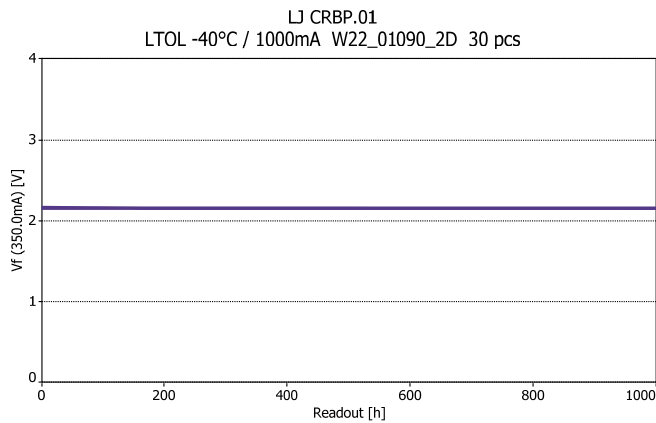
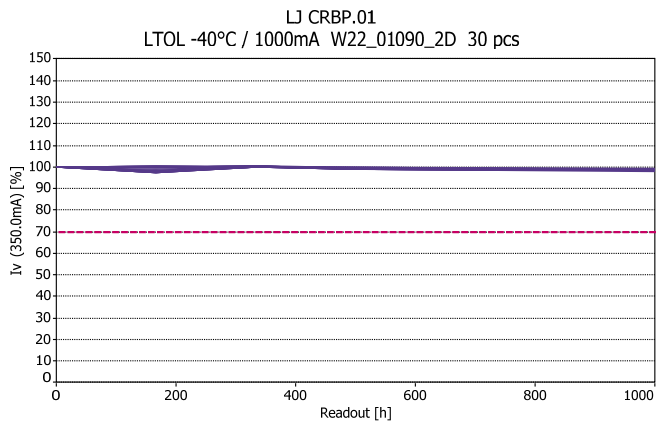
Lot B



Lot C

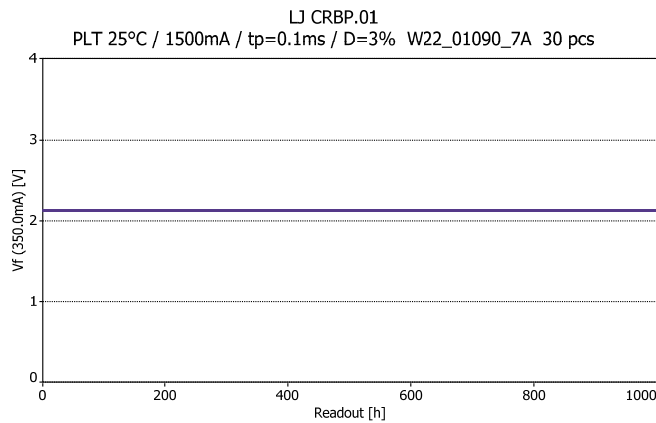
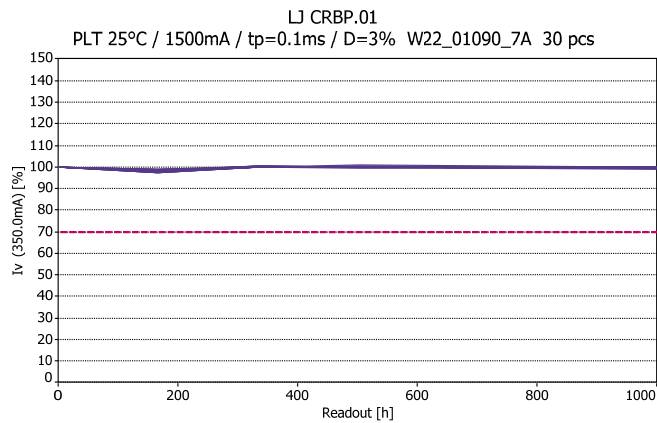


Lot D

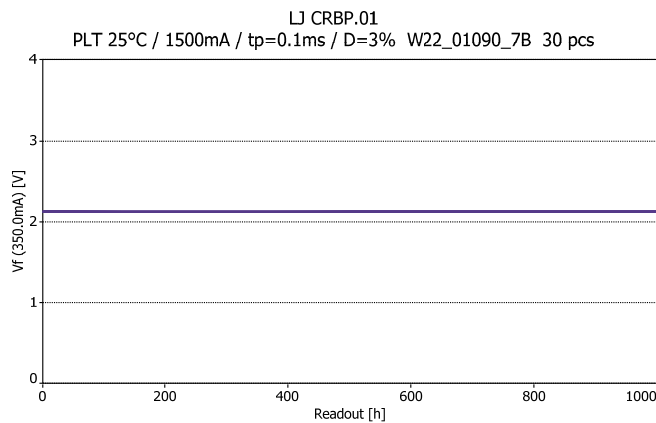
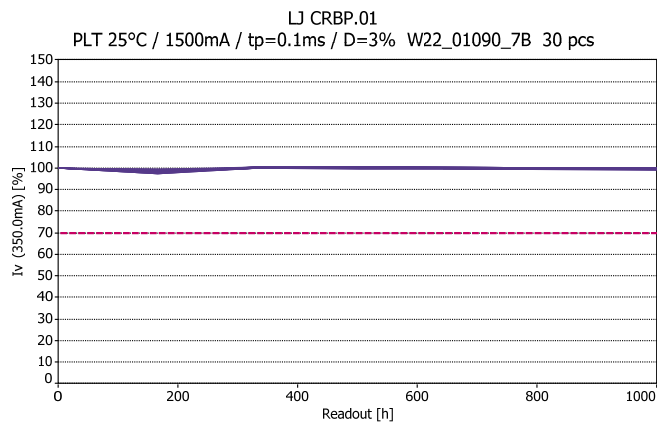


PLT 25°C / 1500mA / tp=0,1ms / D =3%

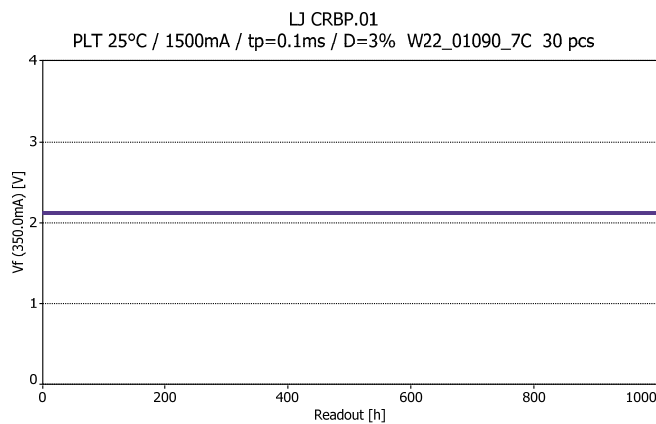
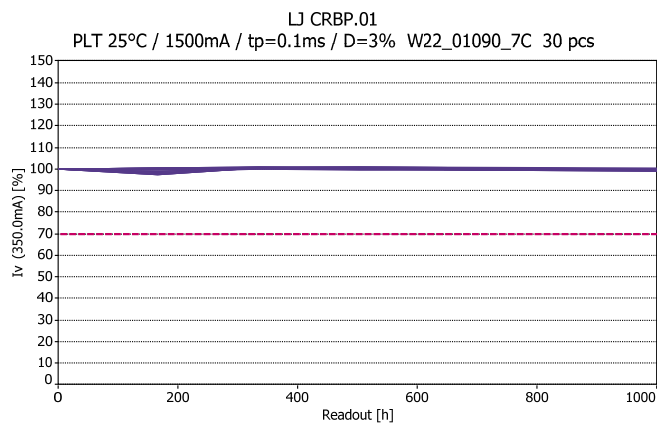
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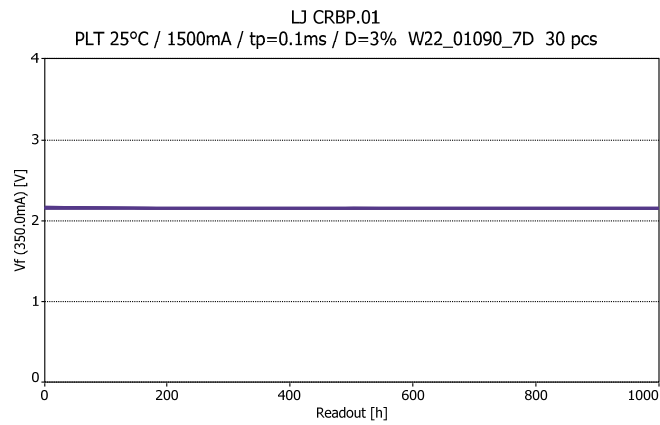
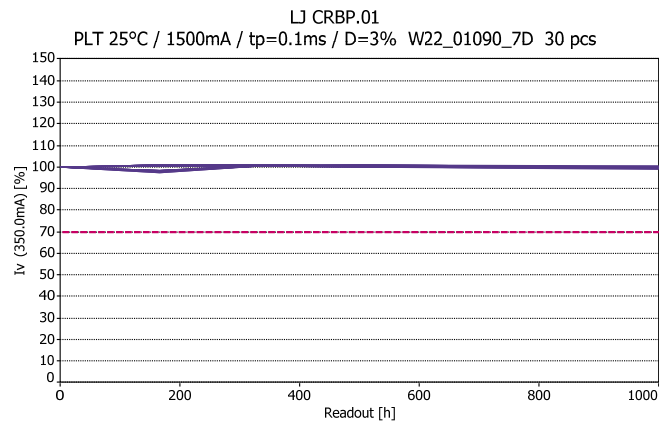
Lot B



Lot C

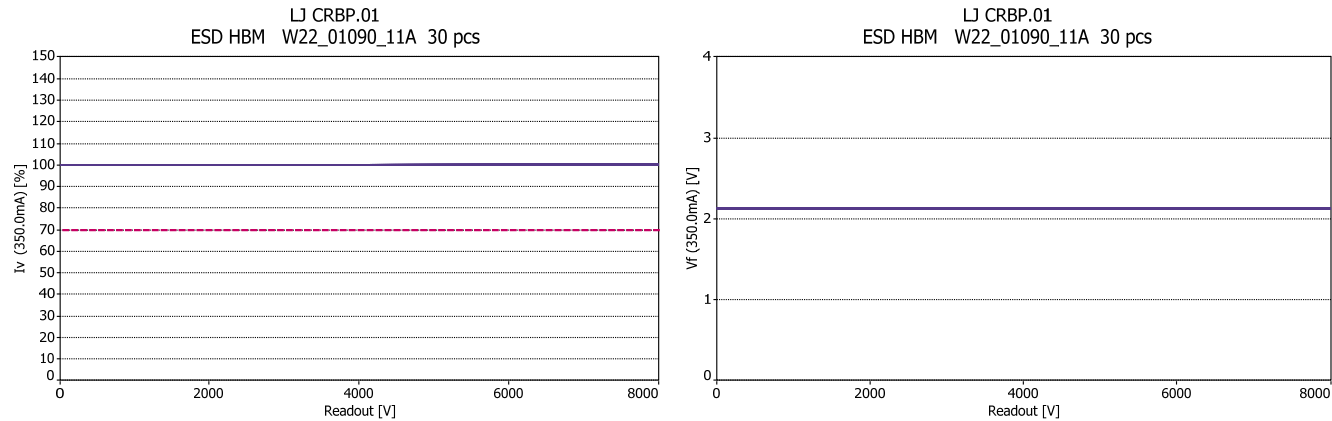


Lot D

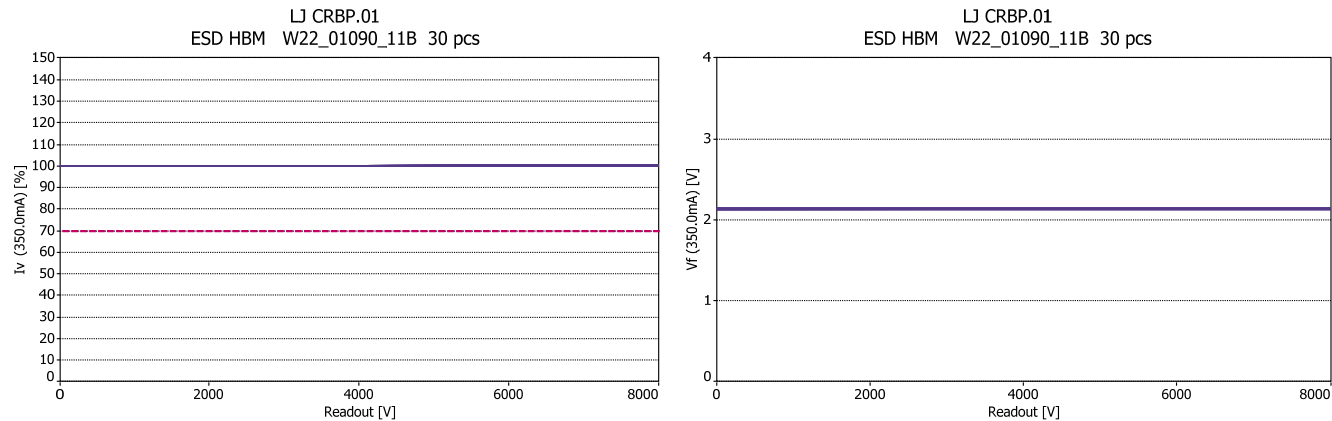


ESD HBM

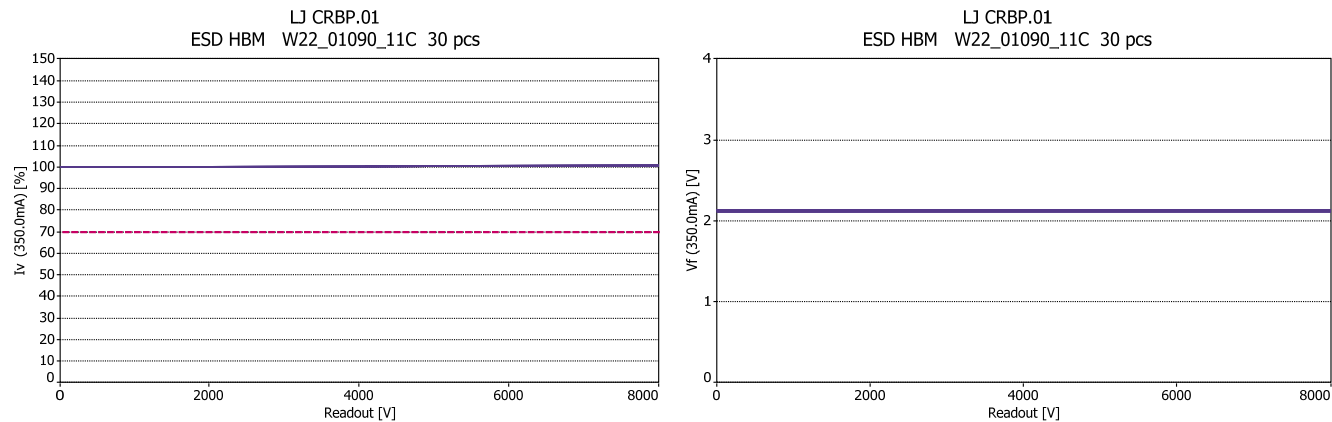
Lot A



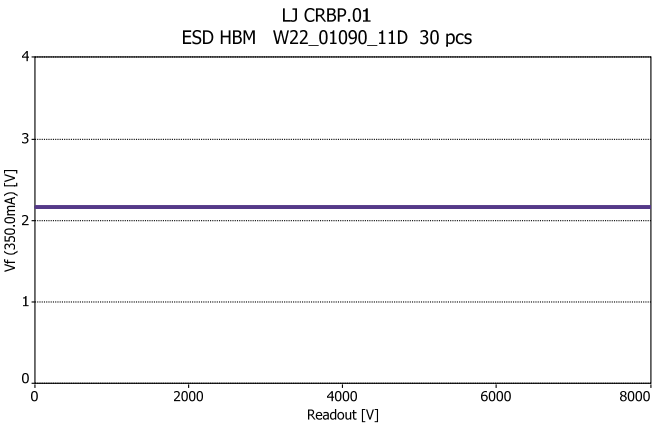
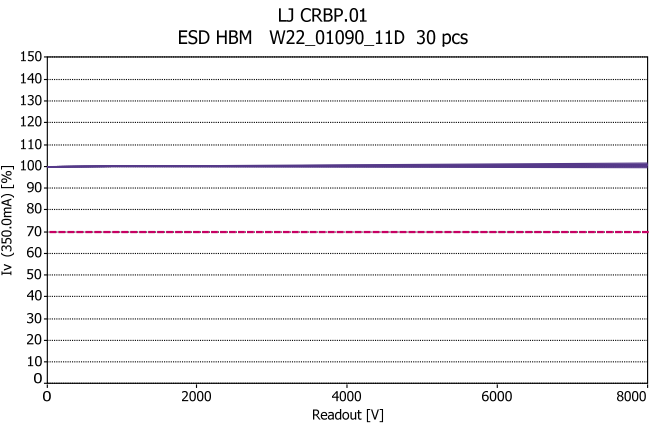
Lot B



Lot C



Lot D



END OF DOCUMENT

Qualification Report 230043C1

Subject	Qualification report for OSOLON Signal LB CRBP.01, LCY CRBP.01 and LUW CRBP.01 according to OS-PCN-2023-030-A
Date	15.03.2023
Tested device	LUW CRBP.01
Brand (including sub brands)	OSOLON Signal
Applies to	LB CRBP.01, LCY CRBP.01, LUW CRBP.01

Pre-conditioning according to Jedec Level 2

Test Performed		Condition	Duration	Sample Size	Failures		
					El.	Opt.	Vis
Low Temperature Operating Life	LTOL	T _A = -40°C	1000h	4x30	0	0	0
		I _F = 1200mA					
JESD22-A108							
High Temperature Operating Life	HTOL	T _A = 100°C	1000h	4x30	0	0	0
		I _F = 1200mA					
JESD22-A108							
Wet High Temperature Operating Life	WHTOL	T _A = 60°C	1000h	4x30	0	0	0
		r.H.= 93%					
JESD22-A101		I _F = 30mA					
Wet High Temperature Operating Life	WHTOL	T _A = 60°C	1000h	4x30	0	0	0
		r.H.= 93%					
JESD22-A101		I _F = 1200mA					
Pulse life test	PLT	T _A = 25°C	1000h	4x30	0	0	0
		I _F = 2000mA					
JESD22-A108		t _p = 0.1ms; D = 3%					
Temperature cycle	TC	T _A = -40°C/+125°C	1000h	4x30	0	0	0
		15min each extreme					
JESD22-A104							
Electrostatic Discharge	HBM	Human Body Model	1000h	4x30	0	0	0
ANSI/ESDA/ JEDEC JS-001							
Gas corrosion test		T _A = 25°C	500h	4x30	0	0	0
		r.H.= 75%					
IEC 60068-2-60		Methode 4					
Damp heat cyclic		T _{A,min} = 25°C; T _{A,max} = 65°C	10c	4x30	0	0	0
		r.H.= 90%					
IEC 60068-2-30		I _F = 30mA					

Note: Lot A-C evaluation lot, Lot D control lot

Failure criteria:

Electrical failures:	V _f (I _f =350mA)	> 3.25V; ± 10% from initial value
Optical failures:	Φ _v (I _f =350mA)	> ± 30% from initial value
	C _x /C _y (I _f =350mA)	± 0.01 from initial value
Visual failures:	acc JEDEC JESD22-B101	

Conclusion: The tested device fulfills the reliability requirements.

Disclaimer

PLEASE CAREFULLY READ THE BELOW TERMS AND CONDITIONS BEFORE USING THE INFORMATION.
IF YOU DO NOT AGREE WITH ANY OF THESE TERMS AND CONDITIONS, DO NOT USE THE INFORMATION.

The Information contained in this Document does not constitute an independent warranty. The committed behavior is described in the Product data sheet and/or further, mutually agreed specifications.

Distribution of part or all of the contents of this Document to any 3rd party in any form without the prior permission of ams-OSRAM International GmbH is prohibited except in accordance with applicable mandatory law.

Further explanations:

Data: The Data used in this Document consider the reliability test results under the mentioned driving conditions only. For Product information on the maximum operating conditions and the OSRAM standard qualification profile please refer to the Product data sheet or contact your local sales partner.

Conditions: The conditions for the generation of the Data are as follows:

1. The Data and curves shown in this Document are based on experiments carried out under laboratory conditions on a random sample size of LED/IRED/Laser/Detector with readouts at discrete readout times (where applicable). Thus, the Data above represent a limited number of production lots only and may differ between different assembly lots over time (including chip or package changes). Thus, the behavior of the LED/IRED/Laser/Detector in the final application may differ from the Data. The behavior of the LED/IRED/Laser/Detector at conditions or readout times deviating from those stated above may not be deduced from the Data.

2. If applicable:

a) Extended driving conditions:

The tested driving conditions exceed the maximum limits stated in the Product data sheet. Therefore, a reduced lifetime or an accelerated degradation is expected. Failure limits noted in the Document refer to the testing condition according to the OSRAM standard Product qualification profile and not to the actual testing condition.

b) Extended testing duration:

The testing duration exceed the OSRAM standard qualification profile of the mentioned Product. Failure limits noted in the Document refer to the testing duration according to the OSRAM standard Product qualification profile and not to the actual testing duration.

c) Exceeding standard qualification conditions – (Product data sheet limits not affected):

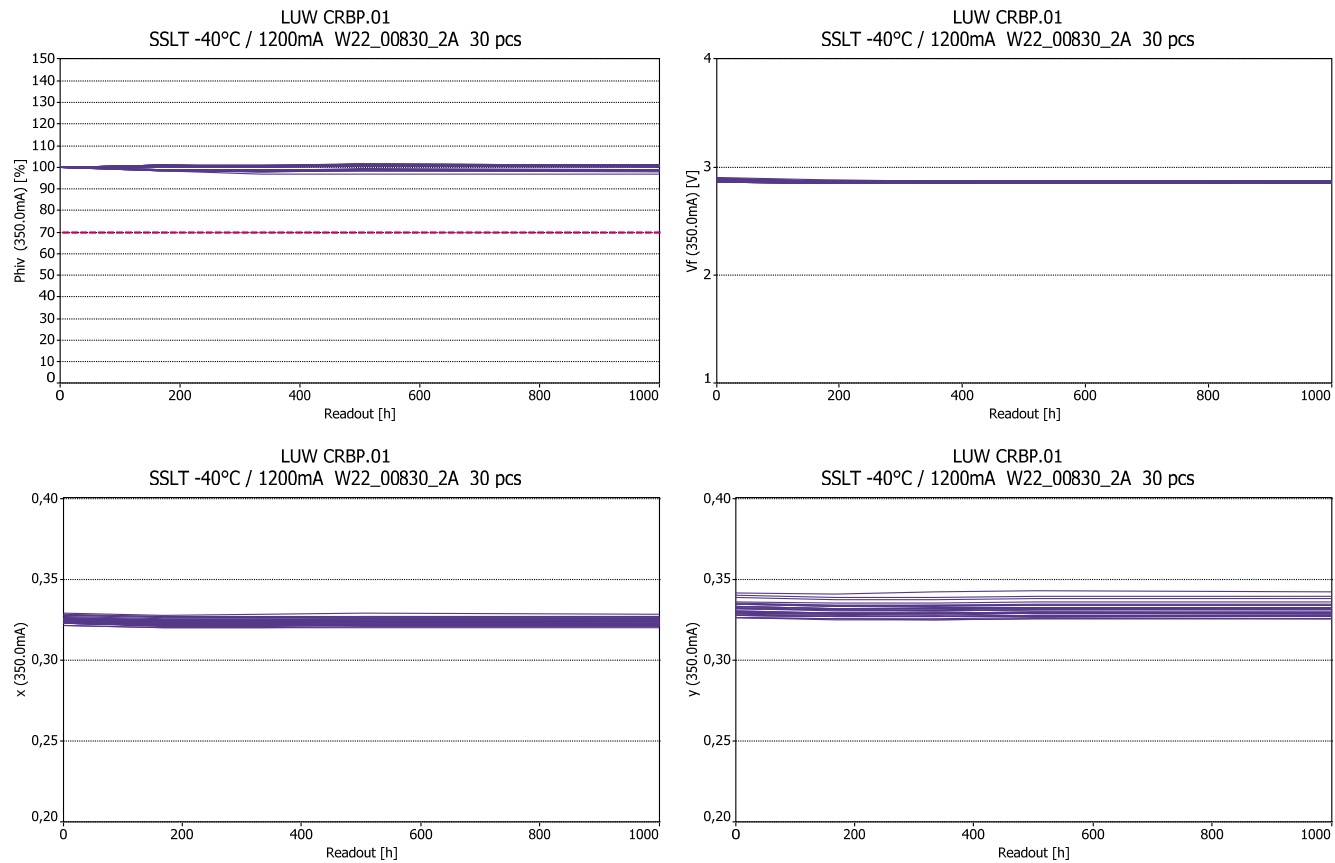
The tested driving conditions exceed the OSRAM standard qualification profile of the mentioned Product. Therefore a reduced lifetime or an accelerated degradation is expected. Failure limits noted in the Document refer to the testing condition according to the OSRAM standard Product qualification profile and not to the actual testing condition.

3. For long term operation additional failure modes of the chip or package can occur which are not shown in this Document.

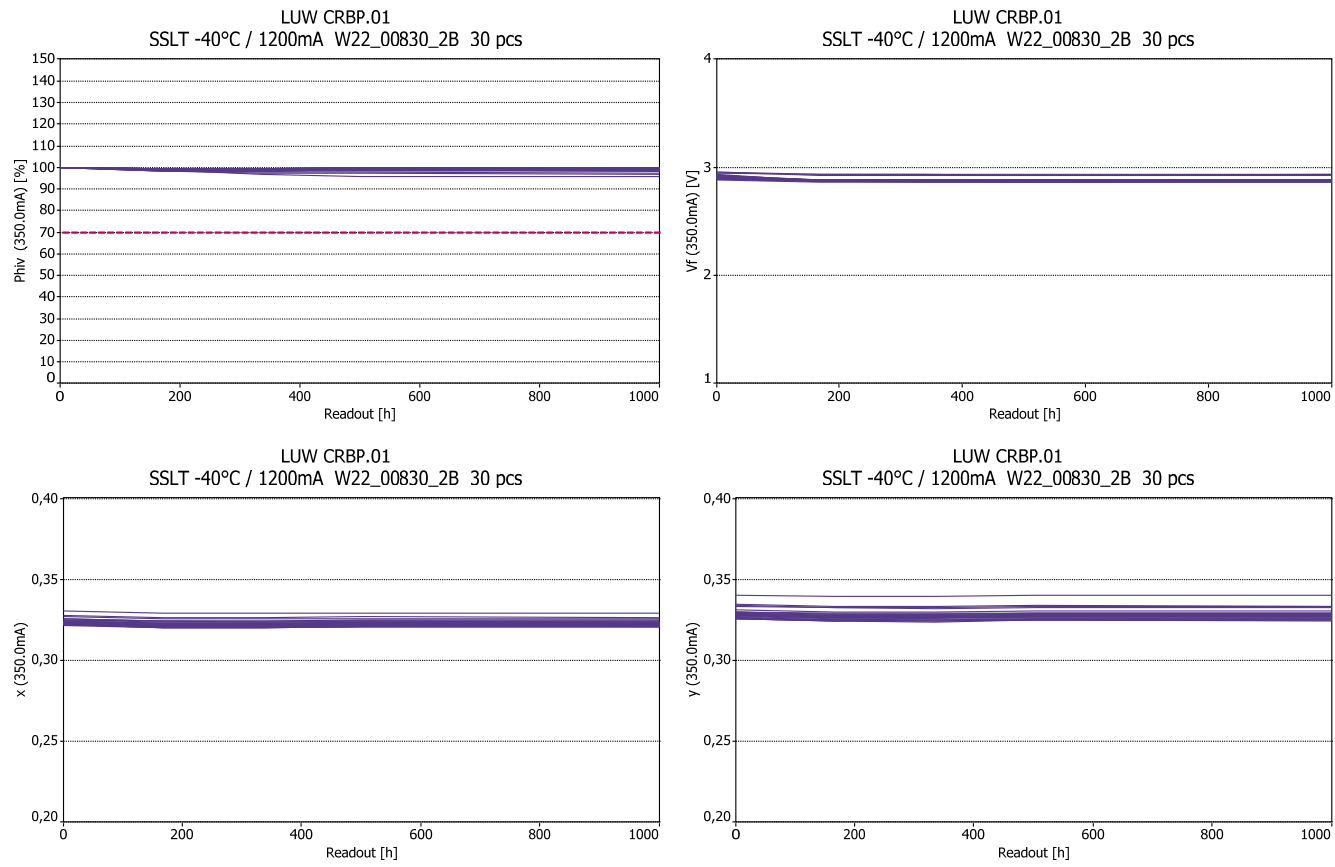
4. Possible differences in the thermal management of OSRAM and customer's setup may lead to a different aging behavior.

LTOL -40°C / 1200mA

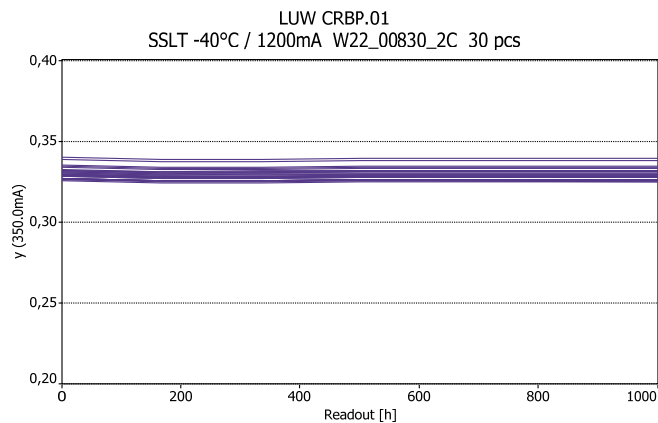
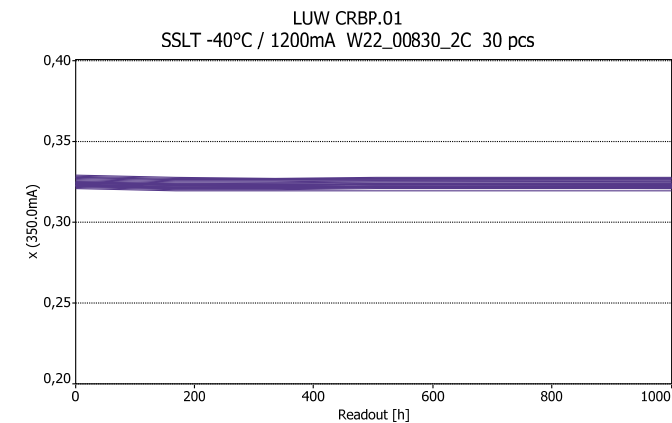
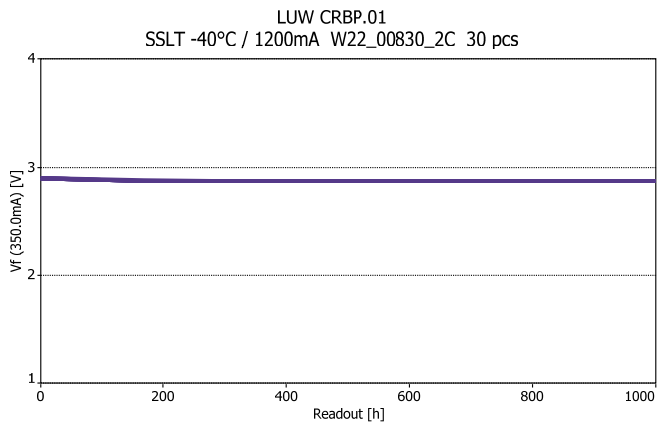
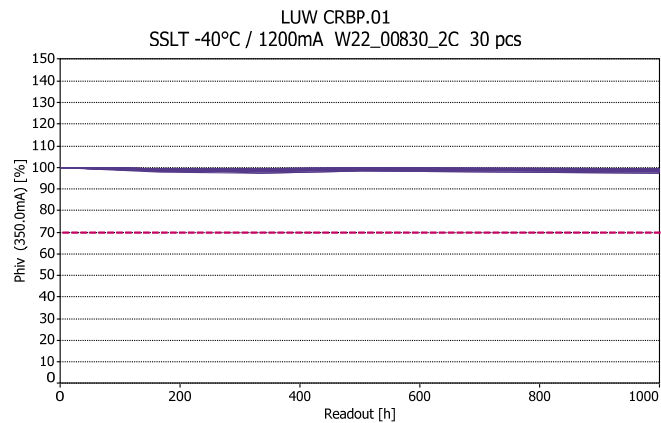
Lot A



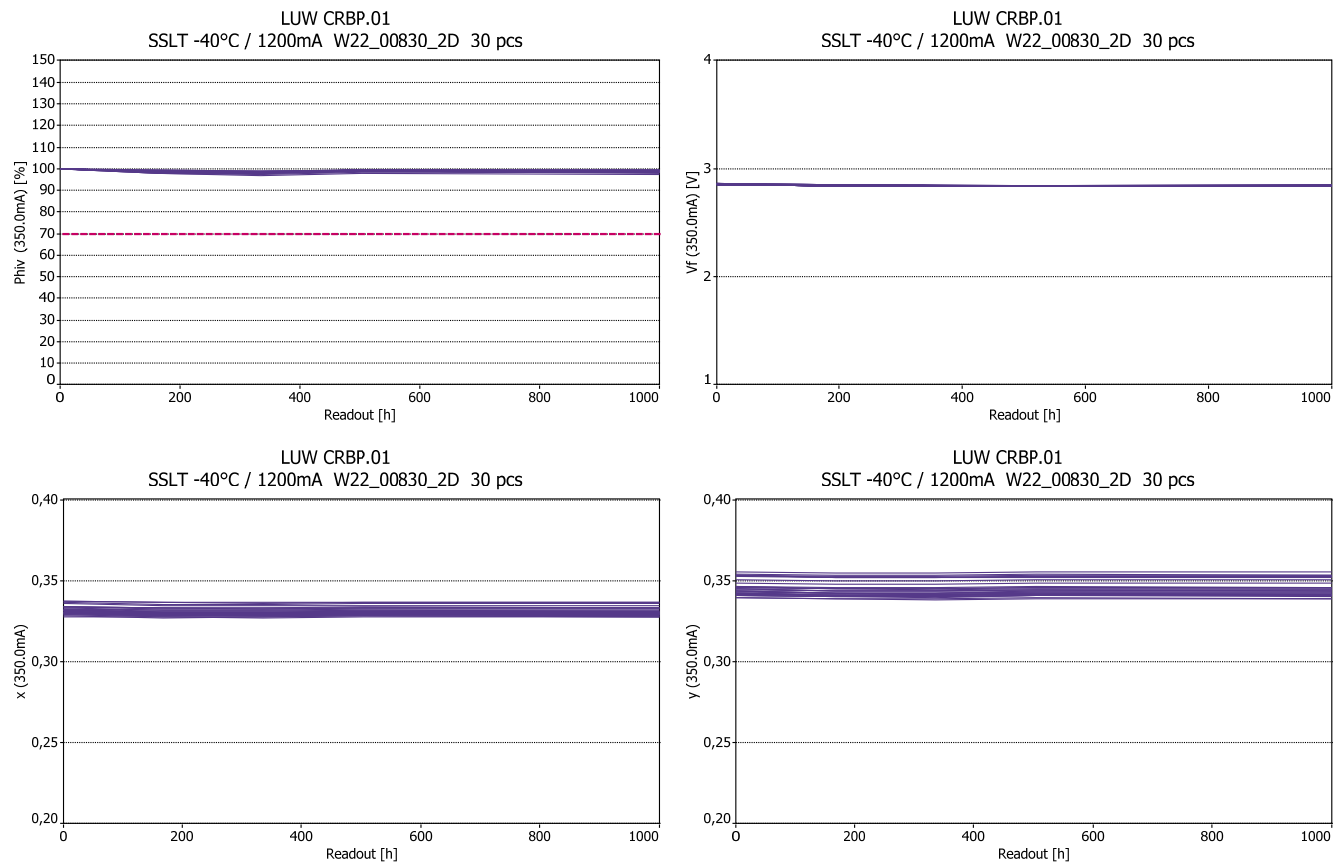
Lot B



Lot C

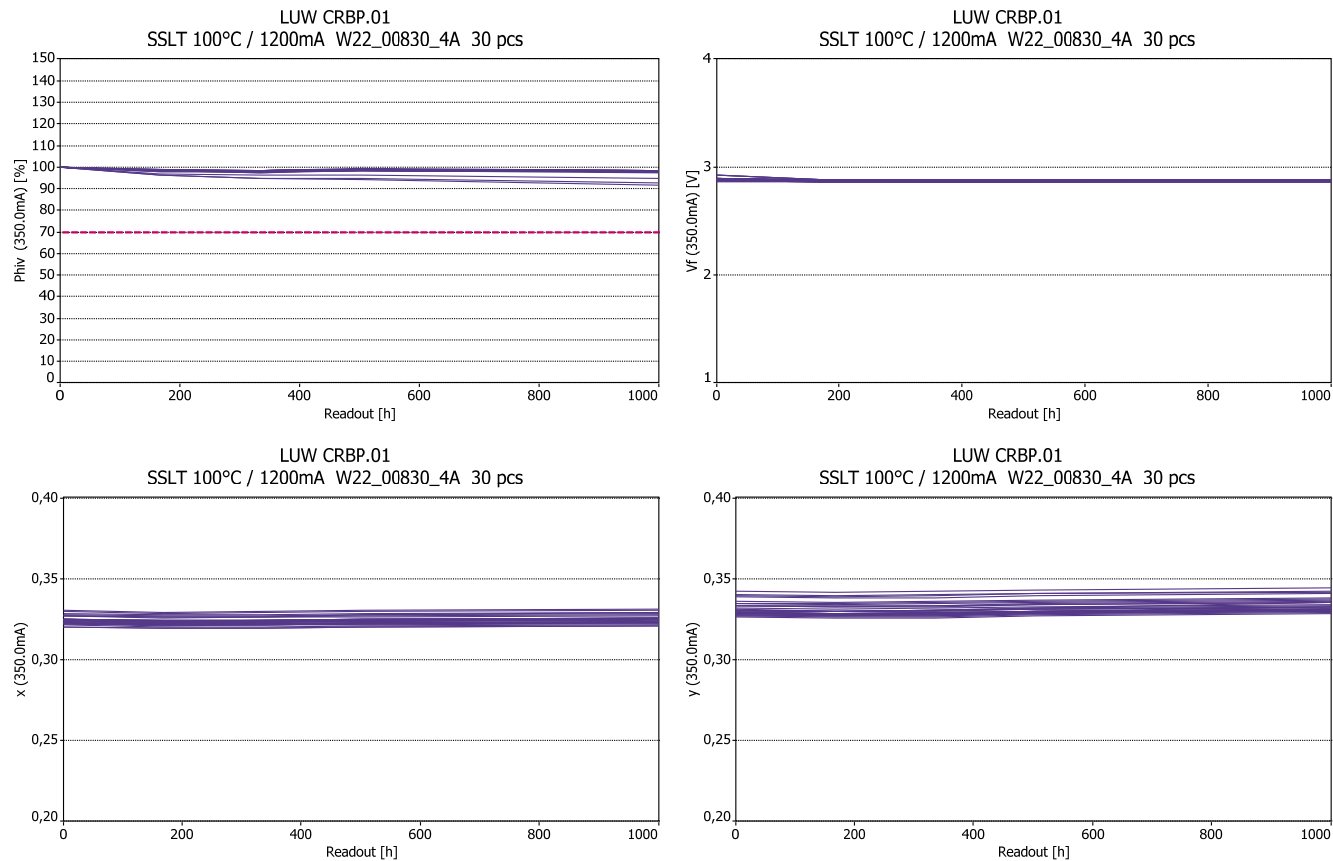


Lot D

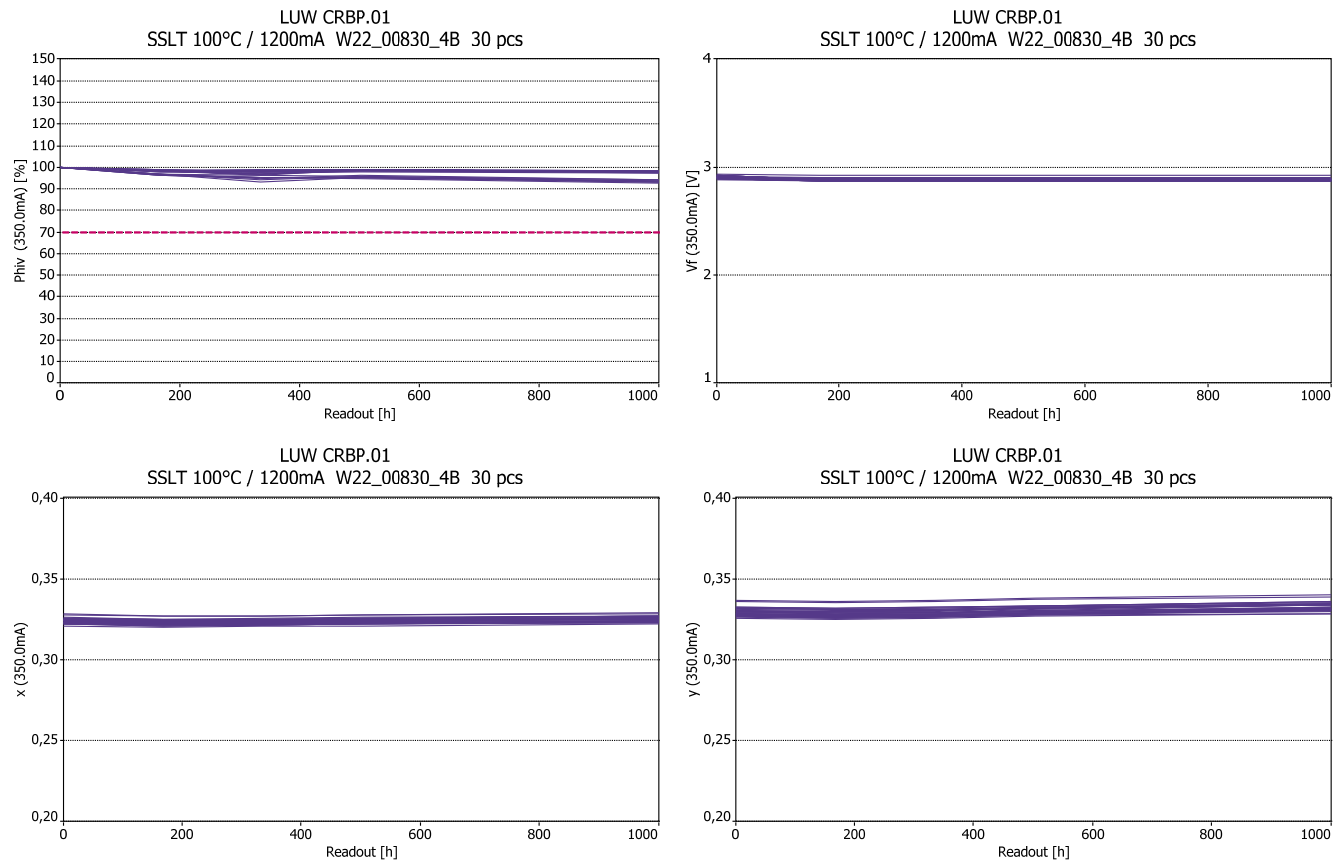


HTOL 100°C / 1200mA

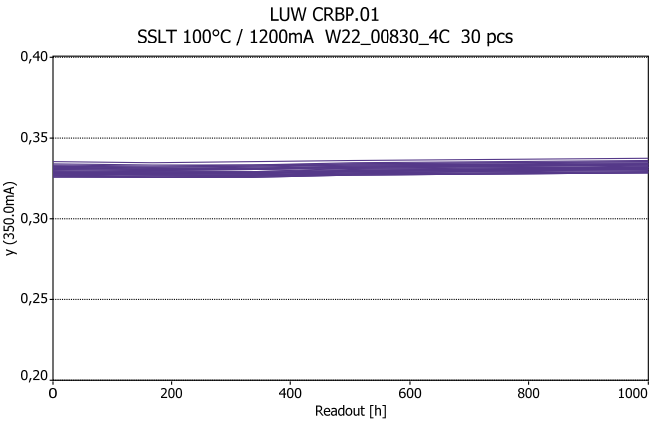
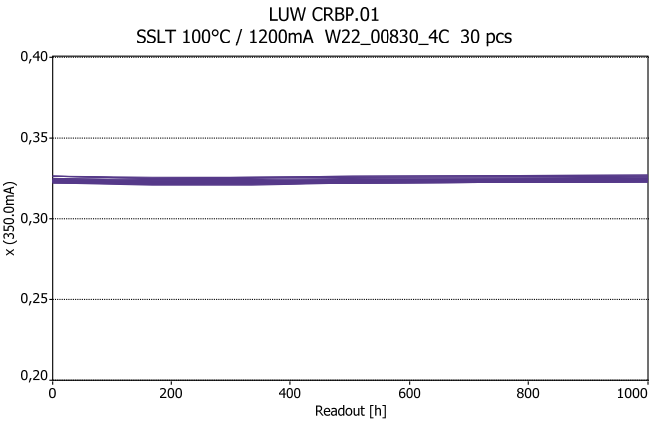
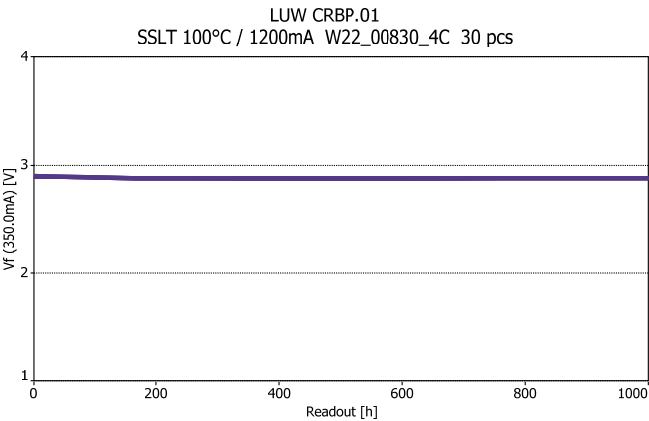
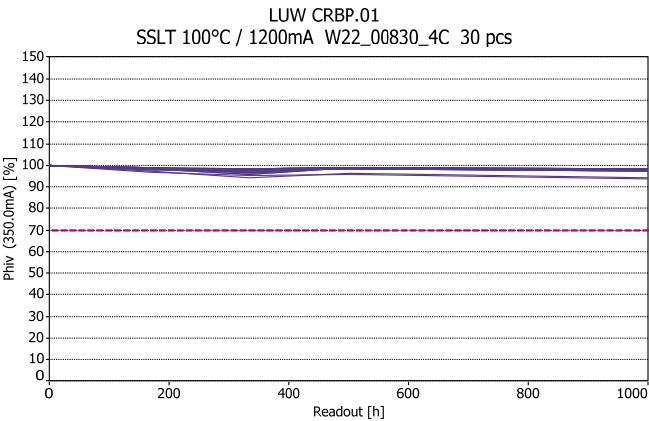
Lot A



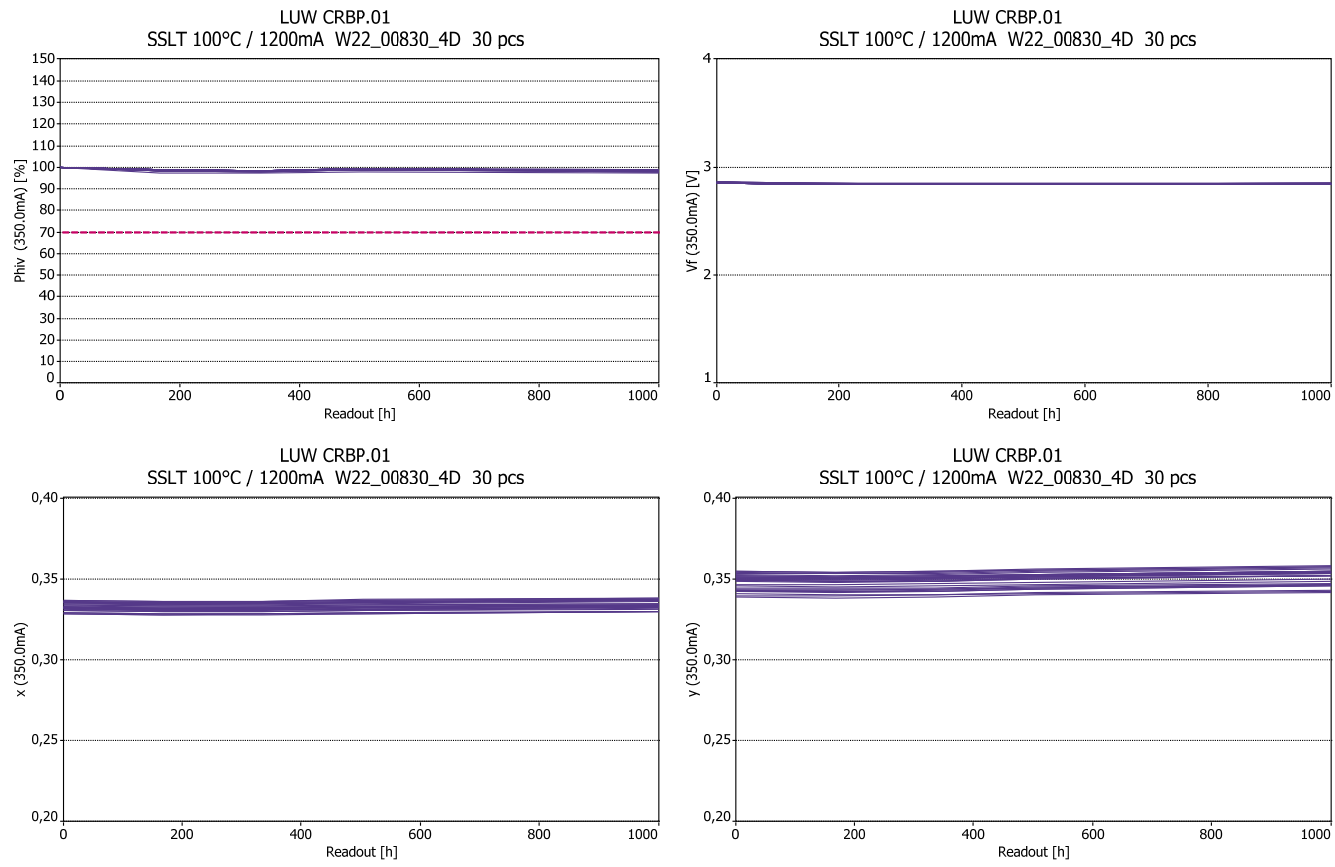
Lot B



Lot C

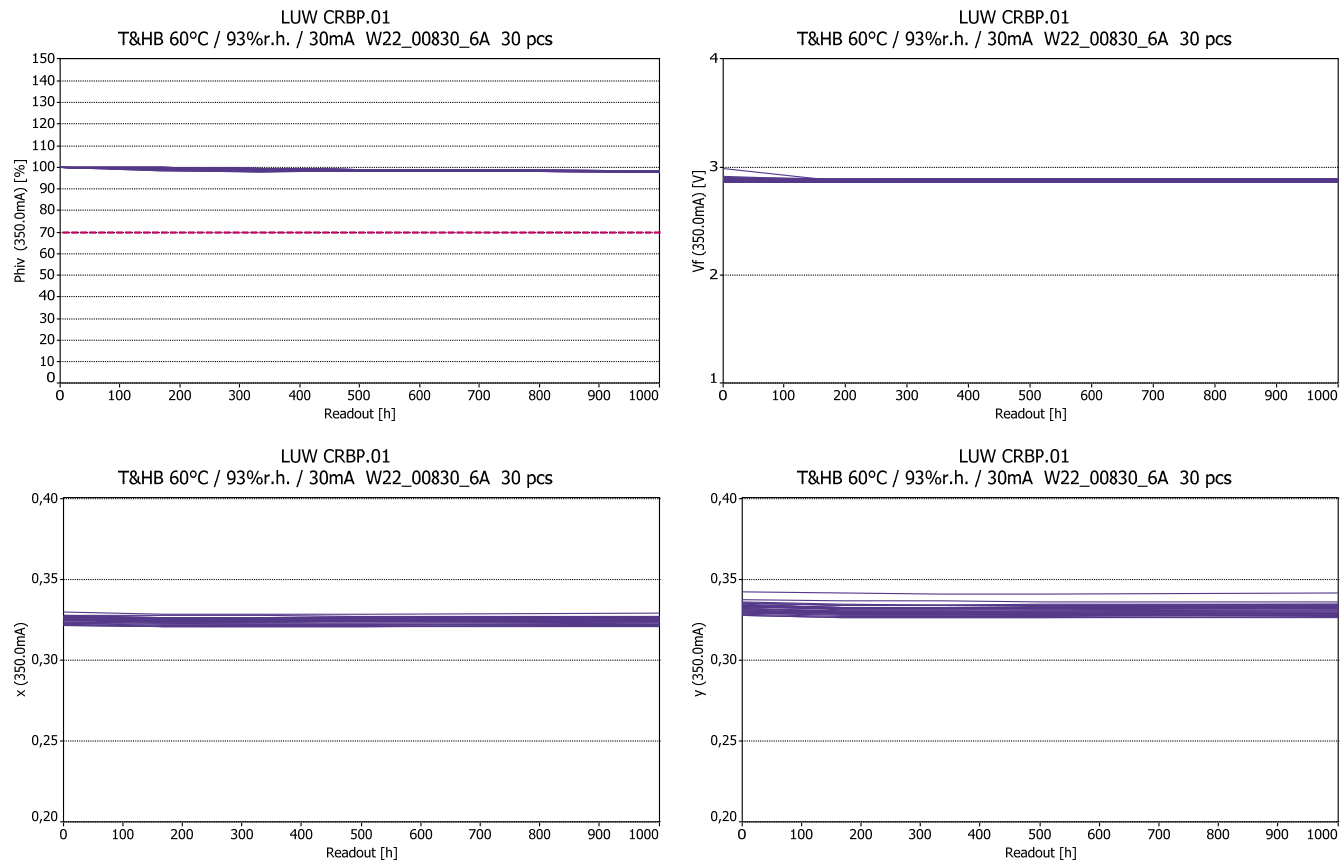


Lot D

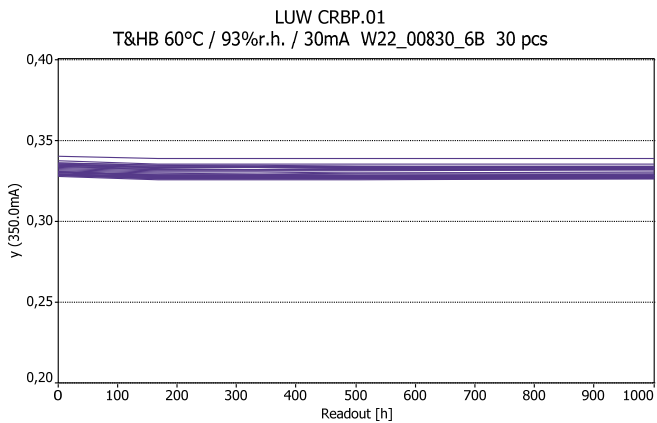
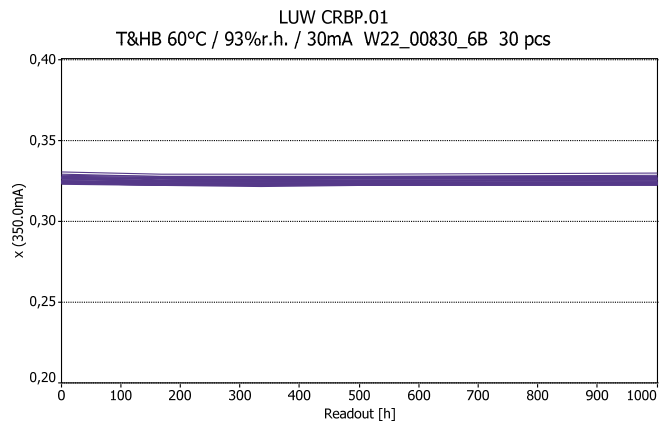
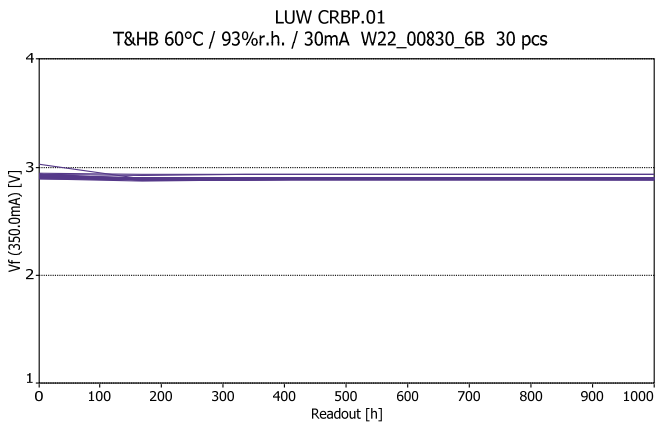
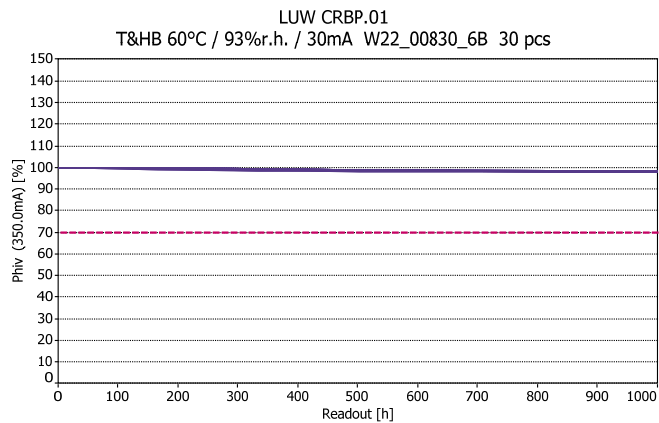


WHTOL 60°C / 93%r.h. / 30mA

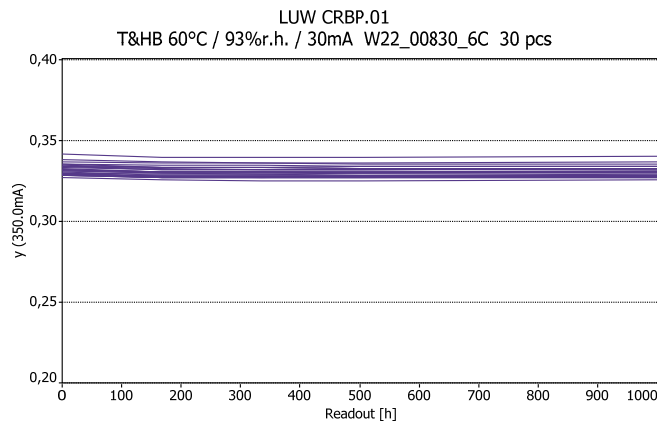
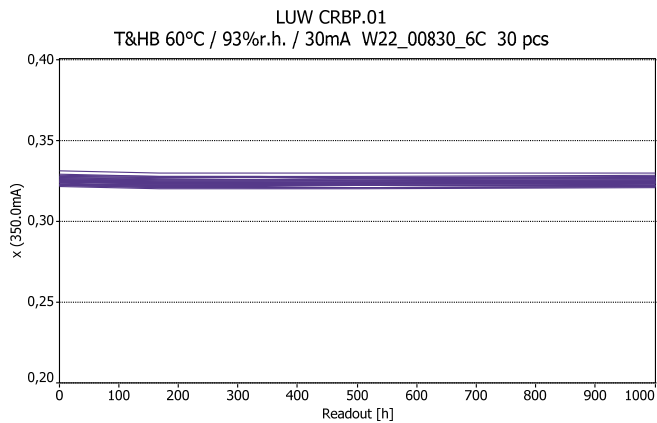
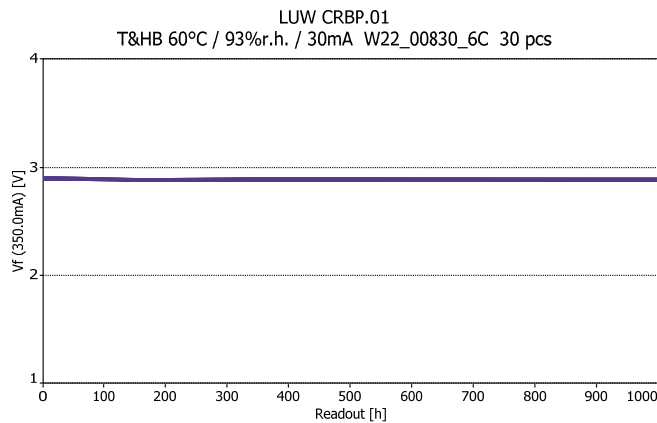
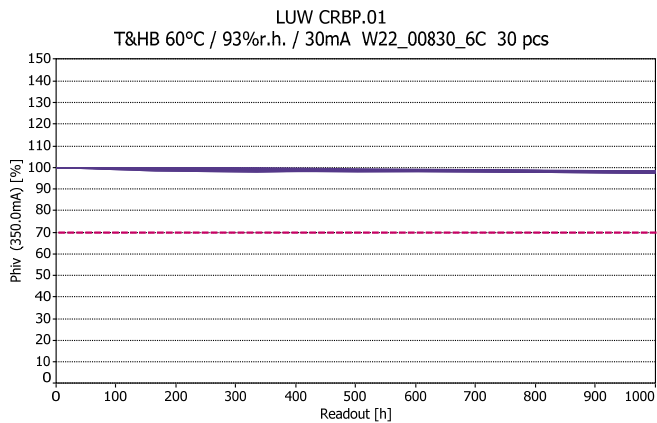
Lot A



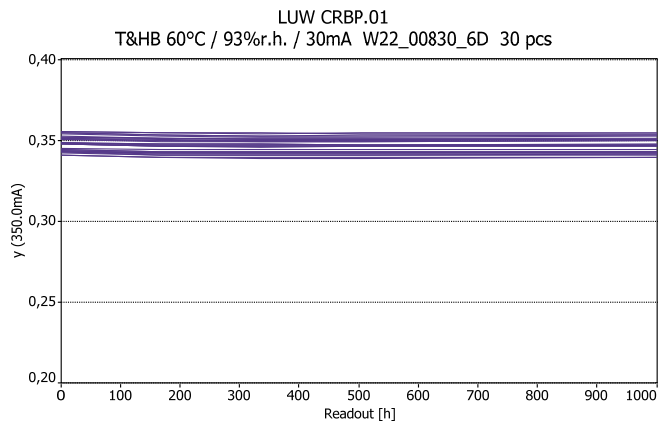
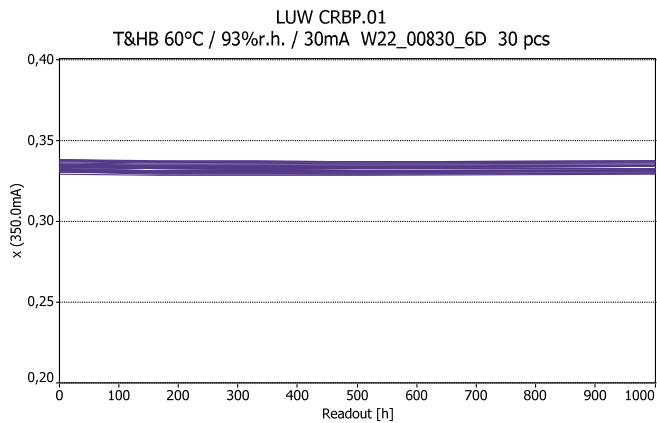
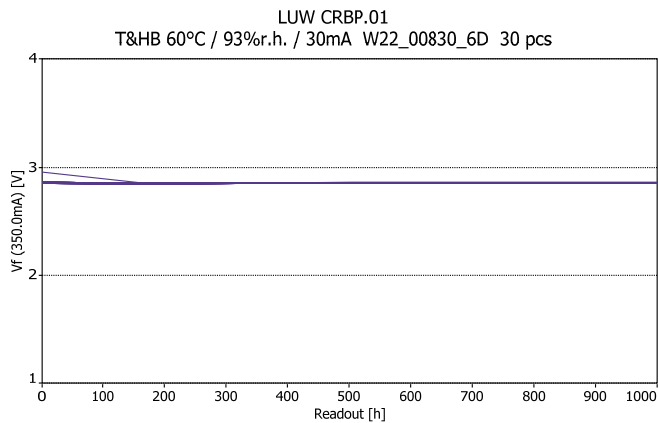
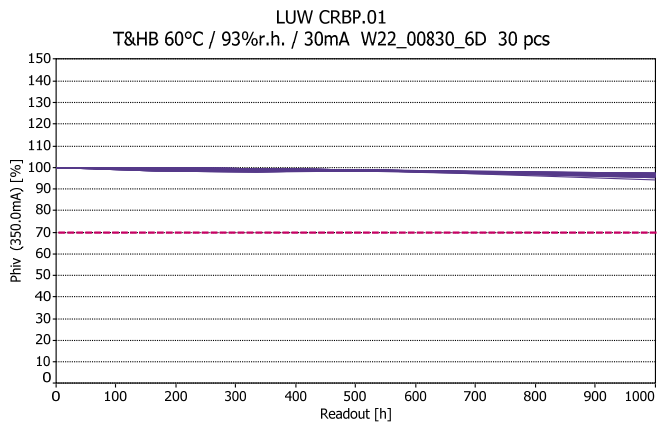
Lot B



Lot C

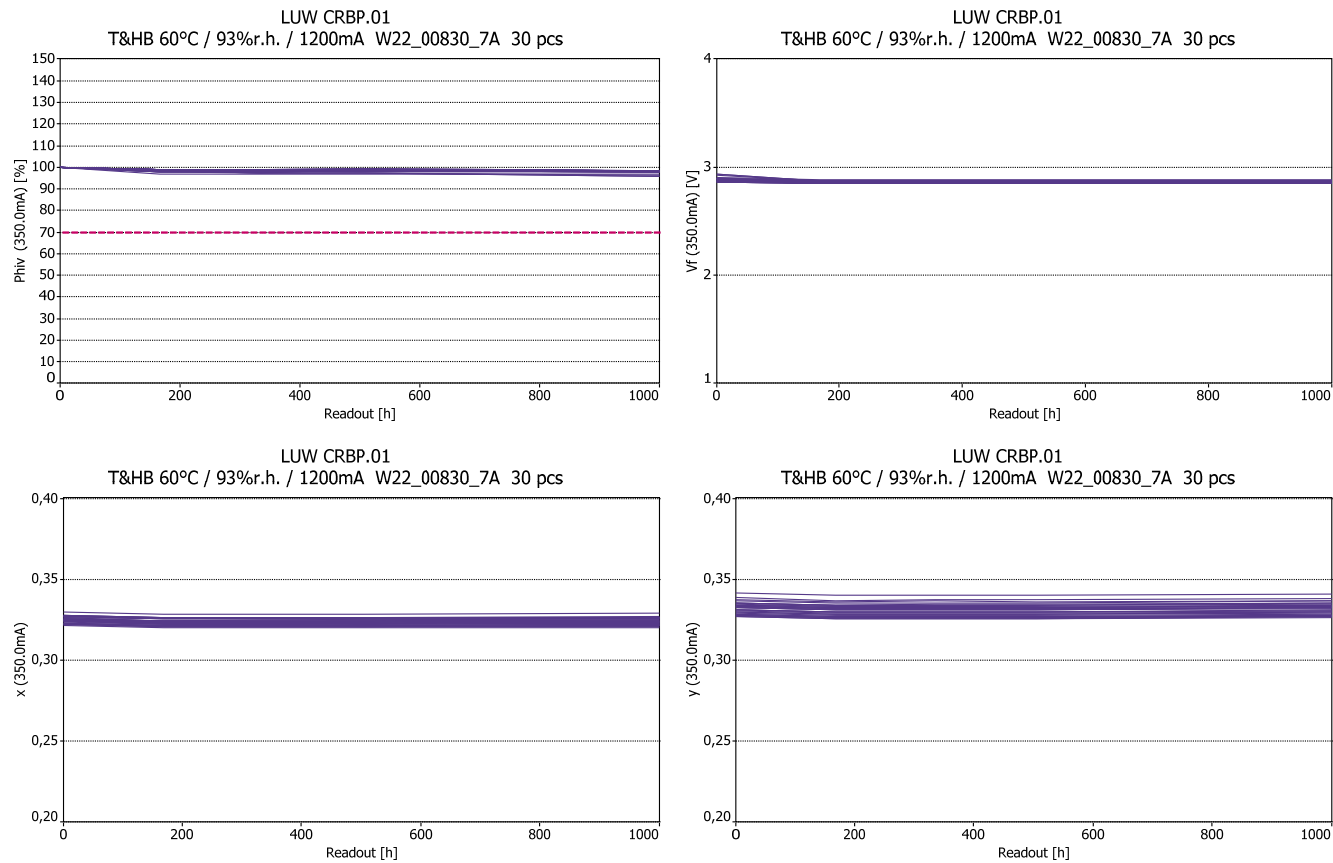


Lot D

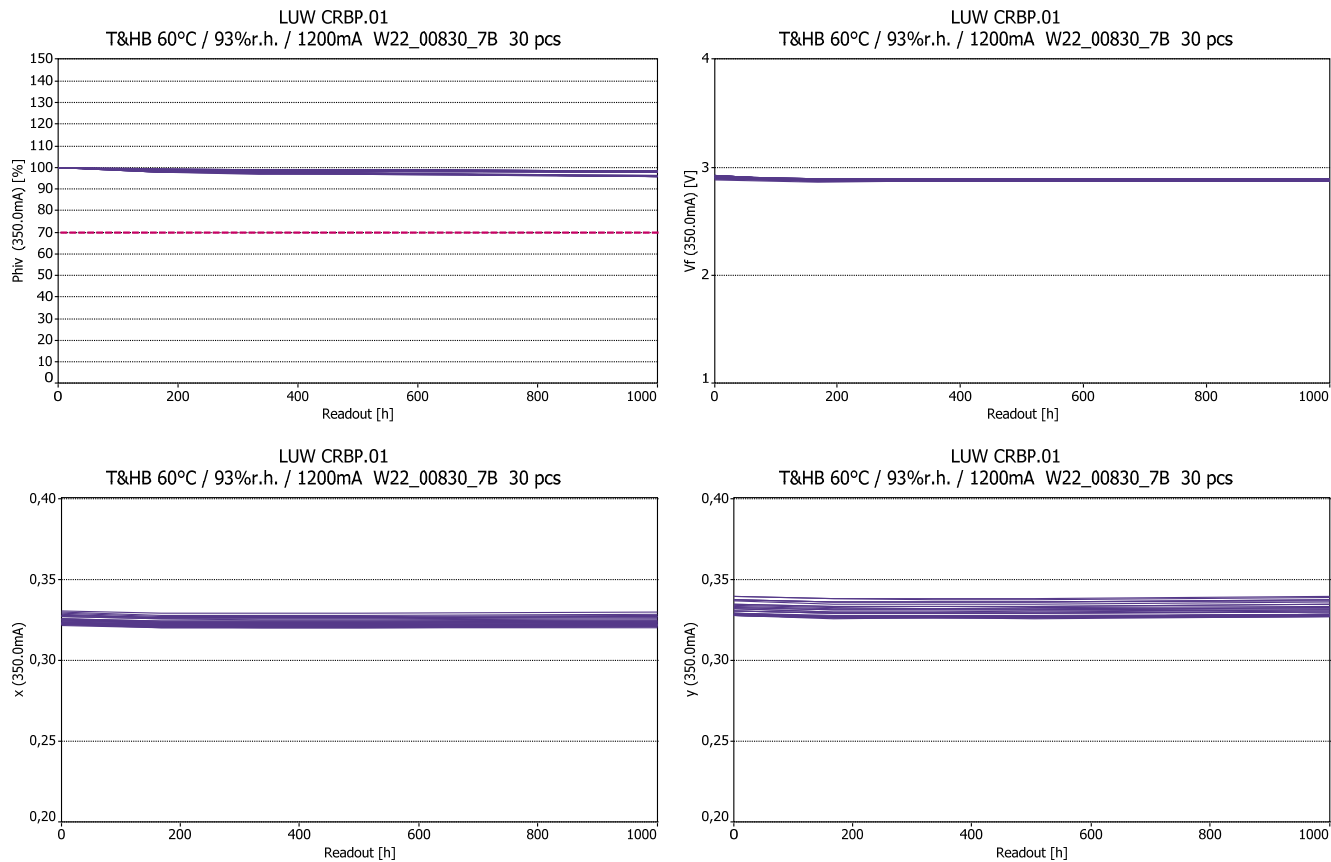


WHTOL 60°C / 93%r.h. / 1200mA

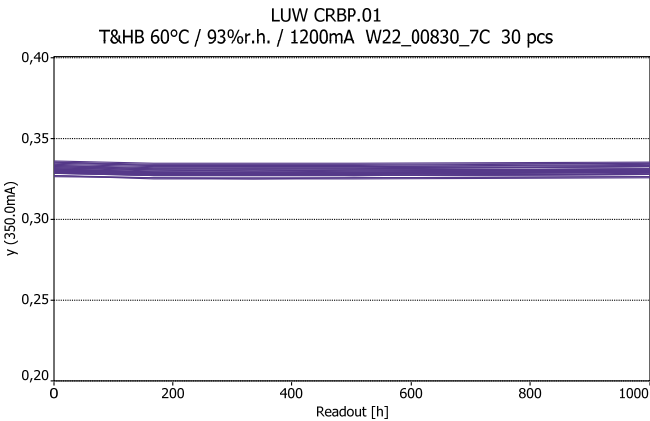
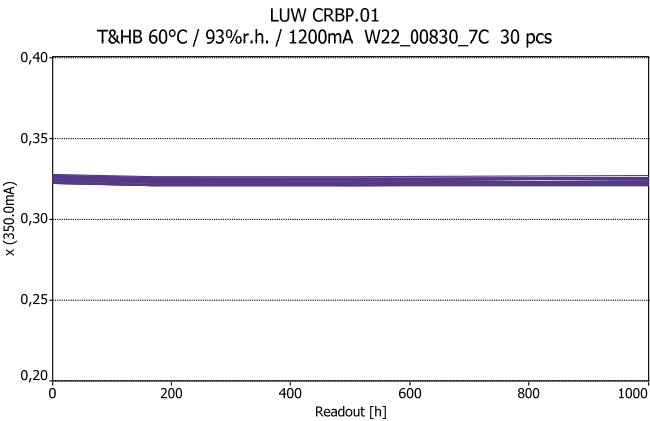
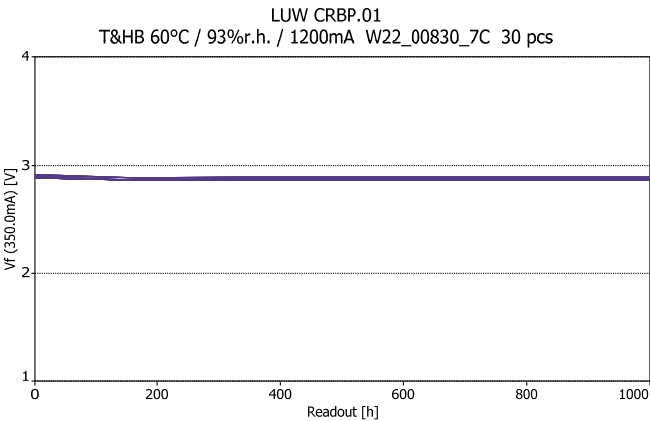
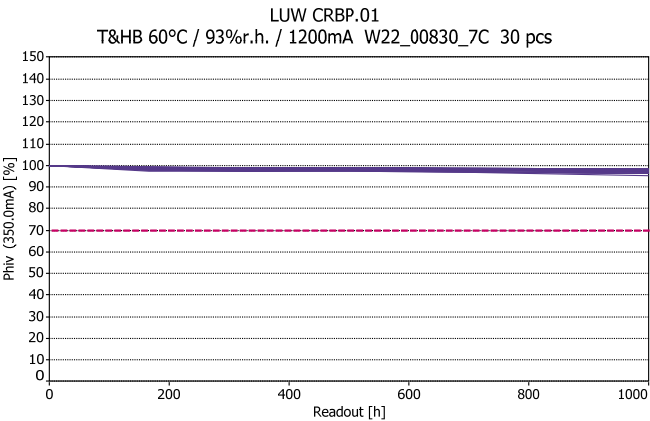
Lot A



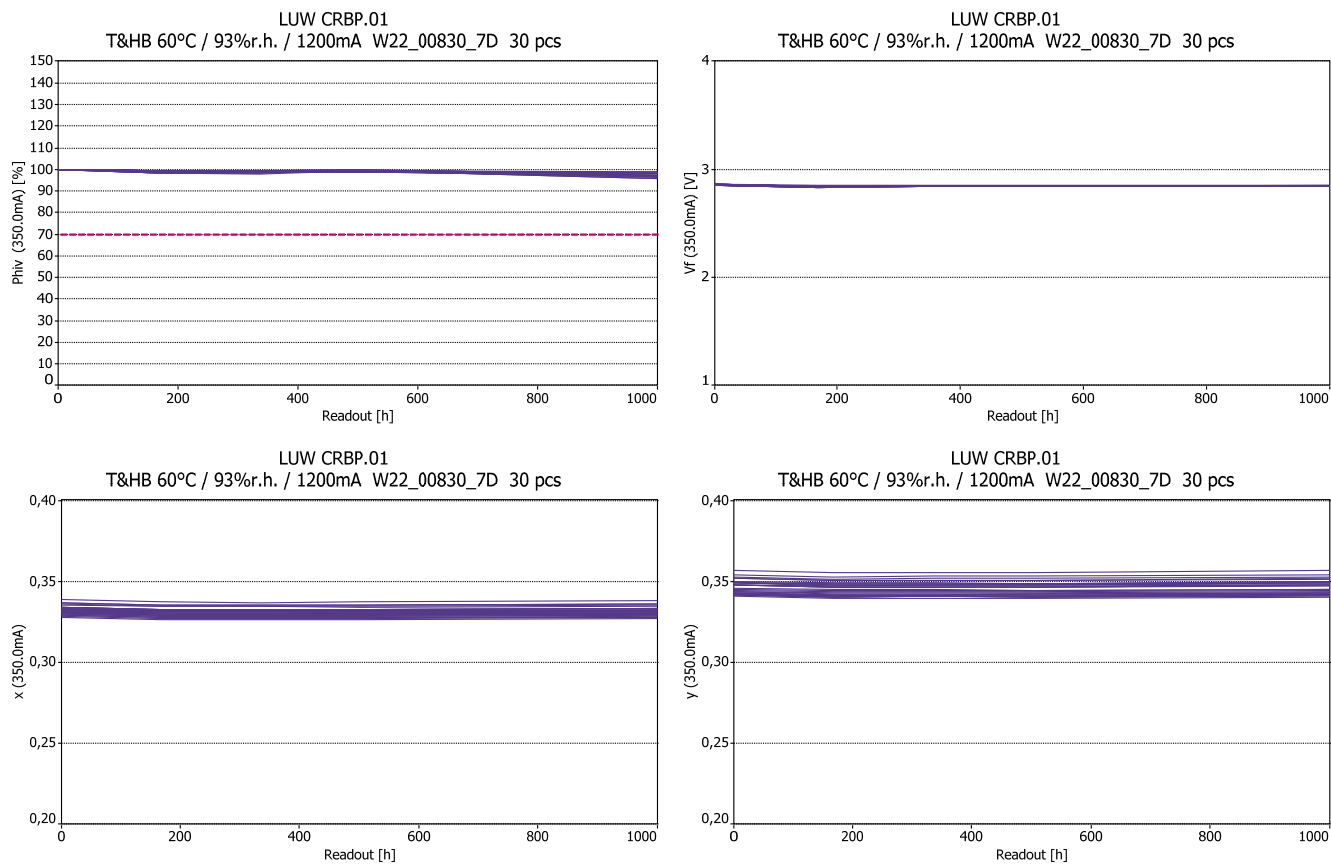
Lot B



Lot C

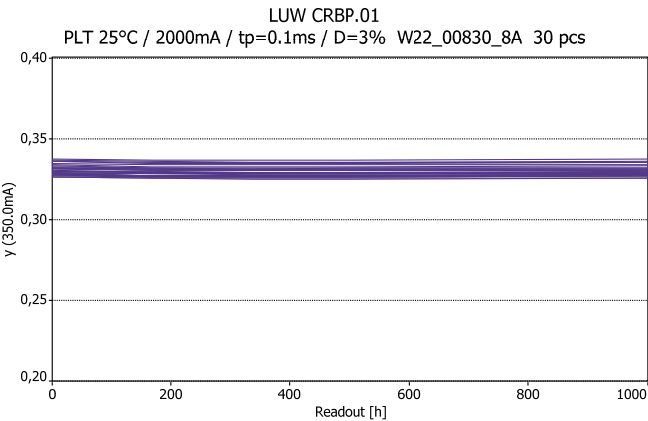
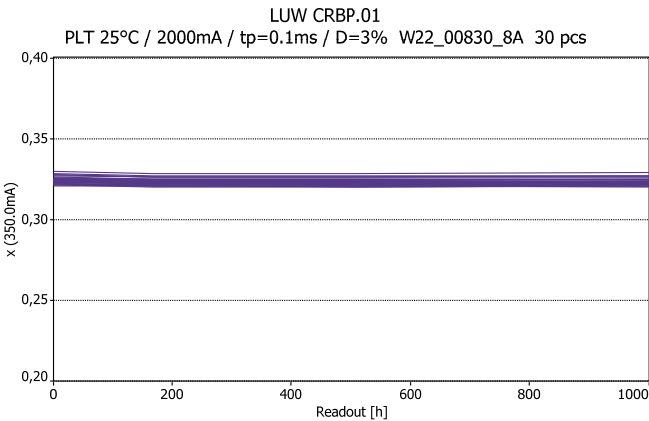
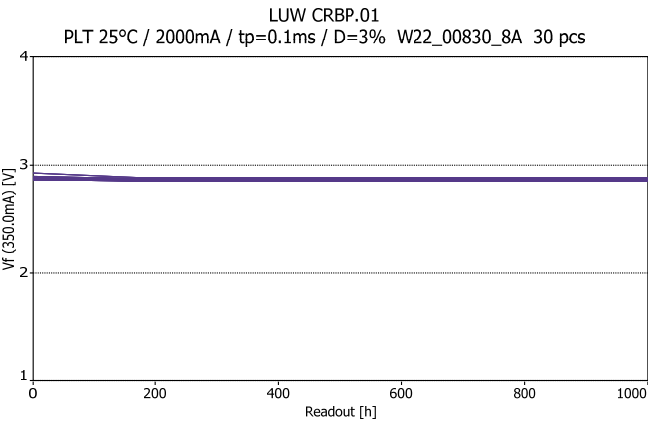
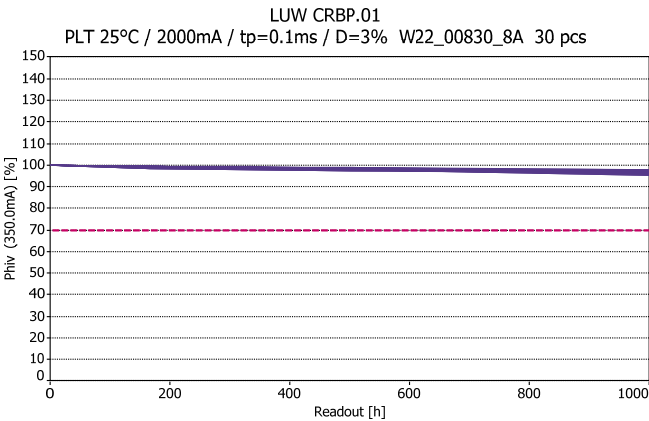


Lot D

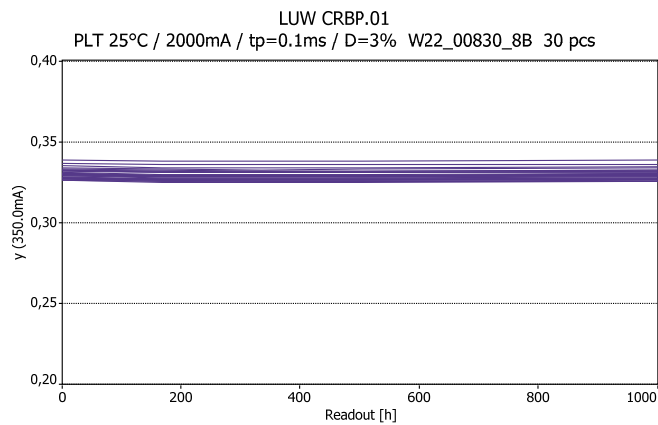
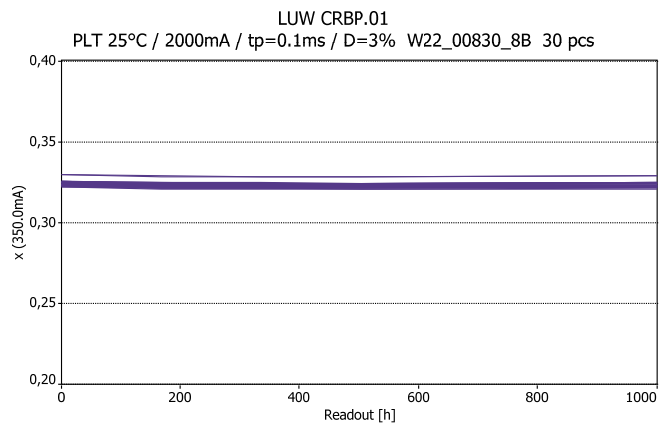
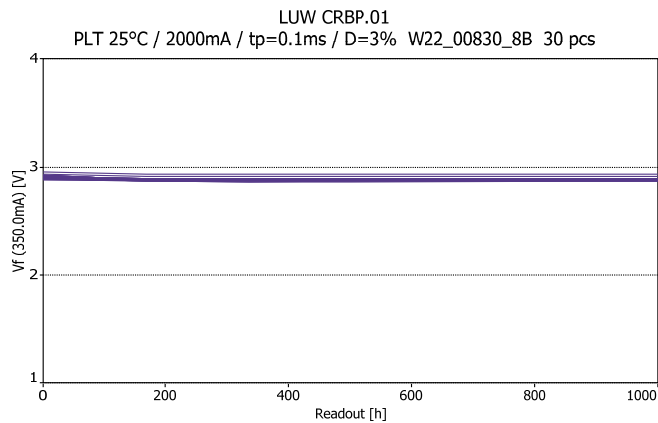
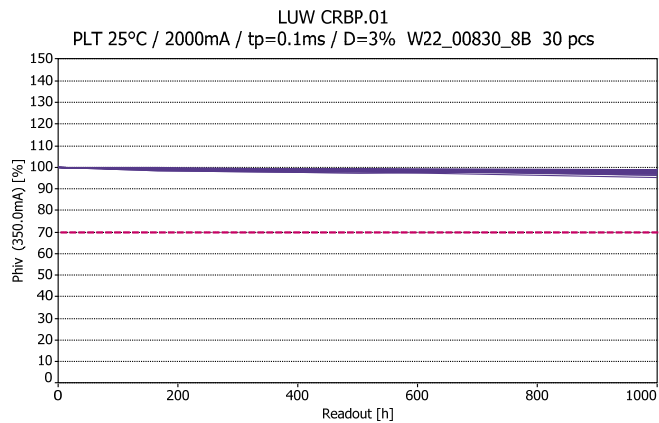


PLT 25°C / 2000mA / tp=0.1ms / D=3%

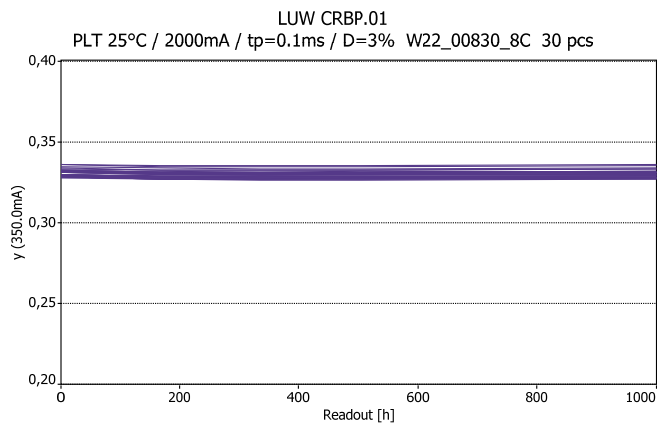
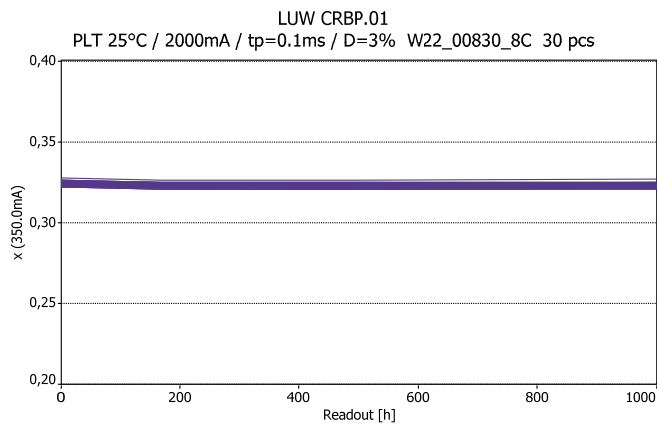
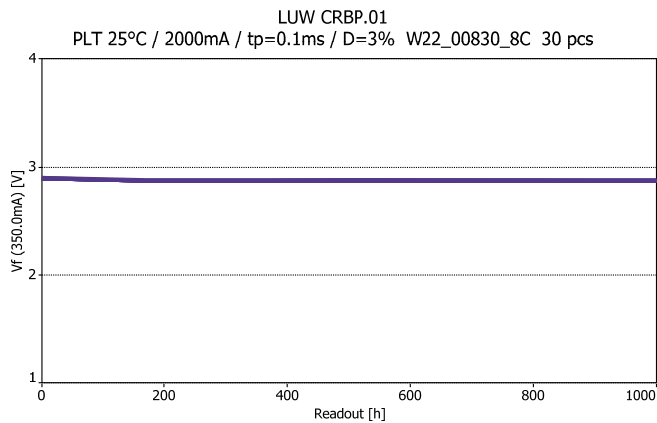
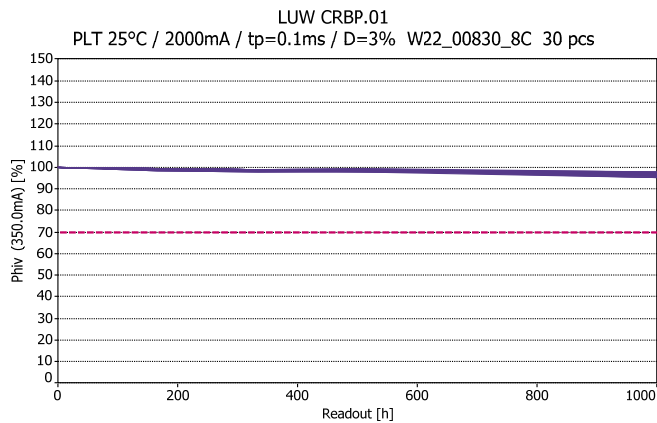
Lot A



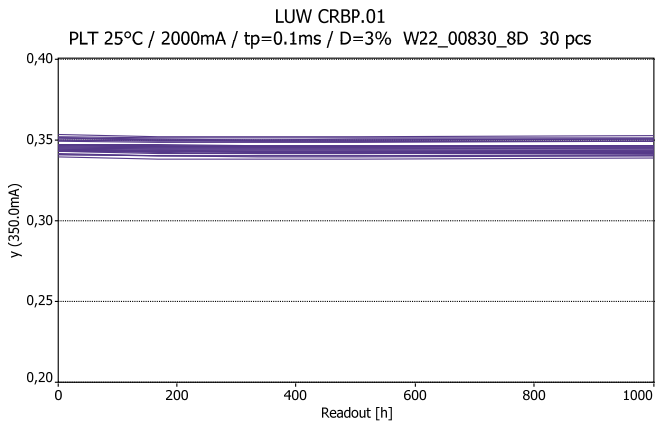
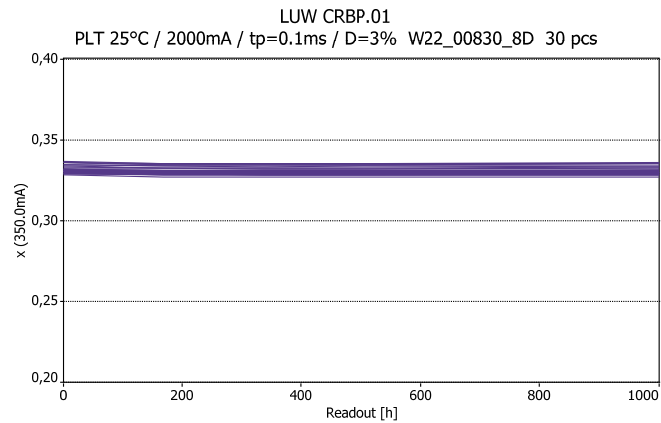
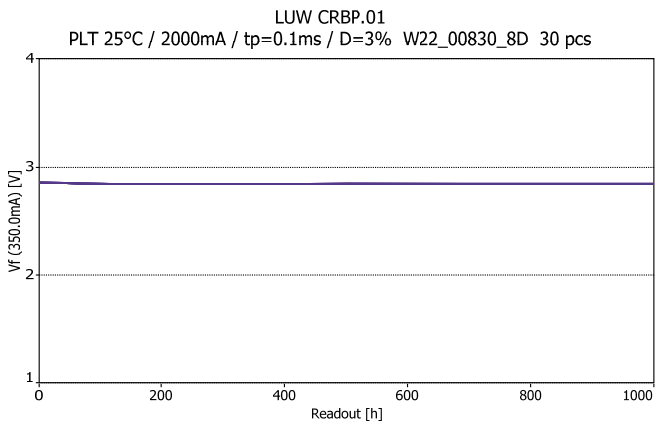
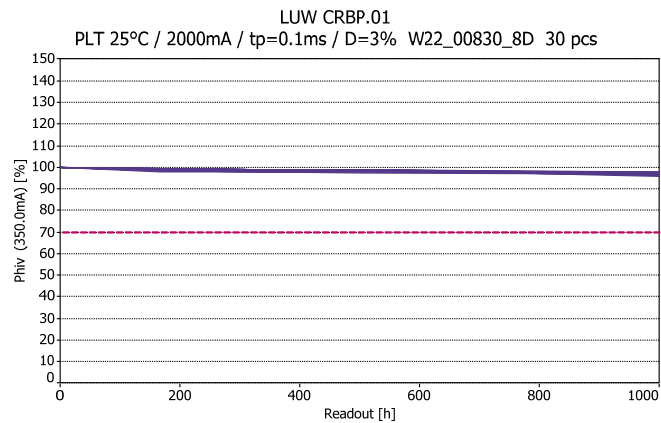
Lot B



Lot C

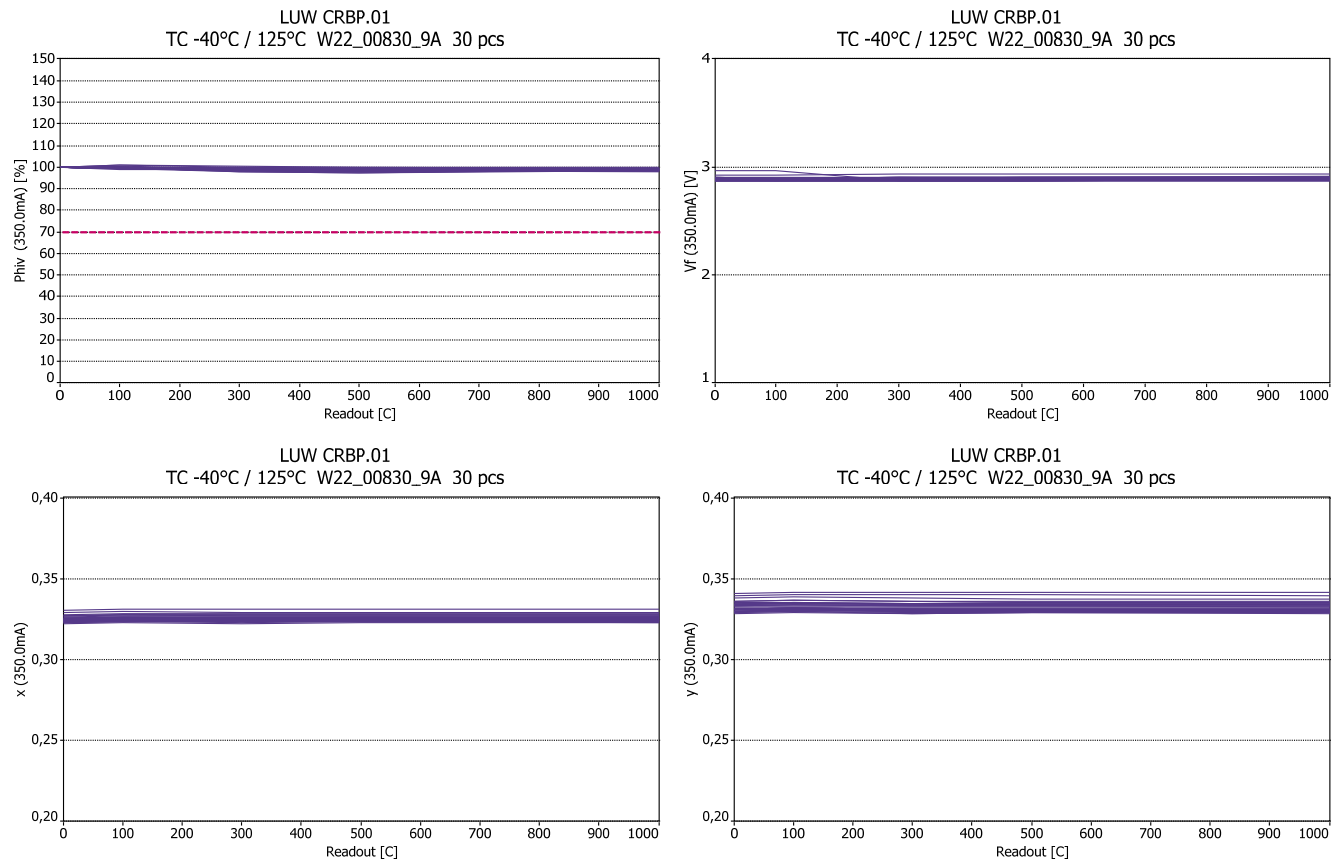


Lot D

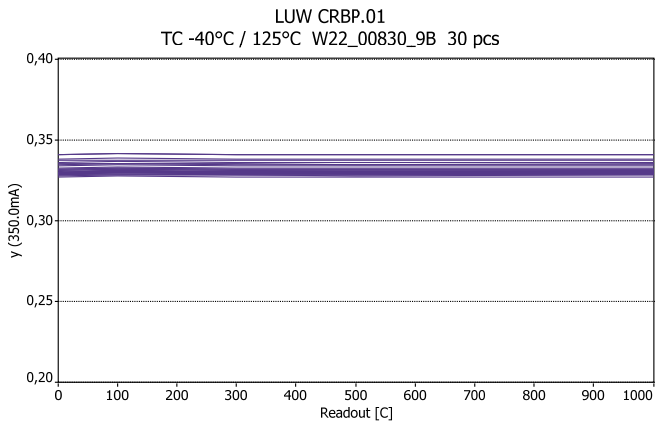
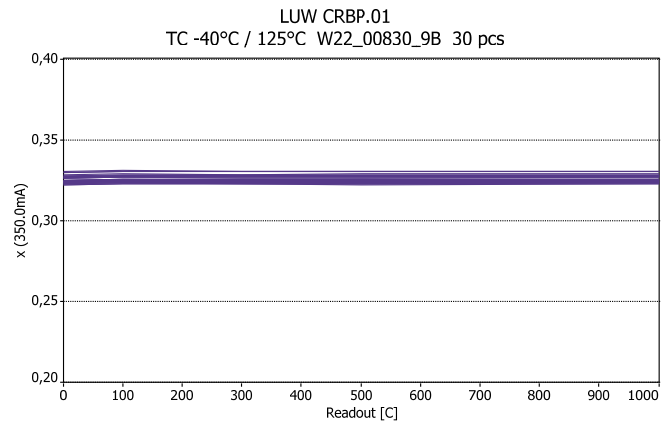
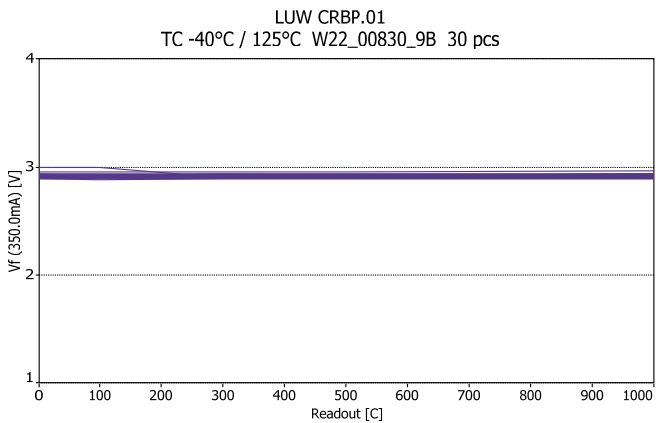
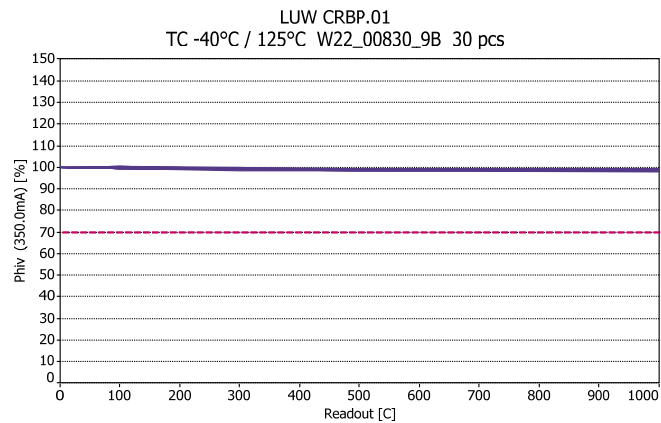


TC -40°C / 125°C

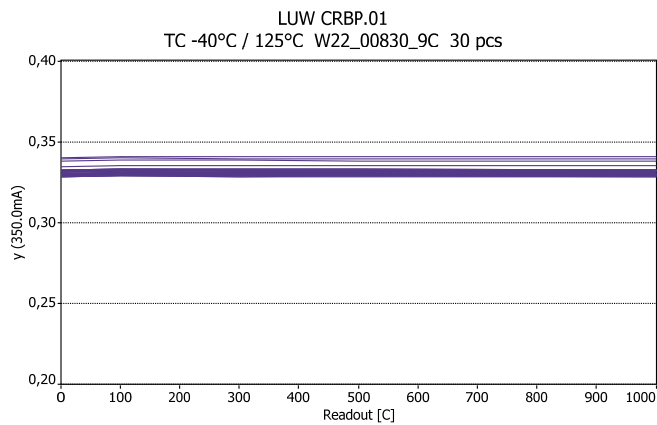
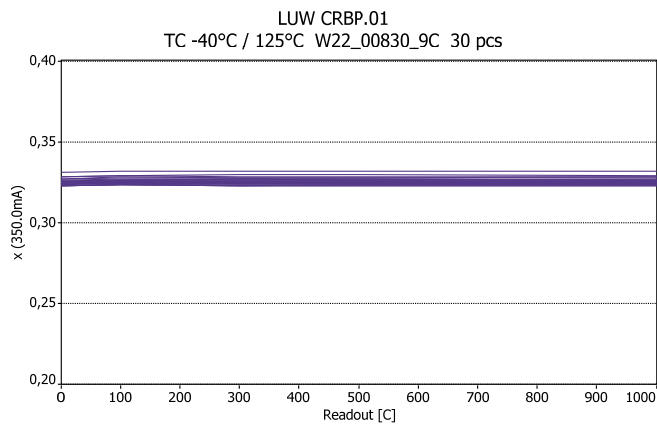
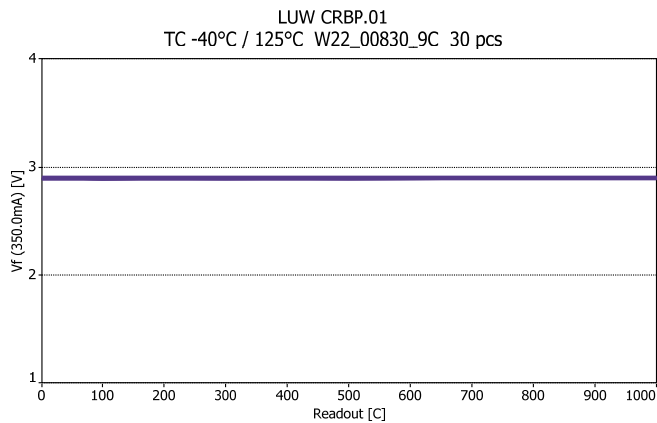
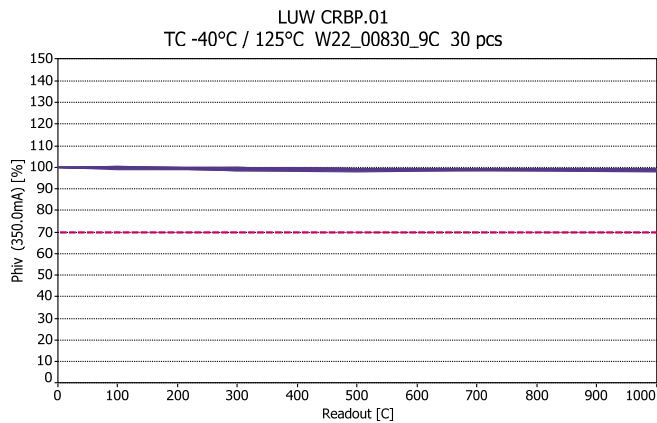
Lot A



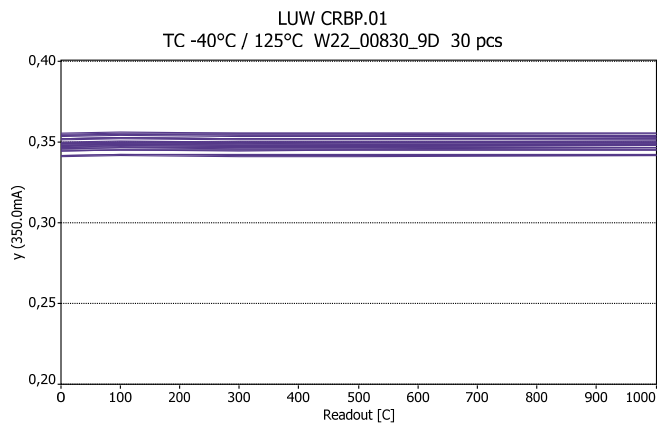
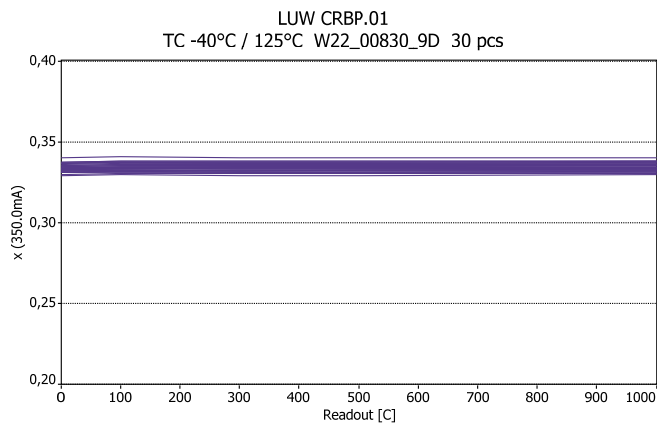
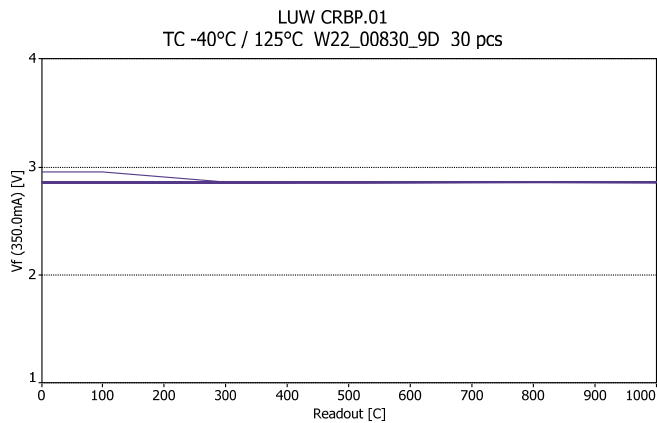
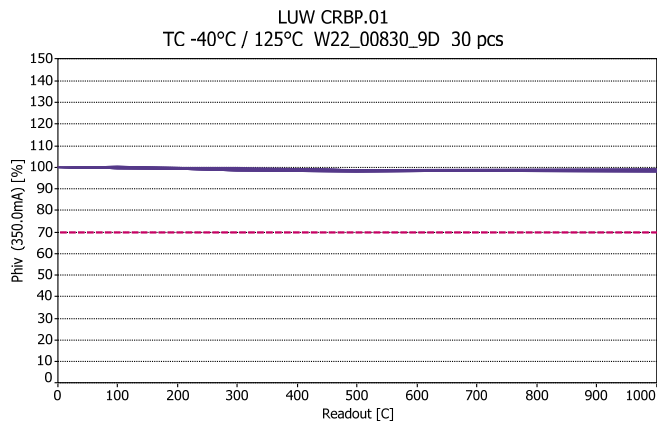
Lot B



Lot C

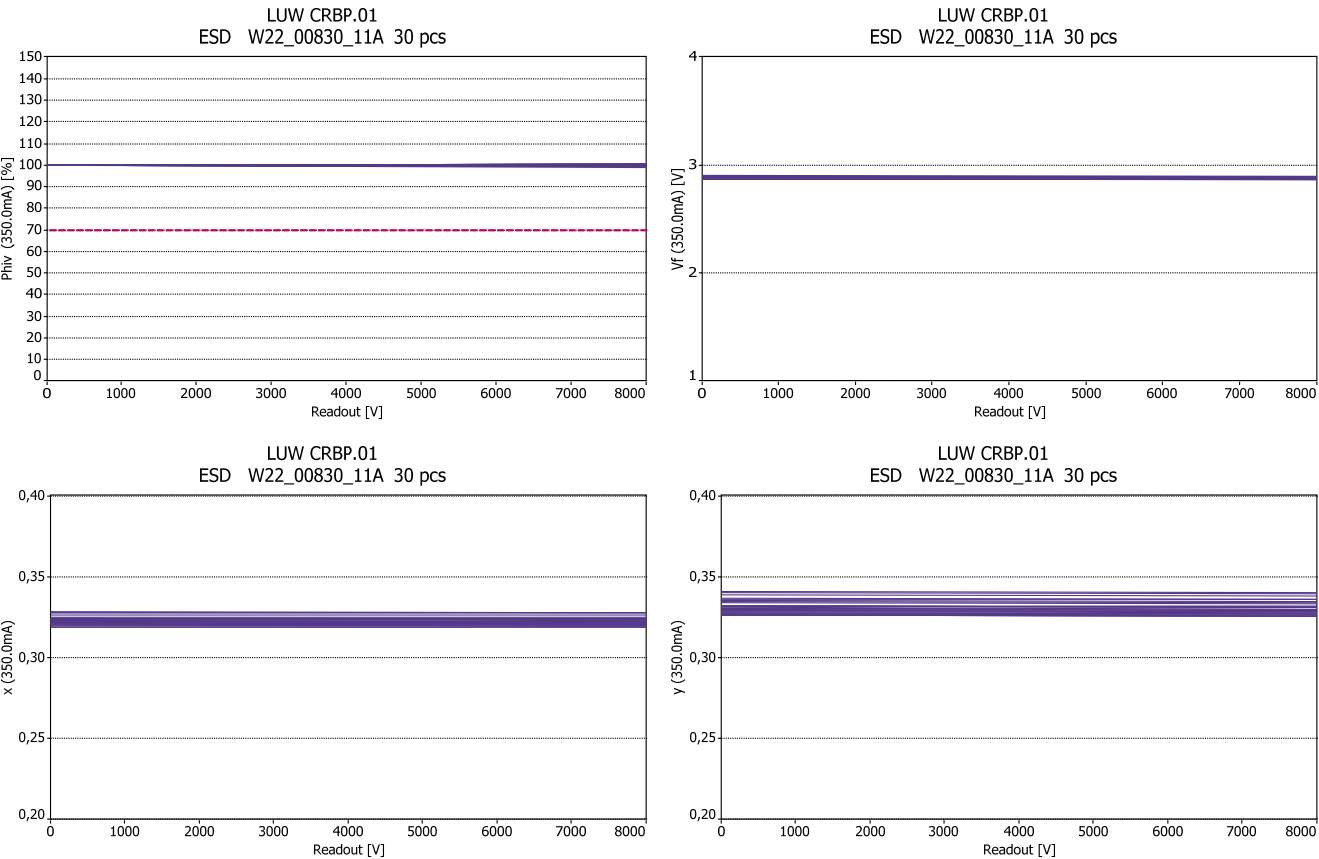


Lot D

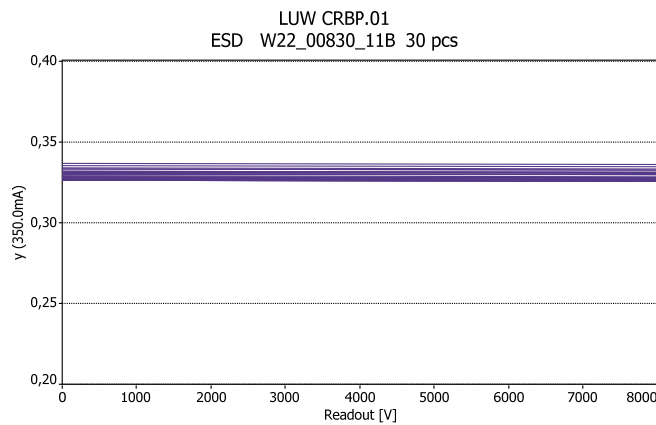
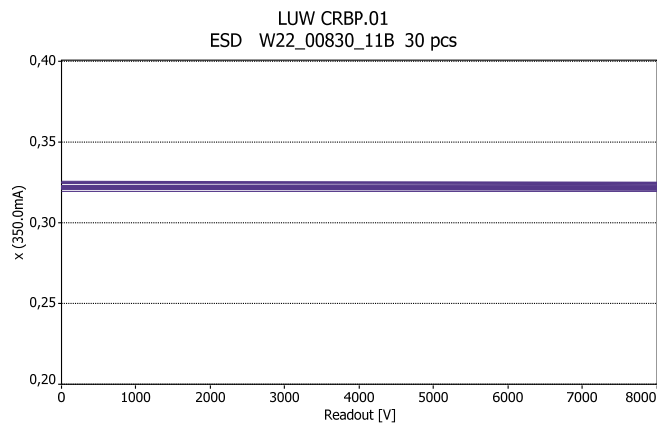
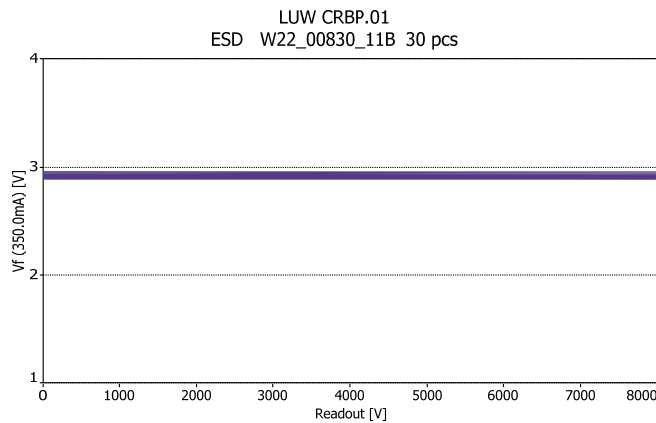
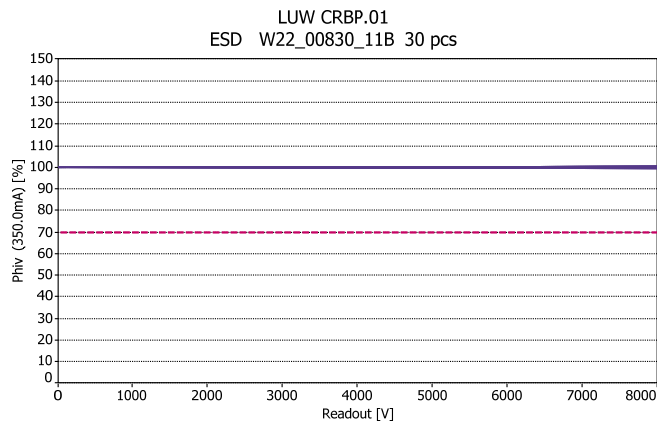


ESD HBM

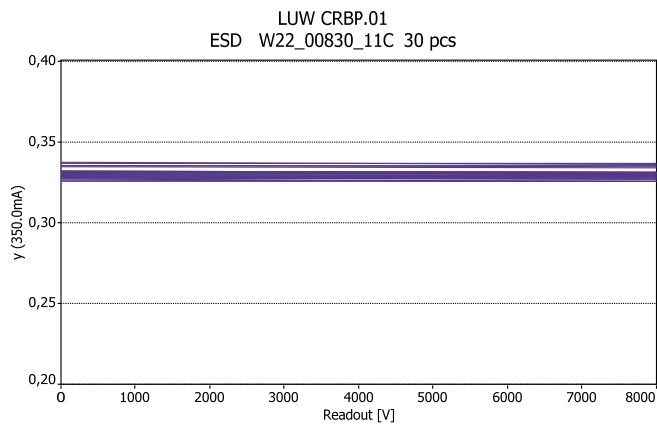
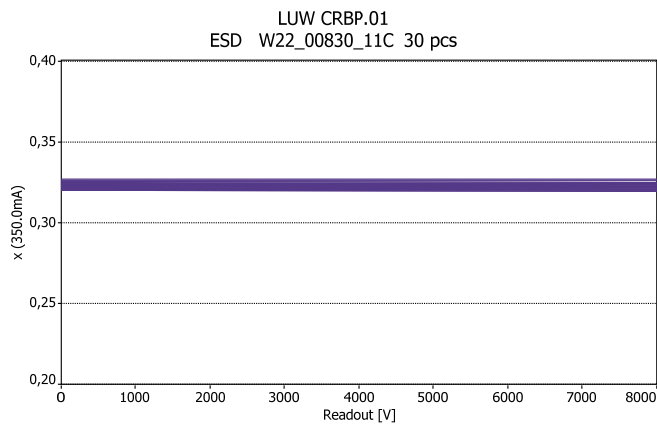
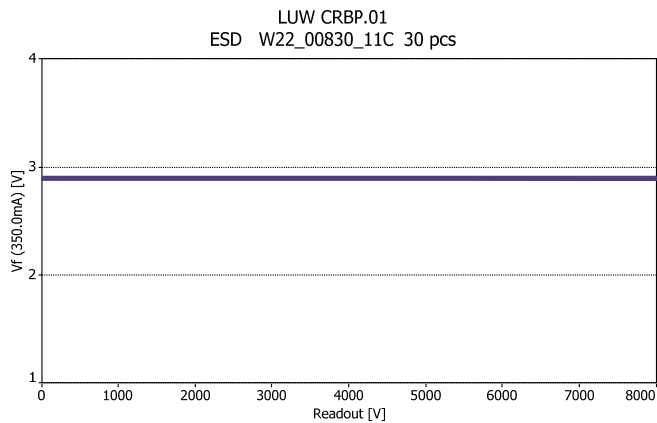
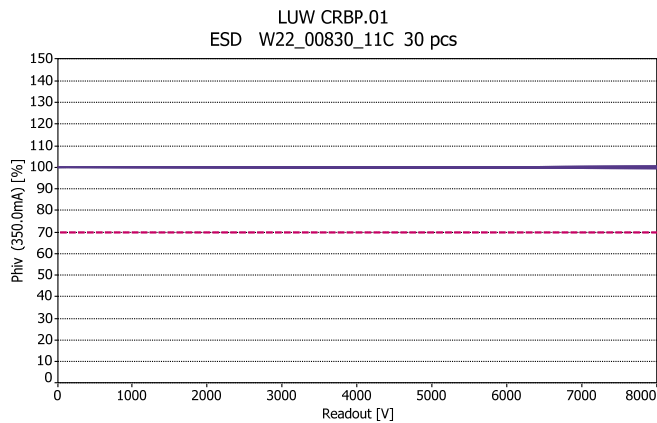
Lot A



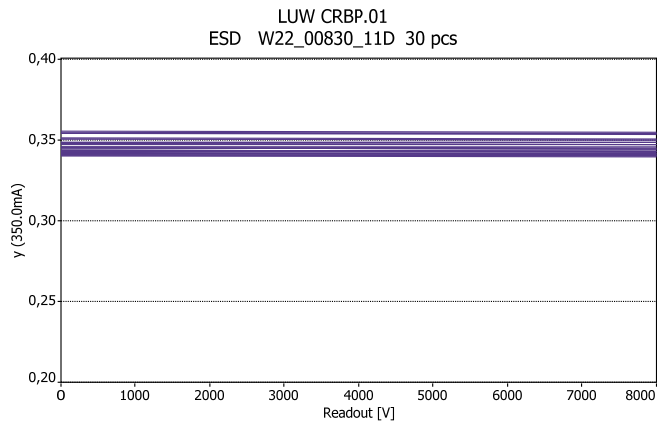
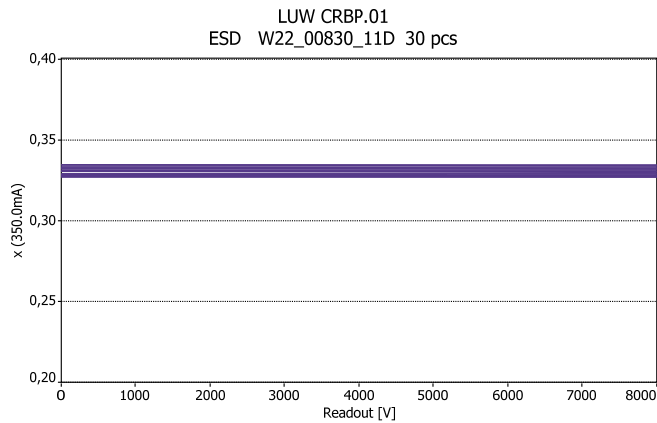
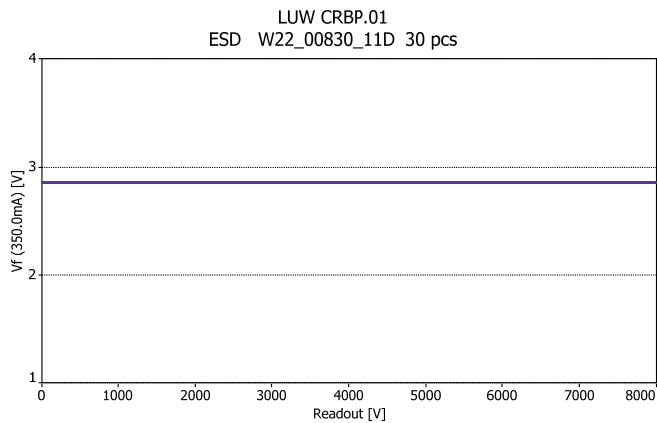
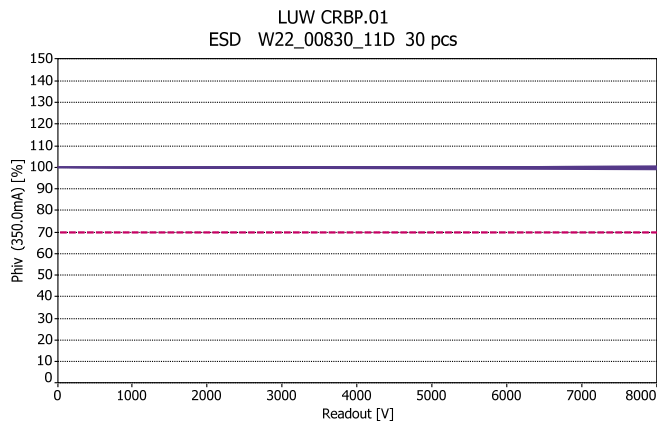
Lot B



Lot C

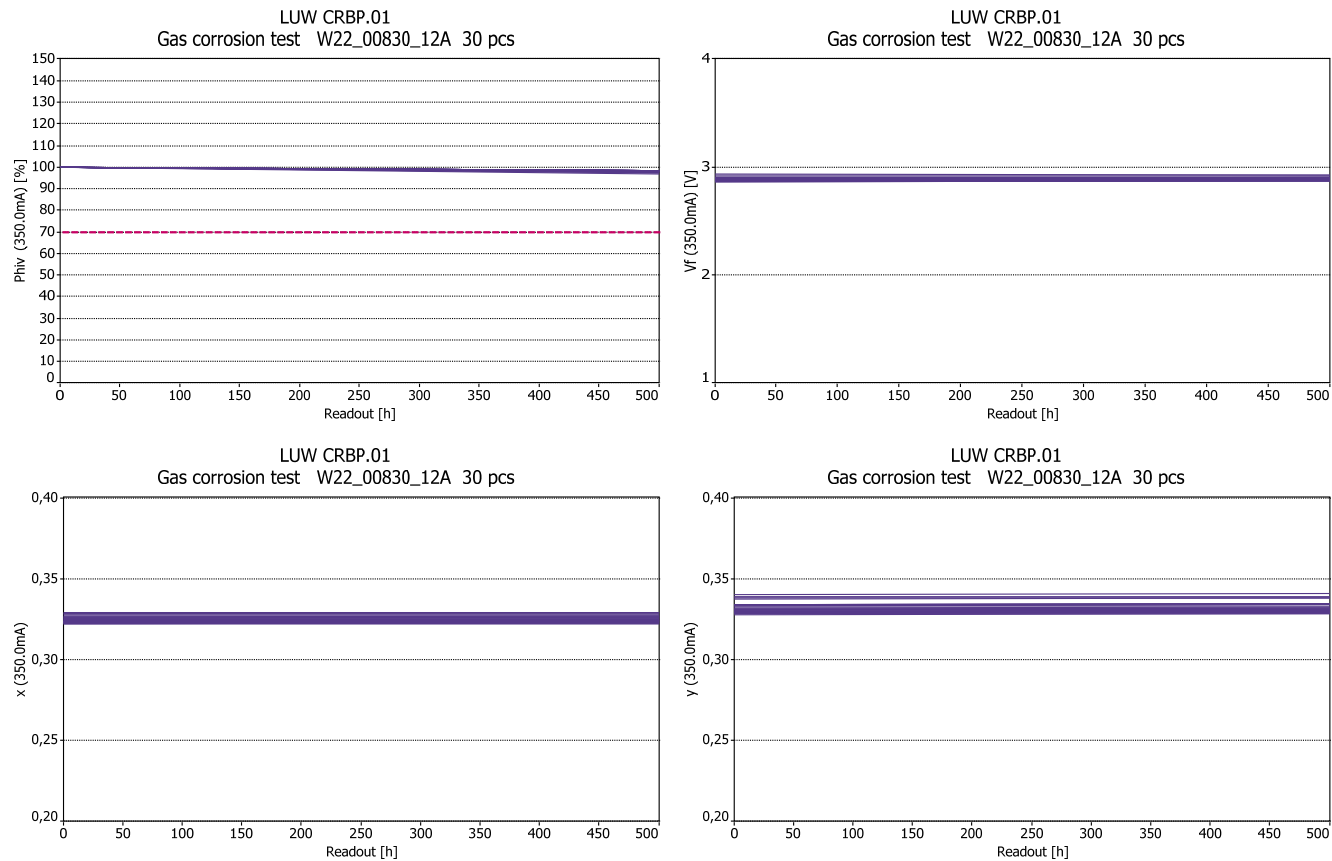


Lot D

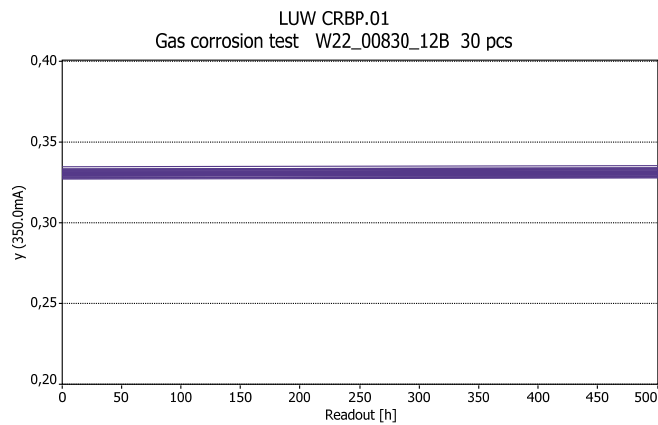
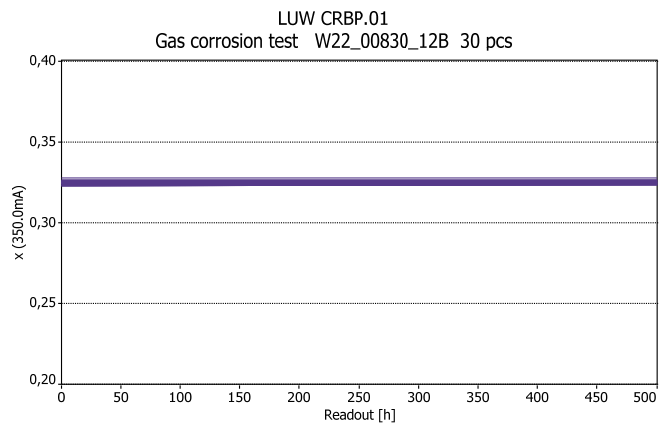
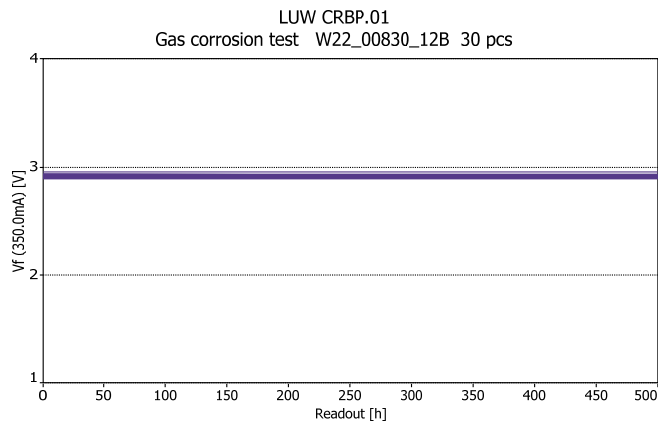
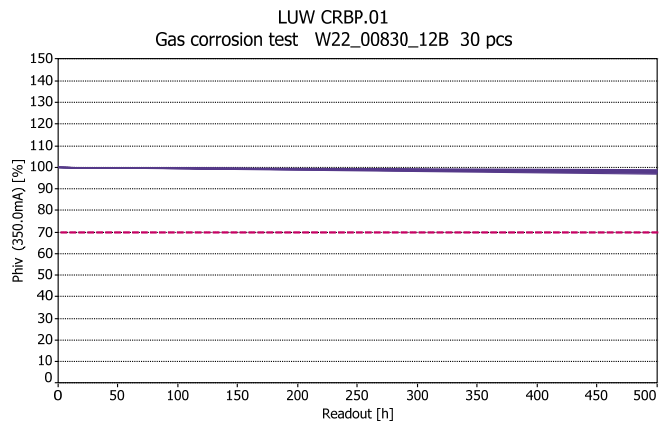


Gas corrosion test

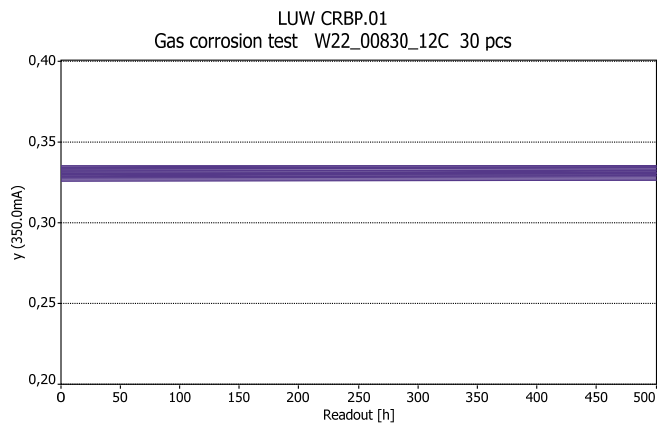
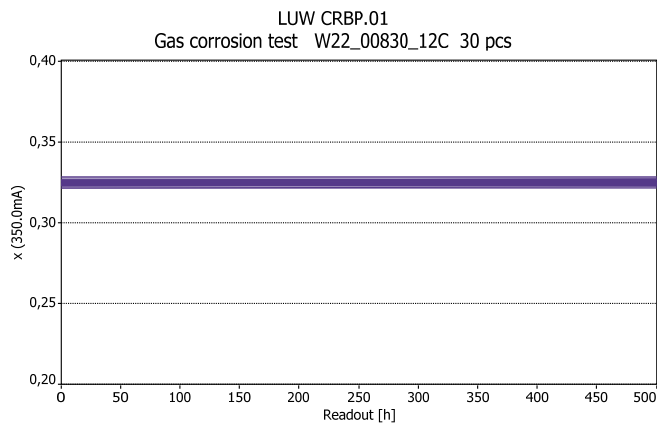
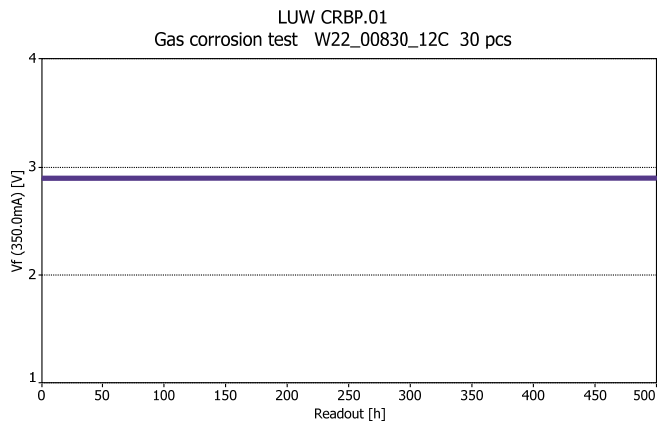
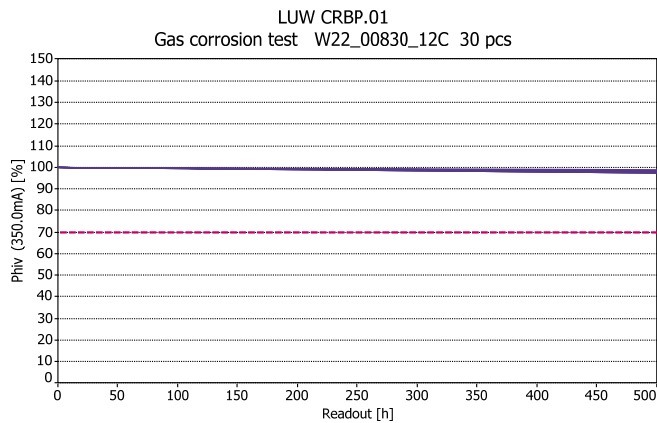
Lot A



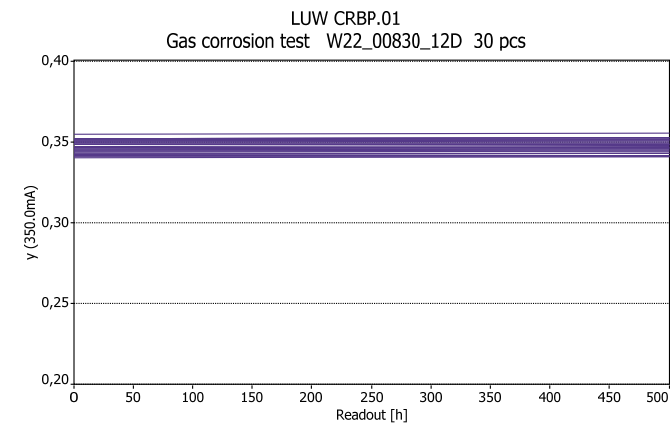
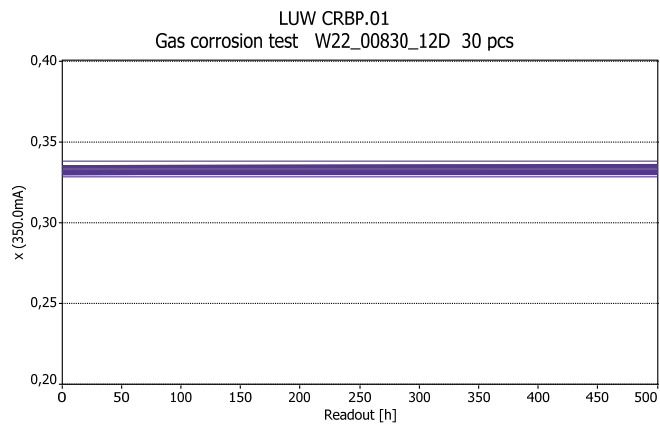
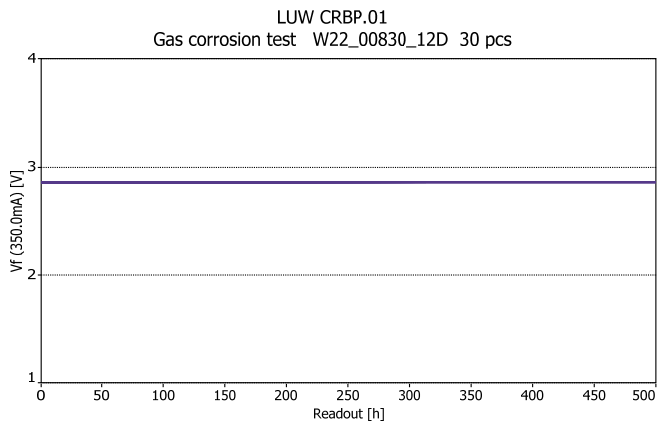
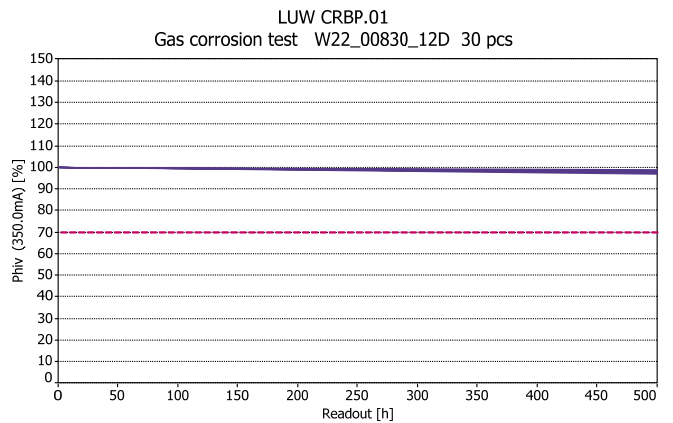
Lot B



Lot C

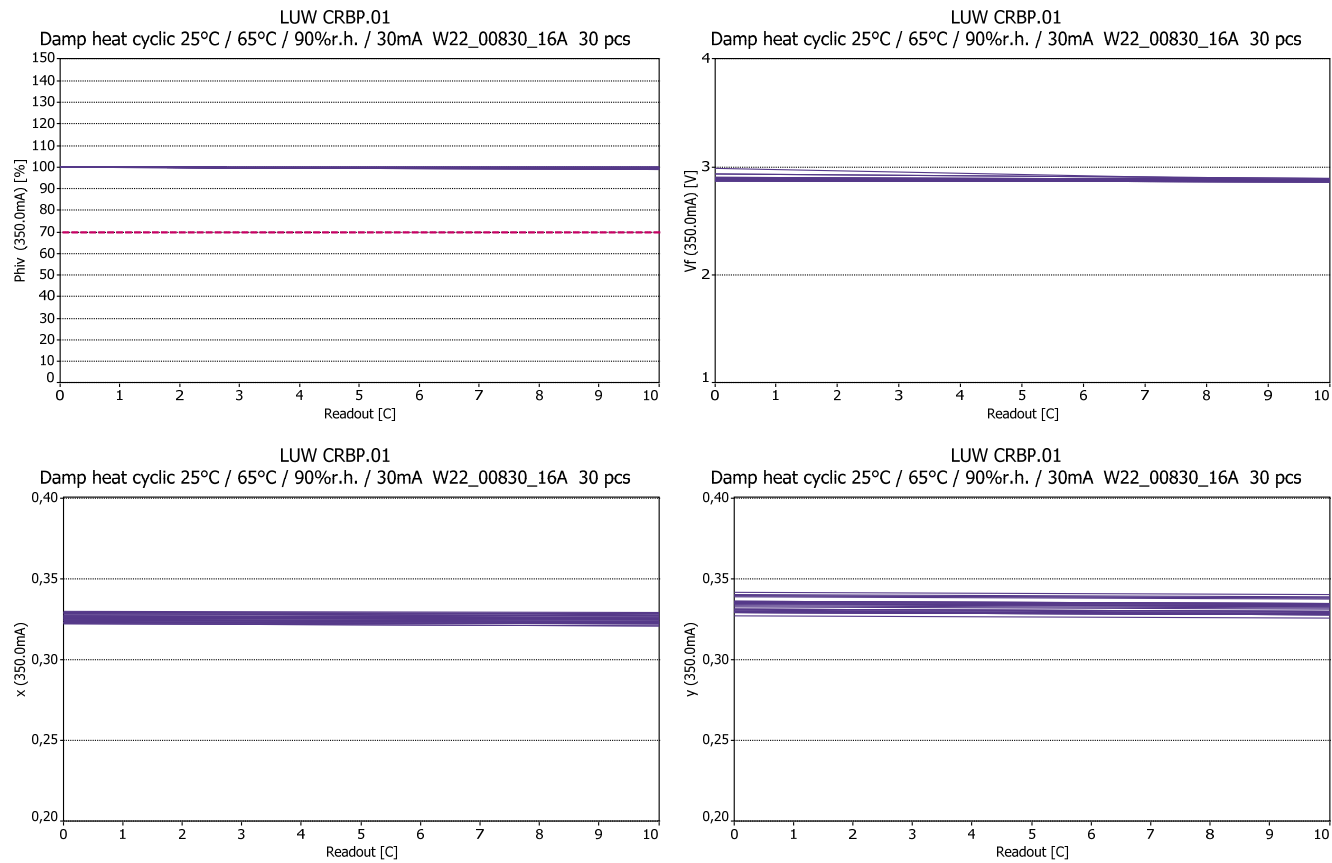


Lot D

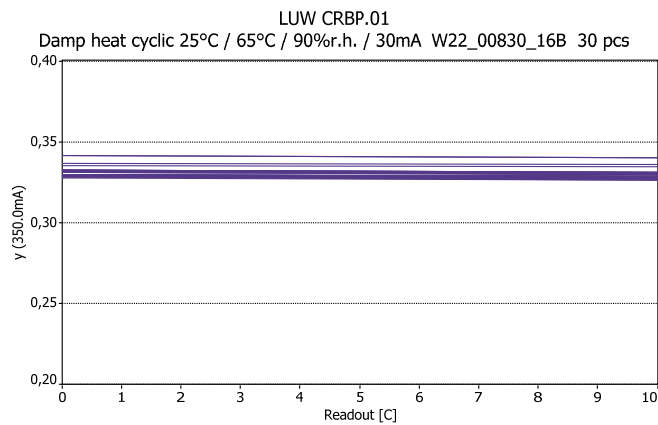
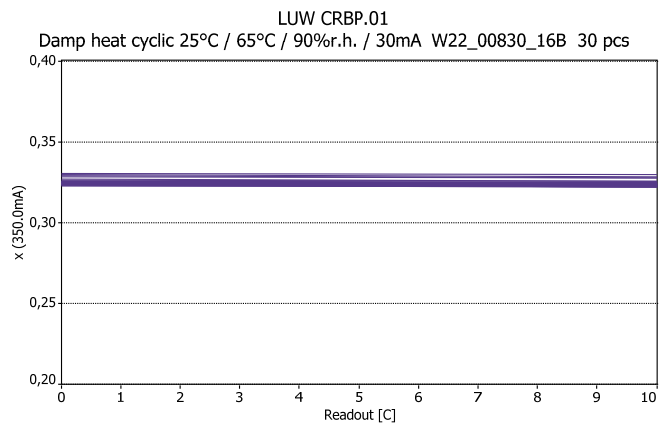
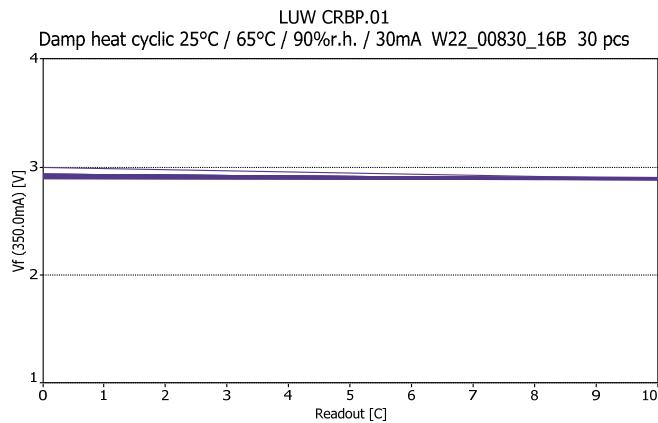
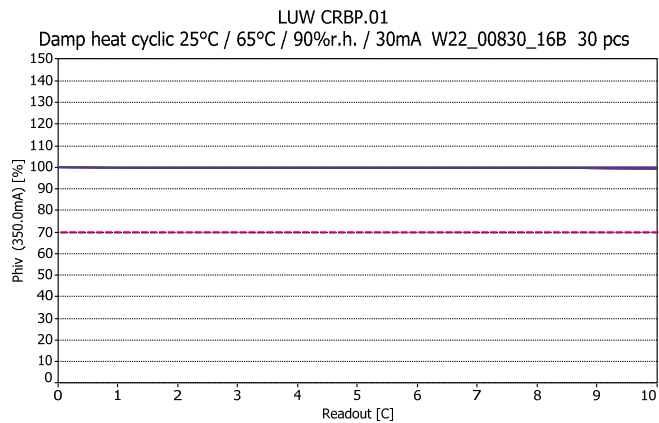


Damp heat cyclic 25°C / 65°C / 90%r.h. / 30mA

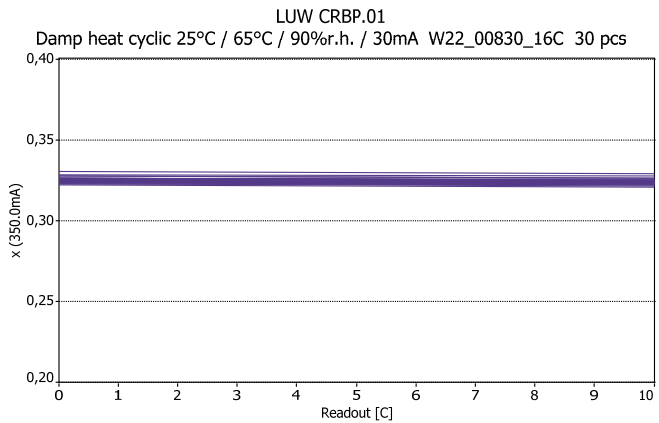
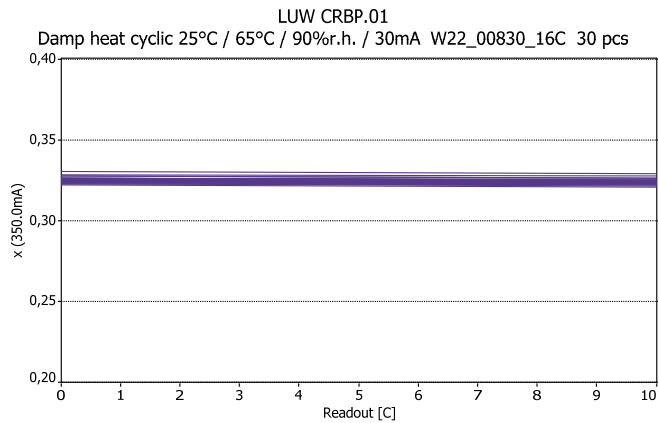
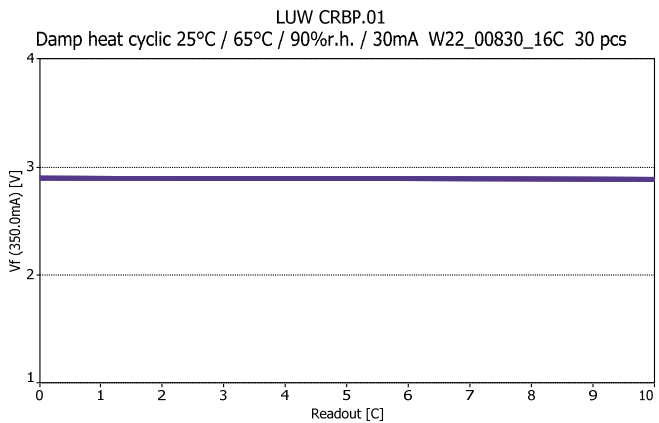
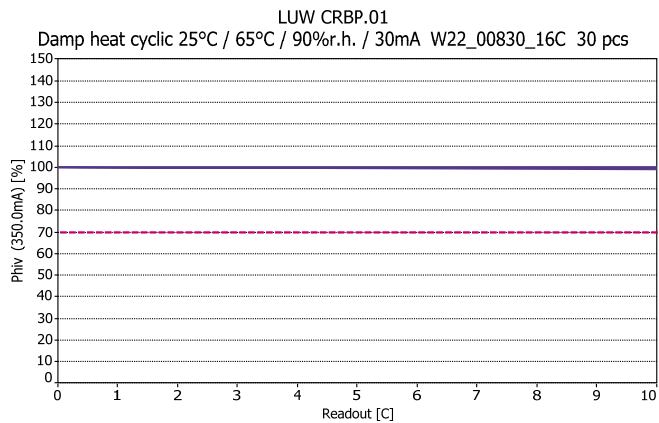
Lot A



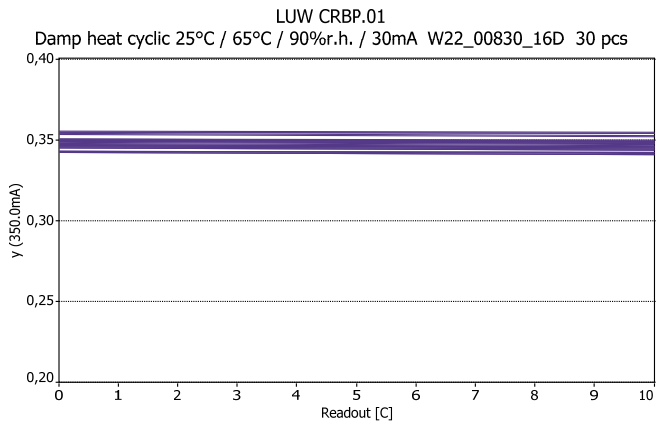
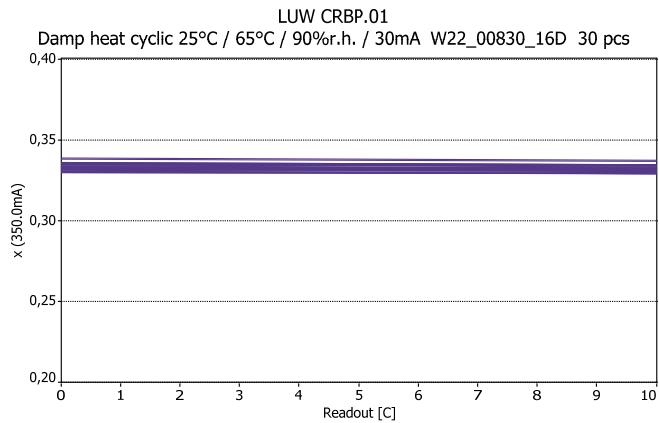
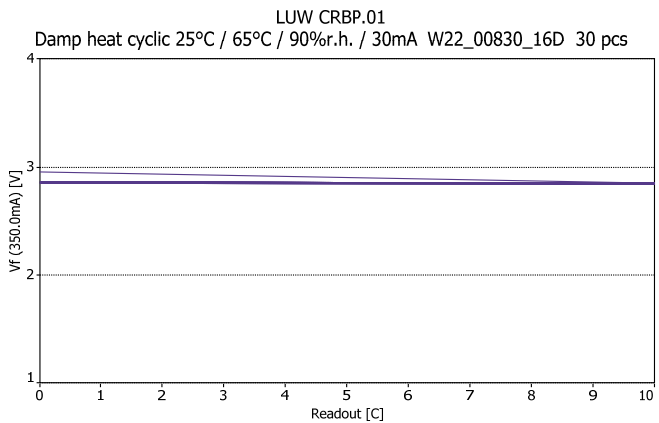
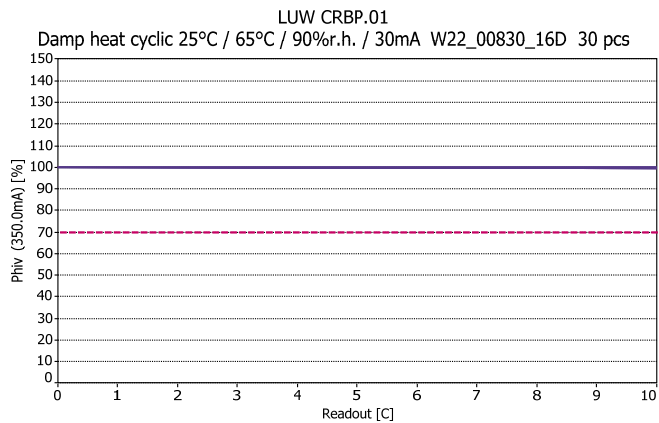
Lot B



Lot C



Lot D



END OF DOCUMENT